











TIC12400-Q1

ZHCSGP5A -AUGUST 2017-REVISED SEPTEMBER 2017

# 适用于汽车系统并具有集成式 ADC 和可调湿性电流的 TIC12400-Q1 24 路输入多开关检测接口 (MSDI)

## 1 特性

- 符合汽车应用 要求
- 符合 AEC-Q100 标准, 其中包括以下内容:
  - 器件温度 1 级: -40°C 至 125°C 的环境运行温度范围
  - 器件人体放电模式 (HBM) 静电放电 (ESD) 分类 等级 H2
  - 器件组件充电模式 (CDM) ESD 分类等级 C4B
- 旨在支持 12V 汽车系统并提供过压和欠压警告
- 监控多达 24 路直接开关输入,并可配置其中 10 路 输入以监控连接到地线或电池的开关
- 开关输入可承受高达 40V 的电压(负载突降条件)
   和低至 -24V 的电压(反极性条件)
- 6 种可配置的湿性电流设置:

   (0mA、1mA、2mA、5mA、10mA 和 15mA)
- 适用于多位模拟开关监控的 10 位集成 ADC
- 适用于数字开关监控并具有 4 个可编程阈值的集成 比较器
- 在轮询模式下具有超低工作电流: 典型值为 68μA(t<sub>POLL</sub> = 64ms, t<sub>POLL\_ACT</sub> = 128μs, 全部 24 路输入均处于活动状态,比较器模式,所
- 使用 3.3V/5V 串行外设接口 (SPI) 协议直接与 MCU 对接
- 可产生中断来支持所有输入的唤醒操作
- 集成电池和温度传感

有开关均打开)

- 采用适当的外部组件根据 ISO-10605 在输入引脚上 实现 ±8kV 接触放电 ESD 保护
- 38 引脚 TSSOP 封装

## 2 应用

- 车身控制模块和网关
- 汽车照明
- 加热和冷却
- 电动座椅
- 后视镜

## 3 说明

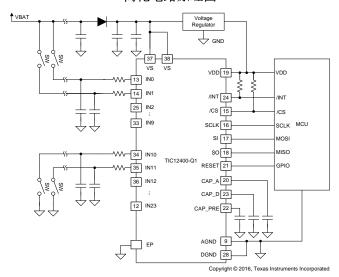
TIC12400-Q1 是先进的多开关检测接口 (MSDI),用于 检测 12V 汽车系统中的外部开关状态。TIC12400-Q1 采用了 集成的 10 位 ADC 对多位模拟开关进行监控, 并采用比较器来独立于 MCU 对数字开关进行监控。可 为 ADC 和比较器设定检测阈值,从而支持各种开关拓 扑和系统非理想特性。该器件监控多达 24 路直接开关 输入,并可配置其中 10 路输入以监控连接到地线或电 池的开关。可为每路输入设定 6 种独特的湿性电流设 置,从而支持不同的应用场景。该器件支持所有开关输 入的唤醒操作,因此无需持续使 MCU 保持活动状态, 讲而可降低系统功耗。TIC12400-Q1 还提供集成故障 检测、ESD 保护和诊断功能,从而提高系统稳健性。 TIC12400-Q1 支持 2 种工作模式: 连续模式和轮询模 式。连续模式下将连续提供湿性电流。轮询模式下将根 据可编程计时器来定期接通湿性电流以对输入状态进行 采样,从而显著降低系统功耗。

## 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
TIC12400-Q1	TSSOP (38)	9.70 mm x 4.40 mm

(1) 如需了解所有可用封装,请参阅产品说明书末尾的可订购产品 附录。

#### 简化电路原理图



M



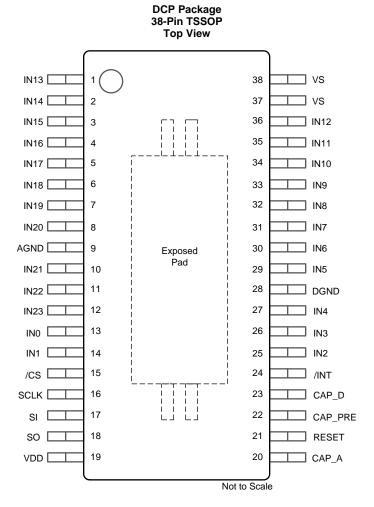
	目录			
1	特性		8.5 Programming	45
2	应用 1		8.6 REGISTER_MAPS	48
3	说明1		8.7 Programming Guidelines	112
4	修订历史记录 2	9	Application and Implementation	115
5	Pin Configuration and Functions3		9.1 Application Information	115
6	Specifications5		9.2 Using TIC12400-Q1 in a 12 V Automotive System	115
	6.1 Absolute Maximum Ratings		9.3 Resistor-coded Switches Detection in Automor Body Control Module	tive
	6.3 Recommended Operating Conditions 5	10	Power Supply Recommendations	121
	6.4 Thermal Information 6	11		
	6.5 Electrical Characteristics		11.1 Layout Guidelines	
	6.6 Timing Requirements 10		11.2 Layout Example	
	6.7 Typical Characteristics	12		
7	Parameter Measurement Information 13		12.1 接收文档更新通知	
8	Detailed Description 14		12.2 社区资源	
	8.1 Overview 14		12.3 商标	124
	8.2 Functional Block Diagram 15		12.4 静电放电警告	124
	8.3 Feature Description		12.5 Glossary	124
	8.4 Device Functional Modes	13	机械、封装和可订购信息	125

## 4 修订历史记录

Changes from Original (August 2017) to Revision A	Page
<ul> <li>Changed the I<sub>WETT</sub> value in the Electrical Characteristics tal</li> </ul>	ble7
• Changed From: $4.5 \text{ V} \le \text{V}_{\text{S}} \le 5 \text{ V}$ To: $4.5 \text{ V} \le \text{V}_{\text{S}} < 5.5 \text{ V}$ in	图 611
<ul> <li>Changed From: 4.5 V ≤ V<sub>S</sub> ≤ 35 V To: 5.5 V ≤ V<sub>S</sub> ≤ 35 V in</li> </ul>	图 711
• Changed the Microcontroller Wake-Up section, and 图 23	24
• Changed 表 64	
<ul> <li>Changed text in list item 2 From: "current ranging between mA and 5.5 mA (for V<sub>S</sub> − IN<sub>X</sub> ≥ 3 V condition)."</li> </ul>	4.3 mA and 5.6 mA." To: "current ranging between 4.5



## 5 Pin Configuration and Functions



## **Pin Functions**

PIN TYPE <sup>(1)</sup>		TVDE(1)	DECEDIPTION
NO.	NAME	ITPE\"	DESCRIPTION
1	IN13	I/O	Ground switch monitoring input with current source
2	IN14	I/O	Ground switch monitoring input with current source
3	IN15	I/O	Ground switch monitoring input with current source
4	IN16	I/O	Ground switch monitoring input with current source
5	IN17	I/O	Ground switch monitoring input with current source
6	IN18	I/O	Ground switch monitoring input with current source
7	IN19	I/O	Ground switch monitoring input with current source
8	IN20	I/O	Ground switch monitoring input with current source
9	AGND	Р	Ground for analog circuitry
10	IN21	I/O	Ground switch monitoring input with current source
11	IN22	I/O	Ground switch monitoring input with current source
12	IN23	I/O	Ground switch monitoring input with current source
13	IN0	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
14	IN1	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.

(1) I = input, O = output, I/O = input and output, P = power.



## Pin Functions (continued)

PIN		TYPE <sup>(1)</sup>	DECORIDE
NO.	NAME	TYPE	DESCRIPTION
15	CS	I	Active-low input. Chip select from the master for the SPI Interface.
16	SCLK	I	Serial clock output from the master for the SPI Interface
17	SI	I	Serial data input for the SPI Interface.
18	SO	0	Serial data output for the SPI Interface
19	V <sub>DD</sub>	Р	3.3 V to 5.0 V logic supply for the SPI communication. The SPI I/Os are not fail-safe protected: VDD needs to be present during any SPI traffic to avoid excessive leakage currents and corrupted SPI I/O logic levels.
20	CAP_A	I/O	External capacitor connection for the analog LDO. Use capacitance value of 100nF.
21	RESET	I	Keep RESET low for normal operation and drive RESET high and release it to perform a hardware reset of the device. The RESET pin is connected to ground via a $1M\Omega$ pull-down resistor. If not used, the RESET pin shall be grounded to avoid any accidental device reset due to coupled noise onto this pin.
22	CAP_Pre	I/O	External capacitor connection for the pre-regulator. Use capacitance value of $1\mu F$ .
23	CAP_D	I/O	External capacitor connection for the digital LDO. Use capacitance value of 100nF.
24	ĪNT	0	Open drain output. Pulled low (internally) upon change of state on the input or occurrence of a special event.
25	IN2	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
26	IN3	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
27	IN4	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
28	DGND	Р	Ground for digital circuitry
29	IN5	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
30	IN6	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
31	IN7	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
32	IN8	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
33	IN9	I/O	Ground/V <sub>BAT</sub> switch monitoring input with configurable current sink or source.
34	IN10	I/O	Ground switch monitoring input with current source
35	IN11	I/O	Ground switch monitoring input with current source
36	IN12	I/O	Ground switch monitoring input with current source
37	Vs	Р	Power supply input pin.
38	Vs	Р	Power supply input pin.
	EP	Р	Exposed Pad. The exposed pad is not electrically connected to AGND or DGND. Connect EP to the board ground to achieve rated thermal and ESD performance.



## 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Input voltage	V <sub>S</sub> , <del>INT</del>	-0.3	40 <sup>(2)</sup>	V
	V <sub>DD</sub> , SCLK, SI, SO, <del>CS</del> , RESET	-0.3	6	V
Input voltage	IN0- IN23	-24	-0.3 40 <sup>(2)</sup> V -0.3 6 V -24 40 <sup>(2)</sup> V -0.3 5.5 V -0.3 5.5 V -0.3 2 V -40 150 °C	
input voltage	CAP_Pre	-0.3	5.5	V
	CAP_A	-0.3	5.5	V
	CAP_D	-0.3	2	V
Operating junction t	temperature, T <sub>J</sub>	-40	150	°C
Storage temperatur	re, T <sub>stg</sub>	-55	155	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

				VALUE	UNIT
V(500)		Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup>	All pins	±2000	
		Human-body model (HBM), per AEC Q100-002**	Pins IN0-IN23 <sup>(2)</sup>	±4000	
			All pins	±500	
		Charged-device model (CDM), per AEC Q100-011	Corner pins (pin 1, 19, 20 and 38)	±750	
V <sub>(ESD)</sub>	Electrostatic discharge		Pins IN0-IN23	±8000	V
		Contact discharge, powered-up, per ISO- 10605:  • External components: capacitor = 15 nF; resistor = 33 $\Omega$ • ESD generator parameters: storage capacitance = 150 pF or 330pF; discharge resistance = 330 $\Omega$ or 2000 $\Omega$	Pins IN0-IN23	20 ±750	

<sup>(1)</sup> AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range and V<sub>S</sub> = 12 V (unless otherwise noted)

		MIN	NOM MAX	UNIT
Vs	Power supply voltage	4.5	35 <sup>(1)</sup>	V
$V_{DD}$	Logic supply voltage	3.0	5.5	V
V <sub>/INT</sub>	INT pin voltage	0	35 <sup>(1)</sup>	V
V <sub>INX</sub>	IN0 to IN23 input voltage	0	35 <sup>(1)</sup>	V
V <sub>RESET</sub>	RESET pin voltage	0	5.5	V
V <sub>SPI_IO</sub>	SPI input/output logic level	0	$V_{DD}$	V
f <sub>SPI</sub>	SPI communication frequency	20 <sup>(2)</sup>	4M	Hz
T <sub>A</sub>	Operating free-air temperature	-40	125	°C

<sup>(1)</sup> Tested for load dump and jump start conditions with nominal operating voltage no greater than 16 V for the life of a 12-V automotive system. Refer to Using TIC12400-Q1 in a 12 V Automotive System for more details.

<sup>(2)</sup> Tested for load dump and jump start conditions with nominal operating voltage no greater than 16V for the life of a 12-V automotive system. Refer to Using TIC12400-Q1 in a 12 V Automotive System for more details.

<sup>(2) ±4</sup>kV rating on pins IN0-IN23 are stressed with respect to GND (with AGND, DGND, and EP tied together).

<sup>(2)</sup> Lowest frequency characterized.



## 6.4 Thermal Information

		TIC12400-Q1	
	THERMAL METRIC <sup>(1)</sup>	DCP (TSSOP)	UNIT
		38 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	33.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	18.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	15.2	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	15.0	°C/W
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	1.2	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 6.5 Electrical Characteristics

over operating free-air temperature range,  $V_S = 4.5 \text{ V}$  to 35 V, and  $V_{DD} = 3 \text{ V}$  to 5.5 V (unless otherwise noted)

PARAMETER			MIN	TYP	MAX	UNIT	
POWER SUPPLY		-					
I <sub>S_CONT</sub>	Continuous mode V <sub>S</sub> power supply current		I <sub>WETT</sub> = 10 mA, all switches open, no active comparator comparison, no unserviced		5.6	7	mA
I <sub>S_POLL_COMP_25</sub>	Polling mode V <sub>S</sub>	T <sub>A</sub> = 25°	Polling mode, t <sub>POLL</sub> = 64 ms, t <sub>POLL</sub> _ACT= 128		68	100	μA
I <sub>S_POLL_COMP_85</sub>	power supply average current in	T <sub>A</sub> = -40° to 85°C	µs, all 24 channels active and configured to comparator mode, all switches open, I <sub>WFTT</sub> =		68	110	μΑ
I <sub>S_POLL_COMP</sub>	comparator mode	$T_A = -40^{\circ} \text{ to } 125^{\circ}\text{C}$	10 mA, no unserviced interrupt		68	170	μΑ
I <sub>S_POLL_ADC_25</sub>	Polling mode V <sub>S</sub>	T <sub>A</sub> = 25°	Polling mode, t <sub>POLL</sub> = 64 ms, t <sub>POLL_ACT</sub> = 128		75	105	μΑ
I <sub>S_POLL_ADC_85</sub>	power supply average current in	T <sub>A</sub> = -40° to 85°C	µs, all 24 channels active and configured to ADC mode, all switches open, I <sub>WETT</sub> = 10 mA,		75	120	μΑ
I <sub>S_POLL_ADC</sub>	ADC mode	$T_A = -40^{\circ} \text{ to } 125^{\circ}\text{C}$	no unserviced interrupt		75	180	μΑ
I <sub>S_RESET</sub>	Reset mode V <sub>S</sub> power supply current	Reset mode, V <sub>RESE</sub>	$v_{T} = V_{DD}$ . $V_{S} = 12$ V, all switches open, $T_{A} = 25$ °C		12	17	μΑ
I <sub>S_IDLE_25</sub>		TRIGGER bit in CO unserviced interrup	ONFIG register = logic 0, T <sub>A</sub> = 25°C, no t		50	75	μΑ
I <sub>S_IDLE_85</sub>	V <sub>S</sub> power supply average current in idle state	TRIGGER bit in CC unserviced interrup	ONFIG register = logic 0, T <sub>A</sub> = -40°C to 85°C, no t		50	95	μA
I <sub>S_IDLE</sub>	Idio state	TRIGGER bit in CC no unserviced inter	ONFIG register = logic 0, T <sub>A</sub> = -40°C to 125°C, rupt		50	145	μA
I <sub>DD</sub>	Logic supply current from V <sub>DD</sub>	SCLK = SI = 0 V, C	SCLK = SI = 0 V, $\overline{\text{CS}} = \overline{\text{INT}} = \text{V}_{\text{DD}}$ , no SPI communication		1.5	10	μA
V <sub>POR_R</sub>	Power on reset		Threshold for rising V <sub>S</sub> from device OFF condition resulting in INT pin assertion and a flagged POR bit in the INT_STAT register			4.5	V
V <sub>POR_F</sub>	(POR) voltage for V <sub>S</sub>	Threshold for falling mode and loss of S	g V <sub>S</sub> from device normal operation to reset PI communication	1.95		2.8	V
V <sub>OV_R</sub>	Over-voltage (OV) condition for V <sub>S</sub>		V <sub>S</sub> from device normal operation resulting in nd a flagged OV bit in the INT_STAT register	35		40	V
V <sub>OV_HYST</sub>	Over-voltage (OV) condition hysteresis for V <sub>S</sub>			1		3.5	V
$V_{UV_{R}}$	Under-voltage (UV)		V <sub>S</sub> from under-voltage condition resulting in nd a flagged UV bit in the INT_STAT register	3.85		4.5	٧
$V_{UV_{F}}$	condition for V <sub>S</sub>	Threshold for falling V <sub>S</sub> from under-votlage condition resulting in INT pin assertion and a flagged UV bit in the INT_STAT register		3.7		4.4	٧
V <sub>UV_HYST</sub>	Under-voltage (UV) condition hysteresis for V <sub>S</sub> <sup>(1)</sup>	J		75		275	mV
$V_{DD_{\_F}}$		Threshold for falling	g V <sub>DD</sub> resulting in loss of SPI communication	2.5		2.9	V
V <sub>DD_HYST</sub>	Valid V <sub>DD</sub> voltage hysteresis			50		150	mV

(1) Verified by design.



## **Electrical Characteristics (continued)**

over operating free-air temperature range,  $V_S = 4.5 \text{ V}$  to 35 V, and  $V_{DD} = 3 \text{ V}$  to 5.5 V (unless otherwise noted)

	AMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
WETTING CURRENT VALUE WITH SWITC		WITCHES, MAXIM	UM RESISTANCE VALUE WITH SWITCH CLOSE	ED ≤ 100Ω ,	MINIMUM	RESISTA	NCE
VALUE WITH SWITC	H OPEN 2 5000 (2)	4 . 4		0.04		4.44	
		1 mA setting	4.5 V ≤ V <sub>S</sub> ≤ 35 V	0.84	1	1.14	
		2 mA setting		1.71	2	2.32	
		5 mA setting	4.5 V ≤ V <sub>S</sub> < 5 V	2.39		5.5	
WETT (CSO)	Wetting current accuracy for CSO	0 00g	5 V ≤ V <sub>S</sub> ≤ 35 V	4.3	5	5.6	mA
WETT (CGC)	(switch closed)	10 mA setting	4.5 V ≤ V <sub>S</sub> < 6 V	2.4		11	ША
		10 IIIA setting	6 V ≤ V <sub>S</sub> ≤ 35 V	8.4	10	11.4	
		45 4 44:	4.5 V ≤ V <sub>S</sub> < 6.5 V	2.4		16.5	
		15 mA setting	6.5 V ≤ V <sub>S</sub> ≤ 35 V	12.5	15	17	
		1 mA setting		0.75	1.1	2.05	
		2 mA setting	T	1.6	2.2	3.3	
	Wetting current	5 mA setting	$4.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}$	4.3	5.6	7.1	
WETT (CSI)	accuracy for CSI (switch closed)	10 mA setting		9.2	11.5	13.4	mA
	(Switch closed)	3	4.5 V ≤ V <sub>S</sub> < 6 V	11	16.5	19.2	
		15 mA setting	6 V ≤ V <sub>S</sub> ≤ 35V	13.7	16.5	19.2	
		10 mA setting,	0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	10.7	10.0	15.2	
	Voltage drop from IN <sub>x</sub>	$R_{SW} = 5k\Omega$				1.7	
V <sub>CSI_DROP_OPEN</sub>	pin to AGND across CSI (switch open)	15 mA setting,	$4.5 \text{ V} \leq \text{V}_{\text{S}} \leq 35 \text{V}$			4.7	V
	cor (owner open)	$R_{SW}=5k\Omega$				1.7	
		2mA setting, I <sub>IN</sub> =				4.0	.,
		1mA (4.5V≤ VS ≤ 35V)				1.2	V
		5mA setting, I <sub>IN</sub> =					
	Voltage drop from	1mA or 2mA				1.3	V
V <sub>CSI_DROP_CLOSED</sub>	INx pin to ground across CSI (switch closed)	10mA setting, I <sub>IN</sub> =					
		1mA, 2mA, or 5mA 15mA setting, I <sub>IN</sub> = 1mA, 2mA, 5mA,				1.5	V
			+				
						2.1	V
		or 10mA					
WETTING CURRENT	ACCURACY (ANALOG	SWITCHES)					
		1 mA setting	$4.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}, \text{ V}_{\text{S}} - \text{V}_{\text{INX}} \ge 2.5 \text{ V}$	0.88	1	1.13	
		2 mA setting	4.5 V 3 V <sub>S</sub> 3 55 V, V <sub>S</sub> - V <sub>INX</sub> 2 2.5 V	1.8	2	2.25	
•	Wetting current	5 A	$5.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}, \text{ V}_{\text{S}} - \text{V}_{\text{INX}} \ge 2.5 \text{ V}$	4.3	5	5.5	
WETT	accuracy	5 mA setting	$5.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}, \text{ V}_{\text{S}} - \text{V}_{\text{INX}} \ge 3 \text{ V}$	4.5	5	5.5	mA
		10 mA setting	$6 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}, \text{V}_{\text{S}} - \text{V}_{\text{INX}} \ge 4 \text{ V}$	9	10	11	
		15 mA setting	$6.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}, \text{ V}_{\text{S}} - \text{V}_{\text{INX}} \ge 5 \text{ V}$	12.5	15	16.5	
LEAKAGE CURRENT	ΓS	<u> </u>	S , S , IVX				
In_leak_off		0 V ≤ V <sub>IN</sub> ≤ V <sub>2</sub> C	hannel disabled (EN_INx register bit= logic 0)	-4		5.3	
-IIN_LEAN_UFF	Leakage current at input INx when		hannel disabled (EN_INx register bit= logic 0),				μΑ
I <sub>IN_LEAK_OFF_25</sub>	channel is disabled	$T_A = 25^{\circ}C$		-0.5		0.5	•
	Leakage current at						μA
IN_LEAK_0mA	input INx when	$0 \text{ V} \le \text{V}_{\text{INx}} \le 6 \text{ V}. 6$	V ≤ V <sub>S</sub> ≤ 35 V , I <sub>WETT</sub> setting = 0 mA	-110		110	
	wetting current setting is 0mA						μΑ
	Leakage current at						
IN_LEAK_LOSS_OF_GND	input INx under loss	$V_S = 24 \text{ V}, 0 \text{ V} \le \text{V}$	$f_{\text{INX}} \le 24 \text{ V}$ , all grounds (AGND, DGND, and EP) and to the grounds (1)	-5			μΑ
	of GND condition	= 27 v, vDD SHOILE	a to the grounds				h,
	Leakage current at	0.1/6.1/ 6.24.1/	V shorted to the grounds = 0 \ \ \ \ = 0 \			_	
	input INIV under less	$0 \text{ V} \le \text{V}_{\text{INx}} \le 24 \text{ V}, \text{ V}_{\text{S}} \text{ shorted to the grounds} = 0 \text{ V}, \text{ V}_{\text{DD}} = 0 \text{ V}$				5	μA
IN_LEAK_LOSS_OF_VS	input INx under loss of V <sub>S</sub> condition	0 V = V <sub>INX</sub> = 24 V,					
		0 v = v <sub>INx</sub> = 24 v,					
IN_LEAK_LOSS_OF_VS		$I_{\text{/INT}} = 2 \text{ mA}$				0.35	



## **Electrical Characteristics (continued)**

over operating free-air temperature range,  $V_S = 4.5 \text{ V}$  to 35 V, and  $V_{DD} = 3 \text{ V}$  to 5.5 V (unless otherwise noted)

P	ARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>SO_L</sub>	SO output low voltage	I <sub>SO</sub> = 2 mA				0.2V <sub>DD</sub>	V
V <sub>SO_H</sub>	SO output high voltage	I <sub>SO</sub> = -2 mA		0.8V <sub>DD</sub>			V
V <sub>IN_L</sub>	SI, SCLK, and CS input low voltage					0.3V <sub>DD</sub>	V
V <sub>IN_H</sub>	SI, SCLK, and CS input high voltage			0.7V <sub>DD</sub>			V
V <sub>RESET_L</sub>	RESET input low voltage					0.8	V
V <sub>RESET_H</sub>	RESET input high voltage			1.6			V
R <sub>RESET_25</sub>	RESET pin internal	V <sub>RESET</sub> = 0 to 5.5	V, T <sub>A</sub> =25°C	0.85	1.25	1.7	MO
R <sub>RESET</sub>	pull-down resistor	V <sub>RESET</sub> = 0 to 5.5	<sub>ESET</sub> = 0 to 5.5V, T <sub>A</sub> = -40° to 125°C			2.1	МΩ
SWITCH INPUT A	ND V <sub>S</sub> MEASUREMENT CO	NVERSION PARA	METERS				
RES	Resolution			10			Bits
			4.5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 100 $\Omega$ resistance to ground at INx	12	17	26	
		1mA setting	4.5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 300 $\Omega$ resistance to ground at INx	42	51	64	LSB
			4.5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 600 $\Omega$ resistance to ground at INx	87	102	122	
		2mA setting	$4.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}$ , 100 Ω resistance to ground at INx	28	34	45	LSB
			$4.5 \text{ V} \le \text{V}_{\text{S}} \le 35 \text{ V}$ , 300 Ω resistance to ground at INx	89	102	122	
			$4.5~\text{V} \le \text{V}_{\text{S}} \le 35~\text{V},~600~\Omega$ resistance to ground at INx	181	205	236	
		5mA setting	5 V ≤ V <sub>S</sub> ≤ 35 V, 100 $\Omega$ resistance to ground at INx	72	85	105	LSB
OUT <sub>SW</sub>	Switch input conversion output		5 V ≤ V <sub>S</sub> ≤ 35 V, 300 $\Omega$ resistance to ground at INx	223	256	296	
			5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 600 $\Omega$ resistance to ground at INx	393	512	620	
		10mA setting	6 V ≤ V <sub>S</sub> ≤ 35 V, 100 $\Omega$ resistance to ground at INx	142	171	202	LSB
			6 V ≤ V <sub>S</sub> ≤ 35 V, 250 $\Omega$ resistance to ground at INx	333	427	486	
			6 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 400 $\Omega$ resistance to ground at INx	430	683	823	
			6.5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 100 Ω resistance to ground at INx	166	256	301	
		15mA setting	6.5 V $\leq$ V <sub>S</sub> $\leq$ 35 V, 200 $\Omega$ resistance to ground at INx	325	512	582	LSB
			6.5 V $\leq$ Vs $\leq$ 35 V, 300 $\Omega$ resistance to ground at INx	450	768	879	
OUT	V <sub>S</sub> measurement	V <sub>S</sub> measurement	ts (V <sub>S</sub> ≥ 4.5V), VS_RATIO= 0 in register CONFIG		-	±2%	
OUT <sub>VS</sub>	output tolerance to full-scale range	V <sub>S</sub> measurement	ts (V <sub>S</sub> ≥ 4.5V), VS_RATIO= 1 in register CONFIG			±2%	
	-	INx measuremer	nts		6		
$V_{FSR}$	Input full-scale range	V <sub>S</sub> measurements (V <sub>S</sub> ≥ 4.5V), VS_RATIO= 0 in register CONFIG			9		V
		V <sub>S</sub> measurement	ts (V <sub>S</sub> ≥ 4.5V), VS_RATIO= 1 in register CONFIG		30		
R <sub>IN, SC</sub>	Input resistance	INx measuremen	nts		240		kΩ
		INx measuremen	nts		2		
R <sub>RATIO</sub>	Input voltage divider factor <sup>(1)</sup>	V <sub>S</sub> measurement	ts ( $V_S \ge 4.5 \text{ V}$ ), $VS\_RATIO = 0$ in register		3		-
		V <sub>S</sub> measurement	ts (V <sub>S</sub> ≥ 4.5 V), VS_RATIO = 1 in register		10		-



## **Electrical Characteristics (continued)**

over operating free-air temperature range,  $V_S = 4.5 \text{ V}$  to 35 V, and  $V_{DD} = 3 \text{ V}$  to 5.5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP MAX	UNIT
COMPARATOR PARAMETERS					
V <sub>TH_ COMP_2V</sub>	Comparator threshold for 2 V	THRES_COMP = 2 V	1.85	2.25	V
V <sub>TH_ COMP_2p7V</sub>	Comparator threshold for 2.7 V	THRES_COMP = 2.7 V	2.4	2.9	V
V <sub>TH_ COMP_3V</sub>	Comparator threshold for 3 V	THRES_COMP = 3 V	2.85	3.3	V
V <sub>TH_ COMP_4V</sub>	Comparator threshold for 4 V	THRES_COMP = 4 V	3.7	4.35	V
		THRES_COMP = 2 V	4.5		
V	Minimum V <sub>S</sub>	THRES_COMP = 2.7 V	5		V
V <sub>S_COMP</sub>	requirement for proper detection	THRES_COMP = 3 V	5.5		
		THRES_COMP = 4 V	6.5		
		THRES_COMP = 2 V	30	130	
R <sub>IN, COMP</sub>	Comparator	THRES_COMP = 2.7 V	35	130	1.0
	equivalent input resistance	THRES_COMP = 3 V	35	105	kΩ
		THRES_COMP = 4 V	43	95	



## 6.6 Timing Requirements

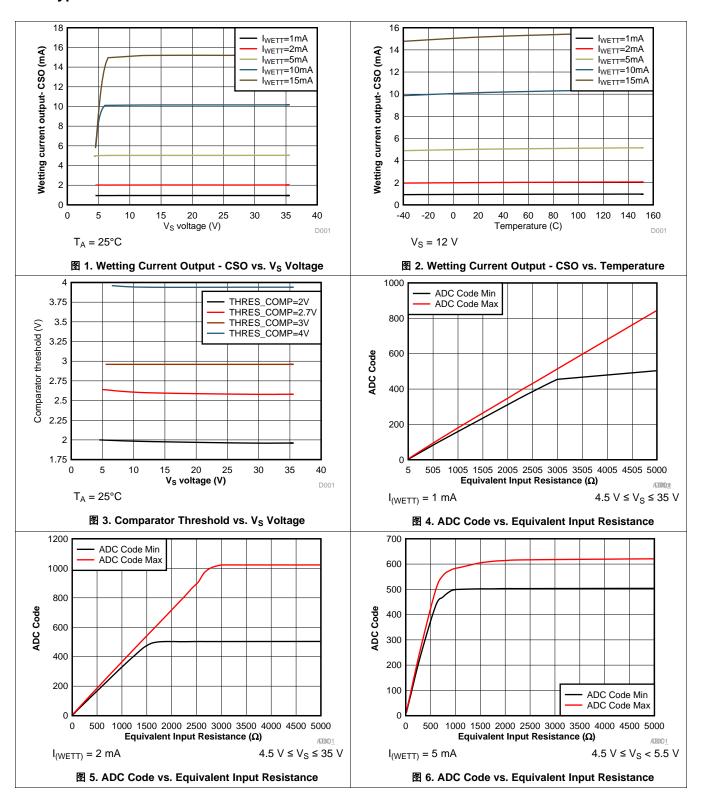
 $V_S$ = 4.5 V to 35 V,  $V_{DD}$ = 3 V to 5.5 V, and 10 pF capacitive load on SO unless otherwise noted; verified by design and characterization

	PARAMETER	TEST CONDITION	MIN	NOM	MAX	UNIT
SWITCH N	MONITORING, INTERRUPT, STARTUP AND RESET					
t <sub>POLL_ACT</sub>	Polling active time accuracy	Polling mode	-12%		12%	
t <sub>POLL_ACT</sub>	Polling active time accuracy for matrix inputs	Polling mode with matrix enabled	-12%		12%	
t <sub>POLL</sub>	Polling time accuracy	Polling mode	-12%		12%	
$t_{COMP}$	Comparator detection time			18		μs
t <sub>ADC</sub>	ADC Conversion time	Sample and hold time included		24		μs
t <sub>CCP_TRAN</sub>	Transition time between last input sampling and start of clean current			20		μs
t <sub>CCP_ACT</sub>	Clean current active time		-12%		12%	
t <sub>STARTUP</sub>	Polling startup time		200	300	400	μs
t <sub>INT_ACTIV</sub>	Active INT assertion duration		1.5	2	2.5	ms
t <sub>INT_INACT</sub>	INT de-assertion duration during a pending interrupt		3	4	5	ms
t <sub>INT_IDLE</sub>	Interrupt idle time		80	100	120	μs
t <sub>RESET</sub>	Time required to keep the RESET pin high to successfully reset the device (no pending interrupt) (1)		2			μs
t <sub>REACT</sub>	Delay between a fault event (OV, UV, TW, or TSD) to a high to low transition on the INT pin	See 图 13 for OV example.			20	μs
SPI INTER	FACE					
$t_{LEAD}$	Falling edge of $\overline{\text{CS}}$ to rising edge of SCLK setup time		100			ns
$t_{LAG}$	Falling edge of SCLK to rising edge of $\overline{\text{CS}}$ setup time		100			ns
$t_{SU}$	SI to SCLK falling edge setup time		30			ns
t <sub>HOLD</sub>	SI hold time after falling edge of SCLK		20			ns
$t_{VALID}$	Time from rising edge of SCLK to valid SO data				70	ns
t <sub>SO(EN)</sub>	Time from falling edge of $\overline{\text{CS}}$ to SO low-impedance				60	ns
t <sub>SO(DIS)</sub>	Time from rising edge of $\overline{\text{CS}}$ to SO high-impedance	Loading of 1 k $\Omega$ to GND. See $\[ \mathbb{R} \]$ 14.			60	ns
$t_R$	SI, $\overline{\text{CS}}$ , and SCLK signals rise time			5	30	ns
t <sub>F</sub>	SI, $\overline{\text{CS}}$ , and SCLK signals fall time			5	30	ns
t <sub>INTER_FR</sub> AME	Delay between two SPI communication ( $\overline{\text{CS}}$ low) sequences		1.5			μs
t <sub>CKH</sub>	SCLK High time		120			ns
t <sub>CKL</sub>	SCLK Low time		120			ns
t <sub>INITIATION</sub>	Delay between valid V <sub>DD</sub> voltage and initial SPI communication		45			μs

<sup>(1)</sup> If there is a pending interrupt (/INT pin asserted low), it can take up to 1ms for the device to complete the reset.

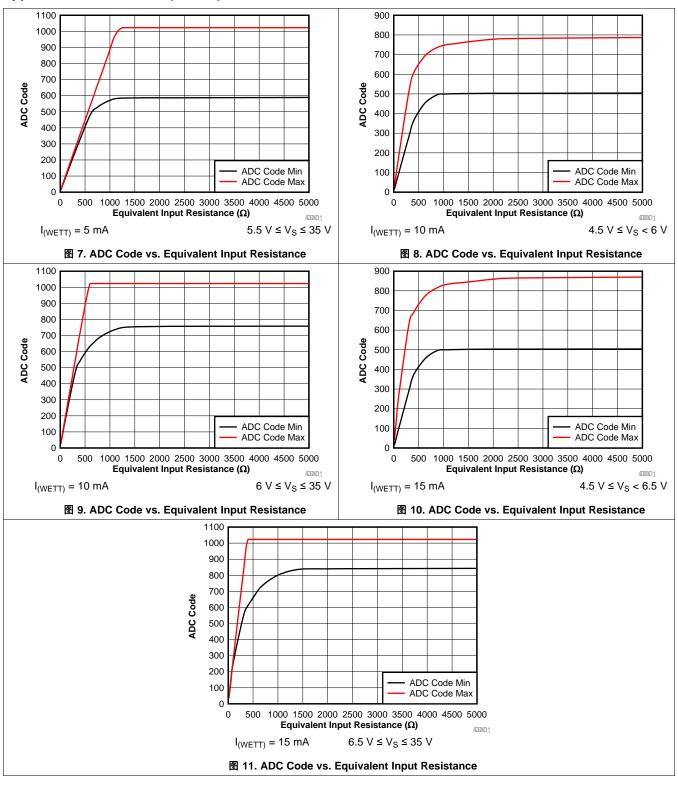


## 6.7 Typical Characteristics



## TEXAS INSTRUMENTS

## Typical Characteristics (接下页)





## 7 Parameter Measurement Information

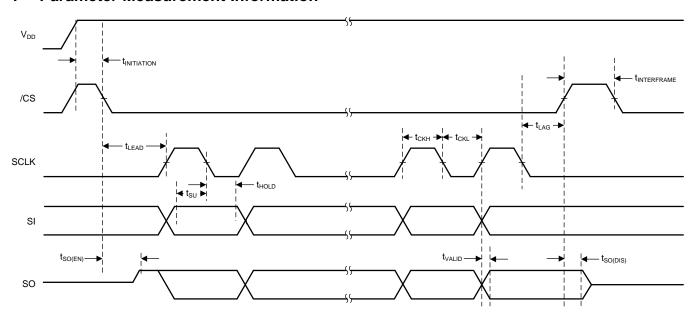


图 12. SPI Timing Parameters

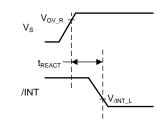


图 13.  $t_{REACT}$  Timing Parameters

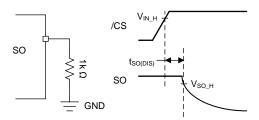


图 14.  $t_{SO(DIS)}$  Timing Parameters



## 8 Detailed Description

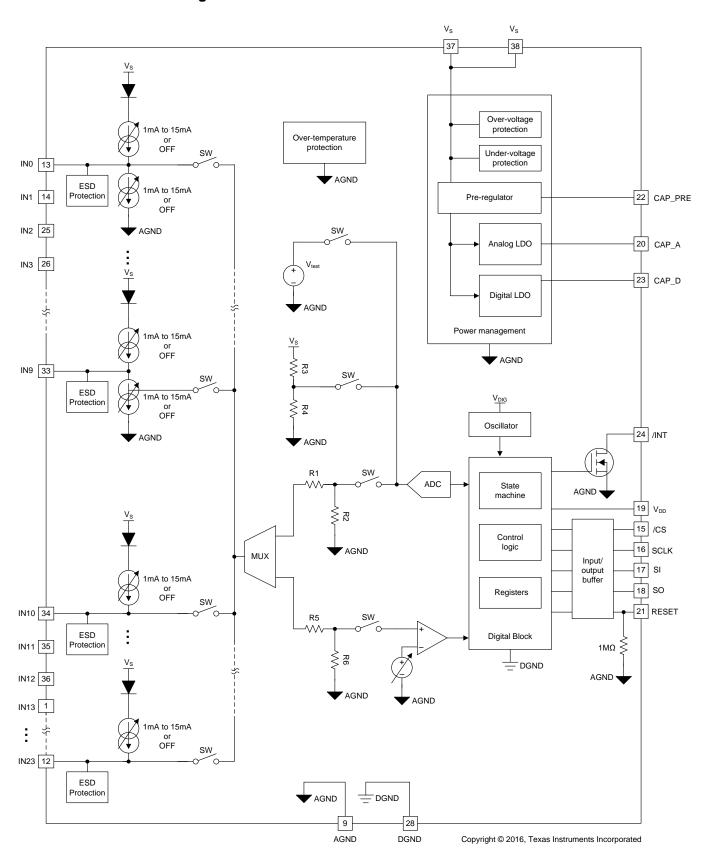
#### 8.1 Overview

The TIC12400-Q1 is an advanced 24-input Multiple Switch Detection Interface (MSDI) device designed to detect external mechanical switch status in a 12-V automotive system by acting as an interface between the switches and the low-voltage microcontroller. The TIC12400-Q1 is an integrated solution that replaces many discrete components and provides integrated protection, input serialization, and system wake-up capability.

The device monitors 14 switches to GND and 10 additional switches that can be programmed to be connected to either GND or  $V_{BAT}$ . It features SPI interface to report individual switch status and provides programmability to control the device operation. The TIC12400-Q1 features a 10-bit ADC which is useful to monitor analog inputs such as resistor coded switches that have multiple switching positions. To monitor only digital switches, an integrated comparator can be used instead to monitor the input status. The device has 2 modes of operation: continuous mode and polling mode. The polling mode is a low-power mode that can be activated to reduce current drawn in the system by only turning on the wetting current for a small duty cycle to detect switch status changes. An interrupt is generated upon detection of switch status change and it can be used to wake up the microcontroller to bring the entire system back to operation.



## 8.2 Functional Block Diagram





## 8.3 Feature Description

## 8.3.1 V<sub>S</sub> Pin

The V<sub>S</sub> supply provides power to the entire chip and it is designed to be connected directly to a 12-V automotive battery via a reverse-polarity blocking diode.

## 8.3.2 V<sub>DD</sub> Pin

The  $V_{DD}$  supply is used to determine the logic level <u>on</u> the SPI communication interface, source the current for the SO driver, <u>and</u> sets the pull-up voltage for the  $\overline{CS}$  pin. It can also be used as a possible external pull-up supply for the  $\overline{INT}$  pin in addition to the  $V_S$  and it shall be connected to a 3 V to 5.5-V logic supply. Removing  $V_{DD}$  from the device disables SPI communications but does not reset the register configurations.

#### 8.3.3 Device Initialization

When the device is powered up for the first time, the condition is called Power-On Reset (POR), which sets the registers to their default values and initializes the device state machine. The internal POR controller holds the device in a reset condition until  $V_S$  has reached  $V_{POR\_R}$ , at which the reset condition is released with the device registers and state machine initialized to their default values. After the initialization process is completed, the  $\overline{INT}$  pin is asserted low to notify the microcontroller, and the register bit POR in the  $\overline{INT\_STAT}$  register is asserted to logic 1. The SPI flag bit POR is also asserted at the SPI output (SO).

During device initialization, factory settings are programmed into the device to allow accurate device operation. The device performs a self-check after the device is programmed to ensure correct settings are loaded. If the self-check returns an error, the CHK\_FAIL bit in the INT\_STAT register will be flagged to logic 1 along with the POR bit. If this event occurs the microcontroller is recommended to initiate software reset (see section *Software Reset*) to re-initialize the device to allow the correct settings to be re-programmed.

#### 8.3.4 Device Trigger

After device initialization, the TIC12400-Q1 is ready to be configured. The microcontroller can use SPI commands to program desired settings to the configuration registers. Once the device configuration is completed, the microcontroller is required to set the bit TRIGGER in the CONFIG register to logic 1 in order to activate wetting current and start external switch monitoring.

After switch monitoring initiates, the configuration registers turn into read-only registers (with the exception of the TRIGGER, CRC\_T, and RESET bits in the CONFIG register and all bits in the CCP\_CFG1 register). If at any time the device setting needs to be re-configured, the microcontroller is required to first set the bit TRIGGER in the CONFIG register to logic 0 to stop wetting current and switch monitoring. The microcontroller can then program configuration registers to the desired settings. Once the re-configuration is completed the microcontroller can set the TRIGGER bit back to logic 1 to re-start switch monitoring.

Note the cyclic redundancy check (CRC) feature stays accessible when TRIGGER bit is in logic 1, allowing the microcontroller to verify device settings at all time. Refer to section *Cyclic Redundancy Check (CRC)* for more details of the CRC feature.

#### 8.3.5 Device Reset

There are 3 ways to reset the TIC12400-Q1 and re-initialize all registers to their default values:

## 8.3.5.1 $V_S$ Supply POR



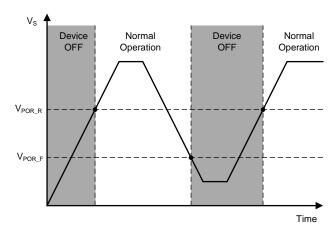


图 15. V<sub>S</sub> is Lowered Below The POR threshold, Then Ramped Back Up To Complete A POR Cycle

#### 8.3.5.2 Hardware Reset

Microcontroller can toggle the RESET pin to perform a hardware reset to the device. The RESET pin is internally pulled-down via a resistor (1.25M $\Omega$  typical) and must be kept low for normal operation. When the RESET pin is toggled high, the device enters the reset state with most of the internal blocks turned off and consumes very little current of  $I_{S\_RESET}$ . Switch monitoring and SPI communications are stopped in the reset state, and all register contents are cleared. When RESET pin is toggled back low, all the registers are set to their default values and the device state machine is re-initialized, similar to a POR event. When the re-initialization process is completed the  $\overline{INT}$  pin is asserted low, and the interrupt register bit POR and the SPI status flag POR are both asserted to notify the microcontroller that the device has completed the reset process.

Note in order to successfully reset the device, the RESET pin needs to be kept high for a minimum duration of  $t_{RESET}$ . The pin is required to be driven with a stable input (below  $V_{RESET\_L}$  for logic low or above  $V_{RESET\_H}$  for logic H) to prevent the device from accidental reset.

#### 8.3.5.3 Software Reset

In addition to hardware reset the microcontroller can also issue a SPI command to initiate software reset. Software reset is triggered by setting the RESET bit in the register CONFIG to logic 1, which re-initializes the device with all registers set to their default values. Once the re-initialization process is completed, the  $\overline{\text{INT}}$  pin is asserted low, and the interrupt register bit POR and the SPI status flag POR are both asserted to notify the microcontroller that the device has completed the reset process.

## 8.3.6 V<sub>S</sub> Under-Voltage (UV) Condition

During normal operation of a typical 12V automotive system, the  $V_S$  voltage is usually quite stable and stays well above 11 V. However, the  $V_S$  voltage might drop temporarily during certain vehicle operations, such as cold cranking. If the  $V_S$  voltage drops below  $V_{UV\_F}$ , the TIC12400-Q1 enters the under-voltage (UV) condition since there is not enough voltage headroom for the device to accurately generate wetting currents. The following describes the behavior of the TIC12400-Q1 under UV condition:

- 1. All current sources/sinks de-activate and switch monitoring stops.
- 2. Interrupt is generated by asserting the INT pin low and the bit UV in the interrupt register (INT\_STAT) is flagged to logic 1. The bit UV\_STAT is asserted to logic 1 in the register IN\_STAT\_MISC. The OI SPI flag is asserted during any SPI transactions. The INT pin is released and the interrupt register (INT\_STAT) is cleared on the rising edge of CS provided that the interrupt register has been read during the SPI transaction.
- 3. SPI communication stays active, and all register settings stay intact without resetting. Previous switch status, if needed, can be retrieved without interruption.
- 4. The device continues to monitor the V<sub>S</sub> voltage, and the UV condition sustains if the V<sub>S</sub> voltage continues to stay below V<sub>UV R</sub>. No further interrupt is generated once cleared.



Note the device resets as described in section VS Supply POR if the V<sub>S</sub> voltage drops below V<sub>POR\_F</sub>.

When the  $V_S$  voltage rises above  $V_{UV\_R}$ , the  $\overline{INT}$  pin is asserted low to notify the microcontroller that the UV condition no longer exists. The UV bit in the register INT\_STAT is flagged to logic 1 and the bit UV\_STAT bit is de-asserted to logic 0 in the register IN\_STAT\_MISC to reflect the clearance of the UV condition. The device resumes operation using current register settings (regardless of the  $\overline{INT}$  pin and SPI communication status) with polling restarted from the first enabled channel. The Switch State Change (SSC) interrupt is generated at the end of the first polling cycle and the detected switch status becomes the baseline switch status for subsequent polling cycles. The content of the  $\overline{INT}$  register, once read by the microcontroller, is cleared, and the  $\overline{INT}$  pin is released afterwards.

The following diagram describes the TIC12400-Q1 operation at various different  $V_S$  voltages. If the  $V_S$  voltage stays above  $V_{UV\_F}$  (Case 1), the device stays in normal operation. If the  $V_S$  voltage drops below  $V_{UV\_F}$  but stays above  $V_{POR\_F}$  (Case 2), the device enters the UV condition. If  $V_S$  voltage drops below  $V_{POR\_F}$  (Case 3), the device resets and all register settings are cleared. The microcontroller is then required to re-program all the configuration registers in order to resume normal operation after the  $V_S$  voltage recovers.

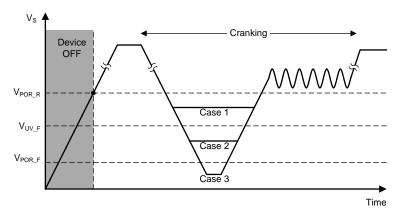


图 16. TIC12400-Q1 Operation At Various V<sub>S</sub> Voltage Levels

## 8.3.7 V<sub>S</sub> Over-Voltage (OV) Condition

If  $V_S$  voltage rises above  $V_{OV\_R}$ , the TIC12400-Q1 enters the over-voltage (OV) condition to prevent damage to internal structures of the device on the  $V_S$  and INx (for battery-connected switches) pins. The following describes the behavior of the TIC12400-Q1 under OV condition:

- 1. All current sources/sinks de-activate and switch monitoring stops.
- 2. Interrupt is generated by asserting the  $\overline{\text{INT}}$  pin low and the bit OV in the interrupt register (INT\_STAT) is flagged to logic 1. The bit OV\_STAT is asserted to logic 1 in the register IN\_STAT\_MISC. The OI SPI flag is asserted during any SPI transactions. The  $\overline{\text{INT}}$  pin is released and the interrupt register (INT\_STAT) is cleared on the rising edge of  $\overline{\text{CS}}$  provided that the interrupt register has been read during the SPI transaction.
- 3. SPI communication stays active, and all register settings stay intact without resetting. Previous switch status, if needed, can be retrieved without any interruption.
- The device continues to monitor the V<sub>S</sub> voltage, and the OV condition sustains if the V<sub>S</sub> voltage continues to stay above V<sub>OV\_R</sub>- V<sub>OV\_HYST</sub>. No further interrupt is generated once cleared.

When the  $V_S$  voltage drops below  $V_{OV\_R}$  -  $V_{OV\_HYST}$ , the  $\overline{INT}$  pin is asserted low to notify the microcontroller that the over-voltage condition no longer exists. The OV bit in the register INT\_STAT is flagged to logic 1 and the bit OV\_STAT bit is de-asserted to logic 0 in the register IN\_STAT\_MISC to reflect the clearance of the OV condition. The device resumes operation using current register settings (regardless of the  $\overline{INT}$  pin and SPI communication status) with polling restarted from the first enabled channel. The Switch State Change (SSC) interrupt is generated at the end of the first polling cycle and the detected switch status becomes the baseline status for subsequent polling cycles. The content of the INT\_STAT register, once read by the microcontroller, is cleared and the  $\overline{INT}$  pin is released afterwards.



## 8.3.8 Switch Inputs Settings

IN0 to IN23 are inputs connected to external mechanical switches. The switch status of each input, whether open or closed, is indicated by the status registers. 表 1 below describes various settings that can be configured for each input. Note some settings are shared between multiple inputs. It is required to first stop device operation by setting the TRIGGER bit low in the register CONFIG before making any configuration changes, as described in *Device Trigger*.

表 1. TIC12400-Q1 Wetting Current and Threshold Setting Details

	Threshold				Current Source (CSC) /	Supported Suitab	
Input	Comparator Input Mode ADC Input Mode		nput Mode	Wetting Current	Current Source (CSO) / Current Sink (CSI)	Supported Switch Type	
IN0		THRES0 to THRES7		VA/C INIO INIA	CSO CSI	Switch to GND Switch to VBAT	
IN1	THRES_COMP_IN	THRES0 to THRES7		WC_IN0_IN1	CSO CSI	Switch to GND Switch to VBAT	
IN2	0_IN3	0_IN3 THRES0 to THRES7	WC IND IND	CSO CSI	Switch to GND Switch to VBAT		
IN3		THRES0 to THRES7		WC_IN2_IN3	CSO CSI	Switch to GND Switch to VBAT	
IN4		THRES0 to THRES7		WC_IN4	CSO CSI	Switch to GND Switch to VBAT	
IN5	THRES_COMP_IN	THRES0 to THRES7	TUDES COM	WC_IN5	CSO CSI	Switch to GND Switch to VBAT	
IN6	4_IN7	THRES0 to THRES7	THRES_COM	M/C INIC INIT	CSO CSI	Switch to GND Switch to VBAT	
IN7		THRES0 to THRES7		WC_IN6_IN7	CSO CSI	Switch to GND Switch to VBAT	
IN8	THRES_COMP_IN 8_IN11	THRES0 to THRES7		WO INIO INIO	CSO CSI	Switch to GND Switch to VBAT	
IN9		THRES0 to THRES7		WC_IN8_IN9	CSO CSI	Switch to GND Switch to VBAT	
IN10		THRES0 to THRES7		WC_IN10	cso	Switch to GND	
IN11		THRES0 to THRES7		WC_IN11	cso	Switch to GND	
IN12			IRES2A IRES2B	WO IN40 40	cso	Switch to GND	
IN13	THRES_COMP_IN		IRES2A IRES2B	WC_IN12_13	CSO	Switch to GND	
IN14	12_IN15		IRES2A IRES2B	WO 1814 4 45	cso	Switch to GND	
IN15			IRES2A IRES2B	WC_IN14_15	cso	Switch to GND	
IN16			IRES2A IRES2B	WO INIAC AT	cso	Switch to GND	
IN17			IRES2A IRES2B	WC_IN16_17	cso	Switch to GND	
IN18	THRES_COMP_IN 16_IN19	TH	IRES3A IRES3B IRES3C	WC IN18 19	CSO	Switch to GND	
IN19		THRES3A THRES3B THRES3C		440 <sup>-</sup> 11410 <sup>-</sup> 13	cso	Switch to GND	



## 表 1. TIC12400-Q1 Wetting Current and Threshold Setting Details (接下页)

	Threshold			Current Source (CSO) /	Supported Switch
Input	Comparator Input Mode	ADC Input Mode	Wetting Current	Current Sink (CSI)	Туре
IN20		THRES3A THRES3B THRES3C		CSO	Switch to GND
IN21		THRES3A THRES3B THRES3C	WC_IN20_21	CSO	Switch to GND
IN22	THRES_COMP_IN 20_IN23	THRES3A THRES3B THRES3C	WC_IN22	CSO	Switch to GND
IN23		THRES3A THRES3B THRES3C THRES8 THRES9	WC_IN23	cso	Switch to GND

#### 8.3.8.1 Input Current Source/Sink Selection

Among the 24 inputs, IN10 to IN23 are intended for monitoring only ground-connected switches and are connected to current sources. IN0 to IN9 can be programmed to monitor either ground-connected switches or battery-connected switches by configuring the *CS\_SELECT* register. The default configuration of the IN0-IN9 inputs after POR is to monitor ground-connected switches (current sources are selected). To set an input to monitor battery-connected switches, set the corresponding bit to logic 1.

#### 8.3.8.2 Input Mode Selection

The TIC12400-Q1 has a built-in ADC and a comparator that can be used to monitor resistor coded switches or digital switches. Digital switch inputs have only two states, either open or closed, and can be adequately detected by a comparator. Resistor coded switches may have multiple positions that need to be detected and an ADC is appropriate to monitor the different states. Each input of the TIC12400-Q1 can be individually programmed to use either a comparator or an ADC by configuring the appropriate bits in the MODE register depending on the knowledge of the external switch connections. The benefit of using a comparator instead of an ADC to monitor digital switches is its reduced polling time which translates to overall power saving when the device operates in the low-power polling mode.

Comparator input mode is selected by default for all enabled inputs upon device reset.

## 8.3.8.3 Input Enable Selection

The TIC12400-Q1 provides switch status monitoring for up to 24 inputs, but there might be circumstances in which not all inputs need to be constantly monitored. The microcontroller may choose to enable/disable monitoring of certain inputs by configuring the *IN\_EN* register. Setting the corresponding bit to logic 0 deactivates the wetting current source/sink and stops switch status monitoring for the input. Disabling monitoring of unused inputs reduces overall power consumption of the device.

All inputs are disabled by default upon device reset.



#### 8.3.8.4 Thresholds Adjustment

When an input is configured as comparator input mode, the threshold level for interrupt generation can be programmed by setting the *THRES\_COMP* register. The threshold level settings can be set for each individual input groups and each group consists of 4 inputs. Four threshold levels are available: 2V, 2.7V, 3V, and 4V.

When an input is configured as ADC input mode the threshold level for interrupt generation can be configured up to 1023 different levels by setting the *THRES\_CFG1* to *THRES\_CFG2* registers. One threshold level can be programmed individually for each of the inputs from IN0 to IN11. Additionally, one common threshold, shared between inputs IN0 to IN11, can be programmed by configuring the THRES\_COM bits in register *MATRIX*. The common threshold acts independently from the threshold THRES0 to THRES7. Inputs IN12 to IN17 use 2 preset threshold levels (THRES2A and THRES2B). Inputs 18 to 22 use 3 preset threshold levels (THRES3A, THRES3B, and THRES3C). Input 23 uses 5 preset threshold levels (THRES3A, THRES3B, THRES3C, THRES8 and THRES9).

When multiple threshold settings are used for ADC inputs, the thresholds levels need to be configured properly. Use the rules below (see  $\frac{1}{2}$  2) when setting up the threshold levels:

	•
INPUT	PROPER THRESHOLD CONFIGURATION
IN12 to IN17	THRES2B ≥ THRES2A
IN18 to IN22	THRES3C ≥ THRES3B ≥ THRES3A
IN23	THRES9 ≥ THRES8 ≥ THRES3C ≥ THRES3B ≥ THRES3A

表 2. Proper Threshold Configuration For ADC Inputs

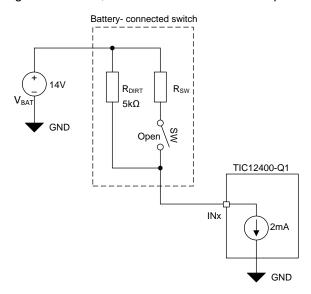


图 17. Example Showing The Calculation of The INx Pin Voltage For A Leaky Battery-Connected Switch

It is possible to configure an input to ADC input mode, instead of comparator input mode, to monitor single-threshold digital switches. The following programming procedure is recommended under such configuration:



## 表 3. Recommended Threshold Configuration When Using An ADC Input To Monitor Digital Switches

INPUT	RECOMMENDED THRESHOLD CONFIGURATION
IN0 to IN11	Configure the desired threshold to one of the settings from THRES0 to THRES7 and map it accordingly
IN12 to IN17	<ul> <li>Configure the desired threshold to THRES2B</li> <li>Set THRES2A to the same code as THRES2B</li> <li>Disable interrupt generation for THRES2A by configuring the INT_EN_CFG1 or INT_EN_CFG2 register.</li> </ul>
IN18 to IN22	<ul> <li>Configure the desired threshold to THRES3C</li> <li>Set THRES3A and THRES3B to the same code as THRES3C.</li> <li>Disable interrupt generation for THRES3A and THRES3B by configuring the INT_EN_CFG3 or INT_EN_CFG4 register.</li> </ul>
IN23	<ul> <li>Configure the desired threshold to THRES9</li> <li>Set THRES3A, THRES3B, THRES3C, and THRES8 to the same code as THRES9.</li> <li>Disable interrupt generation for THRES3A, THRES3B, THRES3C, and THRES8 by configuring the INT_EN_CFG4 register.</li> </ul>

#### 8.3.8.5 Wetting Current Configuration

There are 6 different wetting current settings (0 mA, 1 mA, 2 mA, 5 mA, 10 mA, and 15mA) that can be programmed by configuring the *WC\_CFG0* and WC\_CFG1 registers. 0 mA is selected by default upon device reset.

To monitor resistor coded switches, a lower wetting current setting (1 mA, 2 mA, or 5 mA) is generally desirable to get the resolution needed to resolve different input voltages while keeping them within the ADC full-scale range (0 V to 6 V). Higher wetting current settings (10mA and 15mA) are useful to clean switch contact oxidation that may form on the surface of an open switch contact. If switch contact cleaning is required for resistor coded switches, the clean current polling (CCP) feature (Refer to section *Clean Current Polling (CCP)* ) can be activated to generate short cleaning pulses periodically using higher wetting current settings at the end of every polling cycle.

The accuracy of the wetting current has stronger dependency on the  $V_S$  voltage when  $V_S$  voltage is low. The lower the  $V_S$  voltage falls, the more deviation on the wetting currents from their nominal values. Refer to  $I_{WETT}$  (CSO) and  $I_{WETT}$  (CSO) specifications for more details.

## 8.3.9 Interrupt Generation and INT Assertion

The INT pin is an active-low, open-drain output that asserts low when an event (switch input state change, temperature warning, over-voltage shutdown…etc) is detected by the TIC12400-Q1. An external pull-up resistor to V<sub>DD</sub> is needed on the INT pin (see 图 18). The INT pin can also be connected directly to a 12-V automotive battery to support the microcontroller wake-up feature, as describe in section *Microcontroller Wake-Up*.

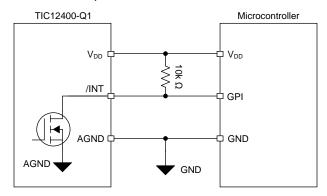


图 18. INT Connection Example #1



#### 8.3.9.1 INT Pin Assertion Scheme

TIC12400-Q1 supports two configurable schemes for  $\overline{\text{INT}}$  assertion: static and dynamic. The scheme can be adjusted by configuring the INT\_CONFIG bit in the *CONFIG* register.

If the static  $\overline{\text{INT}}$  assertion scheme is used (INT\_CONFIG = 0 in the CONFIG register), the  $\overline{\text{INT}}$  pin is asserted low upon occurrence of an event. The  $\overline{\text{INT}}$  pin is released on the rising edge of  $\overline{\text{CS}}$  only if a READ command has been issued to read the INT\_STAT register while  $\overline{\text{CS}}$  is low, otherwise the  $\overline{\text{INT}}$  will be kept low indefinitely. The content of the INT\_STAT interrupt register is latched on the first rising edge of SCLK after  $\overline{\text{CS}}$  goes low for every SPI transaction, and the content is cleared upon a READ command issued to the INT\_STAT register, as illustrated in  $\overline{\mathbb{S}}$  19.

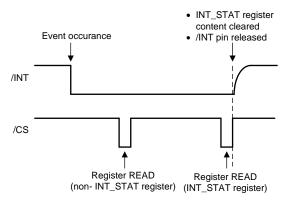


图 19. Static INT Assertion Scheme

In some system implementations an edge-triggered based microcontroller might potentially miss the  $\overline{\text{INT}}$  assertion if it is configured to the static scheme, especially when the microcontroller is in the process of waking up. To prevent missed  $\overline{\text{INT}}$  assertion and improve robustness of the interrupt behavior, the TIC12400-Q1 provides the option to use the dynamic assertion scheme for the  $\overline{\text{INT}}$  pin. When the dynamic scheme is used (INT\_CONFIG= 1 in the CONFIG register), the  $\overline{\text{INT}}$  pin is asserted low for a duration of  $t_{\text{INT\_ACTIVE}}$  and is deasserted back to high if the INT\_STAT register has not been read after  $t_{\text{INT\_ACTIVE}}$  has elapsed. The  $\overline{\text{INT}}$  pin continues to toggle until the INT\_STAT register is read.

If the INT\_STAT register is read when INT pin is asserted low, the INT pin is released on the READ command's CS rising edge and the content of the INT\_STAT register is also cleared, as shown in ₹ 20. If the INT\_STAT register is read when INT pin is de-asserted, the content of the INT\_STAT register is cleared on the READ command's CS rising edge, and the INT pin is not re-asserted back low, as shown in ₹ 21.

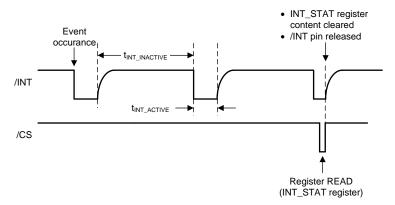


图 20. Dynamic INT Assertion Scheme With INT\_STAT Register Read During t<sub>INT\_ACTIVE</sub>



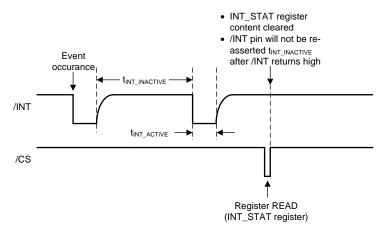


图 21. Dynamic INT Assertion Scheme With INT\_STAT Register Read During t<sub>INT INACTIVE</sub>

The static  $\overline{\text{INT}}$  assertion scheme is selected by default upon device reset. The  $\overline{\text{INT}}$  pin assertion scheme can only be changed when bit TRIGGER is logic 0 in the CONFIG register.

## 8.3.9.2 Interrupt Idle Time (t<sub>INT IDLE</sub>) Time

Interrupt idle time (t<sub>INT IDLE</sub>) is implemented in TIC12400-Q1 to:

- Allow the INT pin enough time to be pulled back high by the external pull-up resistor and allow the next assertion to be detectable by an edge-triggered microcontroller.
- Minimize the chance of glitching on the INT pin if back-to-back events occur.

When there is a pending interrupt event and the interrupt event is not masked,  $t_{\text{INT\_IDLE}}$  is applied after the READ command is issued to the INT\_STAT register. If another event occurs during the interrupt idle time the INT\_STAT register content is updated instantly but the INT pin is not asserted low until  $t_{\text{INT\_IDLE}}$  has elapsed. If another READ command is issued to the INT\_STAT register during  $t_{\text{INT\_IDLE}}$ , the INT\_STAT register content is cleared immediately, but the INT pin is not re-asserted back low after  $t_{\text{INT\_IDLE}}$  has elapsed. An example of the interrupt idle time is given below to illustrate the INT pin behavior under the static INT assertion schemes:

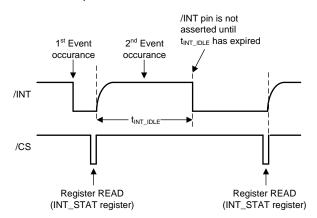


图 22. INT Assertion Scheme With t<sub>INT IDLE</sub>

## 8.3.9.3 Microcontroller Wake-Up

Using a few external components, the INT pin can be used for wake-up purpose to activate a voltage regulator via its inhibit inputs. An implementation example is shown in ₹ 23. This implementation is especially useful for waking up a microcontroller in sleep mode to allow significant system-level power savings.



Before the wake-up event, the  $\overline{\text{INT}}$  pin is in high impedance state on the TIC12400-Q1. The microcontroller can be kept in sleep state with all its GPIOs in logic low. Hence, Q2 remains off with its based in logic low state and the base of Q1 is weakly pulled-high to the  $V_S$  level. This causes Q1 to remain off, and the LDO\_EN signal is pulled-down to logic low to disable the regulator's output.  $V_{DD}$  is therefore unavailable to both the TIC12400-Q1 device and the microcontroller and SPI communication is not supported. Switch status monitoring, however, is still active in the TIC12400-Q1.

When an event (switch status change, temperature warning, or O V...and so on) occurs, the  $\overline{\text{INT}}$  pin is asserted low by TIC12400-Q1, causing Q1 to turn on to activate the voltage regulator. The microcontroller is then reactivated, and the communication between the microcontroller and the TIC12400-Q1 is reestablished. The microcontroller can then access stored event information using SPI communication. Note since the  $\overline{\text{INT}}$  pin is deasserted after the INT\_STAT register is read, the microcontroller is required to keep the regulator on by driving the  $\mu\text{C}_{\text{LDO}}$ EN signal high. This allows  $V_{\text{DD}}$  to stay high to provide power to the microcontroller and support SPI communications.

The wake-up implementation is applicable only when the device is configured to use the static  $\overline{\text{INT}}$  assertion scheme.

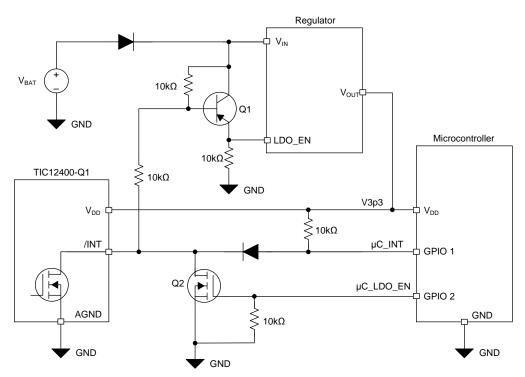


图 23. INT Connection to Support Microcontroller Wake-Up

#### 8.3.9.4 Interrupt Enable / Disable And Interrupt Generation Conditions

Each switch input can be programmed to enable or disable interrupt generation upon status change by configuring registers <code>INT\_EN\_COMP1</code> to <code>INT\_EN\_COMP2</code> (for comparator inputs) and <code>INT\_EN\_CFG1</code> to <code>INT\_EN\_CFG4</code> (for ADC inputs). Interrupt generation condition can be adjusted for THRES\_COM (for IN0-IN11) by adjusting the <code>IN\_COM\_EN</code> bit in the <code>MATRIX</code> register.

The abovementioned registers can also be used to control interrupt generation condition based on the following settings:

- Rising edge: an interrupt is generated if the current input measurement is above the corresponding threshold and the previous measurement was below.
- 2. **Falling edge:** an interrupt is generated if the current input measurement is below the corresponding threshold and the previous measurement was above.
- 3. Both edges: changes of the input voltage in either direction results in an interrupt generation.

Note interrupt generation from switch status change is disabled for all inputs by default upon device reset.



#### 8.3.9.5 Detection Filter

When monitoring the switch input status a detection filter can be configured by setting the DET\_FILTER bits in the *CONFIG* register to generate Switch Status Change (SSC) interrupt only if the same input status (w.r.t the threshold) is sampled consecutively. This detection filter can be useful to debounce inputs during a switch toggle events. Four different filtering schemes are available:

- 1. Generate an SSC interrupt if the voltage level at an input crossed its threshold
- 2. Generate an SSC interrupt if the voltage level at an input crossed its threshold and the status is stable (w.r.t. the threshold) for at least 2 consecutive polling cycles
- 3. Generate an SSC interrupt if the voltage level at an input crossed its threshold and the status is stable (w.r.t. the threshold) for at least 3 consecutive polling cycles
- 4. Generate an SSC interrupt if the voltage level at an input crossed its threshold and the status is stable (w.r.t. the threshold) for at least 4 consecutive polling cycles

The default value of switch status is stored internally after the 1st detection cycle, even if detection filter (by configure the DET\_FILTER in the CONFIG register) is used. An example is illustrated below with the assumption that DET\_FILTER in register CONFIG is set to 11 (SSC interrupt is generated if the input crosses the threshold and the status is stable w.r.t. the threshold for at least 4 consecutive detection cycles). Assume switch status change is detected in the 3rd detection cycle and stays the same for the next 3 cycles.

DETECTION CYCLE	1	2	3	4	5	6
Event	Default Switch status stored	_	Switch status change detected	_	_	

The detection filter applies to all enabled inputs regardless of their input modes (ADC or comparator) selection. The detection filter counter is reset to 0 when the TRIGGER bit in the CONFIG register is de-asserted to logic 0. Upon device reset, the default setting for the detection filter is set to generating an SSC interrupt at every threshold crossing.

Note the detection filter does not apply to the common threshold THRES\_COM.

#### 8.3.10 Temperature Monitor

With multiple switch inputs are closed and high wetting current setting is enabled, considerable power could be dissipated by the device and raise the device temperature. TIC12400-Q1 has integrated temperature monitoring and protection circuitry to put the device in low power mode to prevent damage due to overheating. Two types of temperature protection mechanisms are integrated in the device: Temperature Warning (TW) and Temperature Shutdown (TSD). The triggering temperatures and hysteresis are specified in 表 4 below:

#### 表 4. Temperature Monitoring Characteristics of TIC12400-Q1

PARAMETER	MIN	TYP	MAX	UNIT
Temperature warning trigger temperature (T <sub>TW</sub> )	130	140	155	°C
Temperature shutdown trigger temperature (T <sub>TSD</sub> )	150	160	175	°C
Temperature hysteresis (T <sub>HYS</sub> ) for T <sub>TW</sub> and T <sub>TSD</sub>		15		°C

#### 8.3.10.1 Temperature Warning (TW)

When the device temperature goes above the temperature warning trigger temperature ( $T_{TW}$ ), the TIC12400-Q1 performs the following operations:

- 1. Generate an interrupt by asserting the  $\overline{\text{INT}}$  pin low and flag the TW bit in INT\_STAT register to logic 1. The TEMP bit in the SPI flag is also flagged to logic 1 for all SPI transactions.
- 2. The TW\_STAT bit of the IN\_STAT\_MISC register is flagged to logic 1.
- 3. If the TW\_CUR\_DIS\_CSO or TW\_CUR\_DIS\_CSO bit in *CONFIG* register is set to logic 0 (default), the wetting current is adjusted down to 2 mA for 10 mA or 15 mA settings. The wetting current stays at its preconfigured value if 0 mA, 1 mA, 2 mA, or 5 mA setting is used.
- 4. Maintain the low wetting current as long as the device junction temperature stays above T<sub>TW</sub> T<sub>HYS</sub>.



The  $\overline{\text{INT}}$  pin is released and the  $\overline{\text{INT}}$  register content is cleared on the rising edge of  $\overline{\text{CS}}$  provided the  $\overline{\text{INT}}$ -STAT register has been read during  $\overline{\text{CS}}$  low. The TIC12400-Q1 continues to monitor the temperature, but does not issue further interrupts if the temperature continues to stay above  $T_{\text{TW}}$ -  $T_{\text{HYS}}$ . The status bit TW\_STAT in register IN\_STAT\_MISC continues to stay at logic 1 as long as the temperature warning condition exists.

If desired, the reduction of wetting current down to 2mA setting (from 10 mA or 15 mA) can be disabled by setting the  $\underline{TW}$ \_CUR\_DIS\_CSO or  $\underline{TW}$ \_CUR\_DIS\_CSI bit in the  $\underline{CONFIG}$  register to 1. The interrupt is still generated (INT asserted low and INT\_STAT interrupt register is updated) when the temperature warning event occurs but the wetting current is not reduced. This setting applies to both the polling and continuous mode operation. Note if the feature is enabled, switch detection result might be impacted upon  $T_{TW}$  event if the wetting current is reduced to 2mA from 10mA or 15mA.

When the temperature drops below  $T_{TW}$ -  $T_{HYS}$ , the  $\overline{INT}$  pin is asserted low (if released previously) to notify the microcontroller that the temperature warning condition no longer exists. The TW bit of the interrupt register INT\_STAT is flagged logic 1. The TW\_STAT bit in the IN\_STAT\_MISC register is de-asserted back to logic 0. The device resumes operation using the current programmed settings (regardless of the  $\overline{INT}$  and  $\overline{CS}$  status).

#### 8.3.10.2 Temperature Shutdown (TSD)

After the device enters TW condition, if the junction temperature continues to rise and goes above the temperature shutdown threshold ( $T_{TSD}$ ), the TIC12400-Q1 enters the Temperature Shutdown (TSD) condition and performs the following operations:

- 1. Opens all the switches connected to the current sources/sinks to prevent any further heating due to excessive current flow.
- 2. Generate an interrupt by asserting the  $\overline{\text{INT}}$  pin (if not already asserted) low and flag the TSD bit in the INT\_STAT register to logic 1. The TEMP bit in the SPI flag is also flagged to logic 1 for all SPI transactions.
- 3. The TSD\_STAT bit of the IN\_STAT\_MISC register is flagged to logic 1. The TW\_STAT bit also stays at logic 1.
- 4. SPI communication stays on and all register settings stay intact without resetting. Previous switch status, if needed, can be retrieved without any interruption.
- 5. Maintain the setting as long as the junction temperature stays above  $T_{TSD}$   $T_{HVS}$ .

The  $\overline{\text{INT}}$  pin is released and the INT\_STAT register content is cleared on the rising edge of  $\overline{\text{CS}}$  provided the INT\_STAT register has been read during  $\overline{\text{CS}}$  low. The TIC12400-Q1 continues to monitor the temperature, but does not issue further interrupts if the temperature continues to stay above  $T_{\text{TSD}}$  -  $T_{\text{HYS}}$ . The status bit TSD\_STAT in register IN\_STAT\_MISC continues to stay at logic 1 as long as the temperature shutdown condition exists.

When the temperature drops below  $T_{TSD}$  -  $T_{HYS}$ , the  $\overline{INT}$  pin is asserted low (if released previously) to notify the microcontroller that the temperature shutdown condition no longer exists. The TSD bit of the interrupt register INT\_STAT is flagged logic 1. In the IN\_STAT\_MISC register, the TSD\_STAT bit is de-asserted back to logic 0, while the TW\_STAT bit stays at logic 1. The device resumes operation using the wetting current setting described in section *Temperature Warning* if the temperature stays above  $T_{TW}$  -  $T_{HYS}$ . Note the polling restarts from the first enabled channel and the SSC interrupt is generated at the end of the first polling cycle. The detected switch status from the first polling cycle becomes the default switch status for subsequent polling.

#### 8.3.11 Parity Check And Parity Generation

The TIC12400-Q1 uses parity bit check to ensure error-free data transmission from/to the SPI master.

The device uses odd parity, for which the parity bit is set so that the total number of ones in the transmitted data on SO (including the parity bit) is an odd number (i.e.  $Bit0 \oplus Bit1 \oplus ... \oplus Bit30 \oplus Bit31 \oplus Parity = 1$ ).

The device also uses odd parity check after receiving data on SI from the SPI master. If the total number of ones in the received data (including the parity bit) is an even number the received data is discarded. The INT will be asserted low and the PRTY\_FAIL bit in the interrupt register (INT\_STAT) is flagged to logic 1 to notify the host that transmission error occurred. The PRTY\_FAIL flag is also asserted during SPI communications.



## 8.3.12 Cyclic Redundancy Check (CRC)

The TIC12400-Q1 includes a CRC module to support redundancy checks on the configuration registers to ensure the integrity of data. The CRC calculation is based on the ITU-T X.25 implementation, and the CRC polynomial (0x1021) used is popularly known as CRC-CCITT-16 since it was initially proposed by the ITU-T (formerly CCITT) committee. The CRC calculation rule is defined in 表 5:

CRC RULE	VALUE
CRC result width	16 bits
Polynomial	$x^{16} + x^{12} + x^5 + 1$ (1021h)
Initial (seed) value	FFFFh
Input data reflected	No
Result data reflected	No
XOR value	0000h

表 5. CRC Calculation Rule

The CRC calculation is done on all the configuration registers starting from register *CONFIG* and ending at register *MODE*. The device substitutes a "zero" for each reserved configuration register bit during the CRC calculation. The CRC calculation can be triggered by asserting the CRC\_T bit in the CONFIG register. Once completed, the CRC\_CALC interrupt bit in the INT\_STAT register is asserted and an interrupt is issued. The 16-bit CRC calculation result is stored in the register CRC. This interrupt can be disabled by de-asserting the CRC\_CALC\_EN bit in the INT\_EN\_CFG0 register. It is important to avoid writing data to the configuration registers when the device is undergoing CRC calculations to prevent false calculation results.

₹ 24 shows the block diagram of the CRC module. The module consists of 16 shift-registers and 3 exclusive-OR gates. The registers start with 1111-1111-1111 (or FFFFh) and the module performs an XOR function and shifts its content until the last bit of the register string is used. The final register's content after the last data bit is the calculated CRC value of the data set and the content is stored in the CRC register.

Note the CRC\_T bit self-clears after the CRC calculation is completed. Logic 1 is used for CRC\_T bit during CRC calculation.

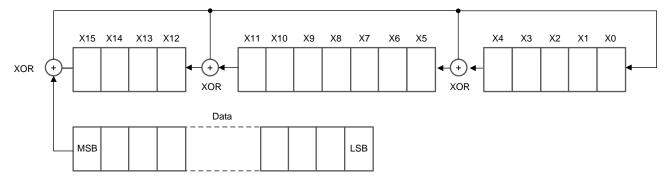


图 24. CCITT-16 CRC Module Block Diagram



#### 8.4 Device Functional Modes

The TIC12400-Q1 has 2 modes of operation: continuous mode and polling mode. The following sections describe the two operation modes in details as well as some of the advanced features that could be activated during normal operations.

#### 8.4.1 Continuous Mode

In continuous mode, wetting current is continuously applied to each enabled input channel, and the status of each channel is sampled sequentially (starting from the IN0 to IN23). The TIC12400-Q1 monitors enabled inputs and issues an interrupt (if enabled) if a switch status change event is detected. The wetting current setting for each input can be individually adjusted by configuring the *WC\_CFG0* and *WC\_CFG1* to the 0mA, 1mA, 2mA, 5mA, 10mA, or 15mA setting. Each input is monitored by either a comparator or an ADC depending on the setting of the input mode in the register *MODE*.

₹ 25 below illustrates an example of the timing diagram of the detection sequence in continuous mode. After the TRIGGER bit in register *CONFIG* is set to logic 1, it takes t<sub>STARTUP</sub> to activate the wetting current for all enabled inputs. The wetting currents stay on continuously, while each input is routed to the ADC/comparator for sampling in a sequential fashion. After conversion/comparison is done for an input, the switch status (below or above detection threshold) is stored in registers (*IN\_STAT\_COMP* for comparator inputs and *IN\_STAT\_ADC0* to *IN\_STAT\_ADC1* for ADC inputs) to be used as the default state for subsequent detection cycles. The digital values (if the input is configured as ADC input mode) are stored in the registers *ANA\_STAT0* to ANA\_STAT11. After the end of the first polling cycle, the INT pin is asserted low to notify the microcontroller that the default switch status is ready to be read. The SSC bit in INT\_STAT register and the SPI status flag SSC are also asserted to logic 1. The polling cycle time (t<sub>POLL</sub>) determines how frequently each input is sampled and can be configured in the register CONFIG.

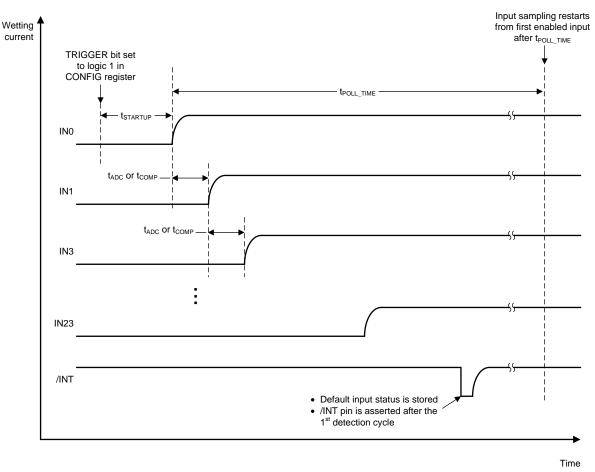


图 25. An Example Of The Detection Sequence In Continuous Mode



The *INT\_STAT* register is cleared and  $\overline{\text{INT}}$  pin de-asserted if a SPI READ command is issued to the register. Note the interrupt is always generated after the 1st detection cycle (after the TRIGGER bit in register *CONFIG* is set to logic 1). In subsequent detection cycles, the interrupt is generated only if switch status change is detected.

No wetting currents are applied to 0mA- configured inputs, although some biasing current (as specified by  $I_{IN\_LEAK\_0mA}$ ) may still flow in and out of the input. Threshold crossing monitoring is still performed for the input using the defined threshold(s). The 0mA setting is useful to utilize the integrated ADC or comparator to measure applied voltage on a specific input without being affected by the device wetting current.

#### 8.4.2 Polling Mode

The polling mode can be activated to reduce current drawn in ignition-off condition to conserve battery charge. Unlike the continuous mode, the current sources/sinks do not stay on continuously in the polling mode. Instead, they are turned on/off sequentially from IN0 to IN23 and cycled through each individual input channel. The microcontroller can be put to sleep to reduce overall system power. If a switch status change (SSC) is detected by the TIC12400-Q1, the INT pin (if enabled for the input channel) is asserted low (and the SSC bit in INT\_STAT register and the SPI status flag SSC are also asserted to logic 1). The INT pin assertion can be used to wake up the system regulator which, in turn, wakes up the microcontroller as described in section *Microcontroller Wake-Up*. The microcontroller can then use SPI communication to read the switch status information.

The polling is activated when the TRIGGER bit in the *CONFIG* register is set to logic 1. There are 2 different polling schemes that can be configured in TIC12400-Q1: standard polling and matrix polling.

#### 8.4.2.1 Standard Polling

In standard polling mode, wetting current is applied to each input for a pre-programmed polling active time between 64  $\mu$ s and 2048  $\mu$ s, set by the POLL\_ACT\_TIME bits in the *CONFIG* register . At the end of the wetting current application, the input voltage is sampled by the comparator (if input is configured as comparator input mode) or the ADC (if input is configured as ADC input mode). Each input is cycled through in sequential order from IN0 to IN23. Sampling is repeated at a frequency from 2 ms to 4096 ms, set by the POLL\_TIME bits in the *CONFIG* register . Wetting currents are applied to closed switches only during the polling active time; hence the overall system current consumption can be greatly reduced.

Similar to continuous mode, after the first polling cycle, the switch status of each input (below or above detection threshold) is stored in registers (*IN\_STAT\_COMP* for comparator inputs and *IN\_STAT\_ADC0* to *IN\_STAT\_ADC1* for ADC inputs) to be used as the default state for subsequent polling cycles. The digital values (if the input is configured as ADC input mode) are stored in the registers *ANA\_STAT0* to *ANA\_STAT11*. The *INT* pin is asserted low to notify the microcontroller that the default switch status is ready to be read. The SSC bit in INT\_STAT register and the SPI status flag SSC are also asserted to logic 1. The *INT\_STAT* register is cleared and *INT* pin de-asserted if a SPI READ command is issued to the register. Note the interrupt is always generated after the 1st polling cycle (after the TRIGGER bit in register *CONFIG* is set to logic 1). In subsequent polling cycles the interrupt is generated only if switch status change is detected.

An example of the timing diagram of the polling mode operation is shown in 图 26.



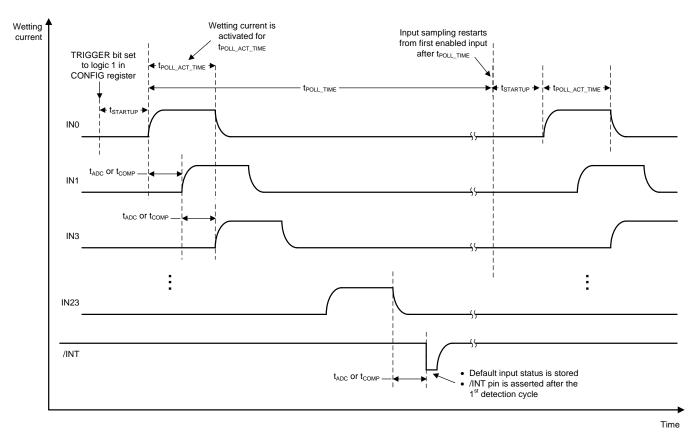


图 26. An Example Of The Polling Sequence In Standard Polling Mode



If the switch position changes between two active polling times, no interrupt will be generated and the status registers (*IN\_STAT\_COMP* for comparator inputs and *IN\_STAT\_ADC0* to *IN\_STAT\_ADC1* for ADC inputs) will not reflect such a change. An example is shown in 图 27.

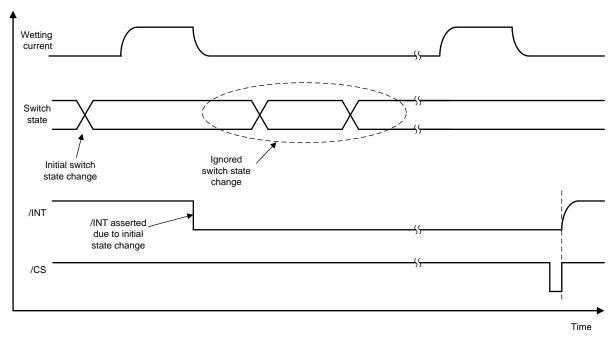


图 27. Example For Ignored Switch Position Change Between 2 Wetting Current Cycles



## 8.4.2.2 Matrix polling

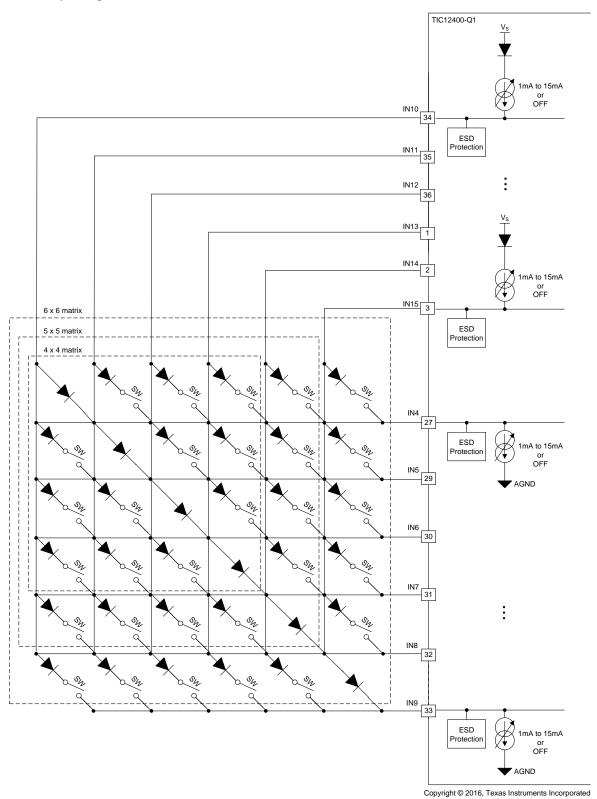


图 28. TIC12400-Q1 Matrix Configuration



From IN4 to IN15 a special input switch matrix (see 28) can be configured and monitored in addition to the standard switches to GND and V<sub>BAT</sub>. This feature could be useful to monitor a special switch input configuration called Matrix Inputs as required by some specific OEMs.

Three different matrix configurations are possible, and are defined by MATRIX bits in the *MATRIX* register. If the MATRIX bits are set to '00' all inputs are treated as standard inputs with identical polling active time according to the POLL\_ACT\_TIME bits in the *CONFIG* register. Any settings other than '00' for MATRIX bits causes the polling active time for the matrix inputs to be configured according to POLL\_ACT\_TIME\_M bits in the *MATRIX* register. Inputs that are not part of the matrix configuration will be configured using the POLL\_ACT\_TIME bits in the *CONFIG* register. t<sub>POLL\_ACT\_TIME\_M</sub> should be configured properly to allow sufficient time for the current source/sink to charge/discharge the capacitors (if any) connected to the switch inputs.

	4 x 4 N	MATRIX	5 x 5	MATRIX	6 x 6	MATRIX
Input	Current Source Or Sink	Polling Active Time Setting	Current Source Or Sink	Polling Active Time Setting	Current Source Or Sink	Polling Active Time Setting
IN4	CSI		CSI		CSI	
IN5	CSI	POLL_ACT_TIME_ M	CSI	CSI CSI POLL_ACT_TIME_M	CSI	
IN6	CSI		CSI		CSI	
IN7	CSI		CSI		CSI	
IN8	Configurable to CSO or CSI	DOLL ACT TIME	CSI		CSI	
IN9	Configurable to CSO or CSI	POLL_ACT_TIME	Configurable to CSO or CSI	POLL_ACT_TIME	CSI	POLL_ACT_TIME_M
IN10	CSO		CSO		CSO	
IN11	CSO	POLL_ACT_TIME_	CSO		CSO	
IN12	CSO	_ M	CSO	POLL_ACT_TIME_M	CSO	
IN13	CSO		CSO		CSO	
IN14	CSO	DOLL ACT TIME	CSO		CSO	
IN15	CSO	POLL_ACT_TIME	CSO	POLL ACT TIME	CSO	

表 6. TIC12400-Q1 Matrix Configuration Settings

The TIC12400-Q1 implements a different polling scheme when matrix input is configured. After the polling sequence is started (by setting TRIGGER bit in *CONFIG* register to logic 1), the polling takes place within the matrix input group first before the rest of the standard inputs are polled. After the matrix inputs are polled, the switch status of each input combination (below or above detection threshold) is stored internally in registers *IN\_STAT\_MATRIX0* and *IN\_STAT\_MATRIX1*, and it is used as the default state for subsequent matrix polling cycles. The standard inputs follow the same polling behavior <u>as</u> described in section *Standard Polling*. After the polling cycle is completed on matrix and standard inputs, the *INT* pin is asserted low to notify the microcontroller that the default switch status is ready to be read. The SSC bit in the *INT\_STAT* register and the SPI status flag SSC are also asserted to logic 1.

The *INT\_STAT* register is cleared and  $\overline{\text{INT}}$  pin de-asserted if a SPI READ command is issued to the register. Note the interrupt is always generated after the 1st complete polling cycle (after the TRIGGER bit in register *CONFIG* is set to logic 1). In subsequent polling cycles, the interrupt is generated only if switch status change is detected.



Note the following programming requirement when using the matrix polling:

- It is critical to program the CSO/CSI configuration for each matrix input appropriately according to 表 6 to avoid incorrect switch status detection.
- It is mandatory to set higher wetting current for the sinks (IN4-IN9) than the sources (IN10-IN15). The actual current flowing through the external switches will be the lesser of the two settings. If the same setting is used for both the sink and the source, the detected result might be incorrect. Because of this, the 15 mA setting shall not be used for the current sources and the 1 mA setting shall not be used for the current sinks. Depending on the type of matrix switches, the TIC12400-Q1 might require some specific wetting current settings to be able to distinguish between switch open/closed states.
- If TW\_CUR\_DIS\_CSO or TW\_CUR\_DIS\_CSI is set to logic 0 in the *CONFIG* register, wetting current is reduced to 2 mA for 10 mA and 15 mA settings upon TW event. Since it's mandatory to have higher wetting current for the sinks (IN4-IN9) than the sources (IN10-IN15) during matrix polling,表 7 below summarizes the only possible settings if TW event is expected:

## 表 7. Possible Wetting Current Settings For The Matrix Polling Mode If TW\_CUR\_DIS=0 And TW Event Is Expected

CSO (IN10-IN15)	CSI (IN4-IN9)	RESULTING WETTING CURRENT
1 mA	2 mA, 5 mA, 10 mA, 15 mA	1 mA
2 mA	5 mA	2 mA

If higher wetting current is needed and TW event might be expected, the TW wetting current reduction feature needs to be disabled by setting TW CUR DIS CSO or TW CUR DIS CSI bit in the CONFIG register to 1.

Only comparator input mode is supported for the matrix polling. Do not program the matrix inputs into ADC input mode. The comparison takes place on the source side (IN10-IN15) since the sink side is pulled to ground. Interrupt generation condition can be set by configuring the INT\_EN\_COMP1 and INT\_EN\_COMP2 registers for inputs IN10 to IN15.

Some programmability is removed when matrix polling mode is used, as listed below:

- To keep the polling scheme simple, the ability to disable inputs is removed for the matrix inputs. Only 3 configurations (4x4, 5x5, and 6x6) can be used for the matrix polling. Standard inputs outside the matrix input group can still be disabled, if desired.
- Detection filter (by configuring the DET\_FILTER in the CONFIG register) does not apply to the matrix inputs, but still applies to the standard inputs outside the matrix input group.
- When matrix polling is selected, continuous mode is not available to the standard inputs outside the matrix input group.



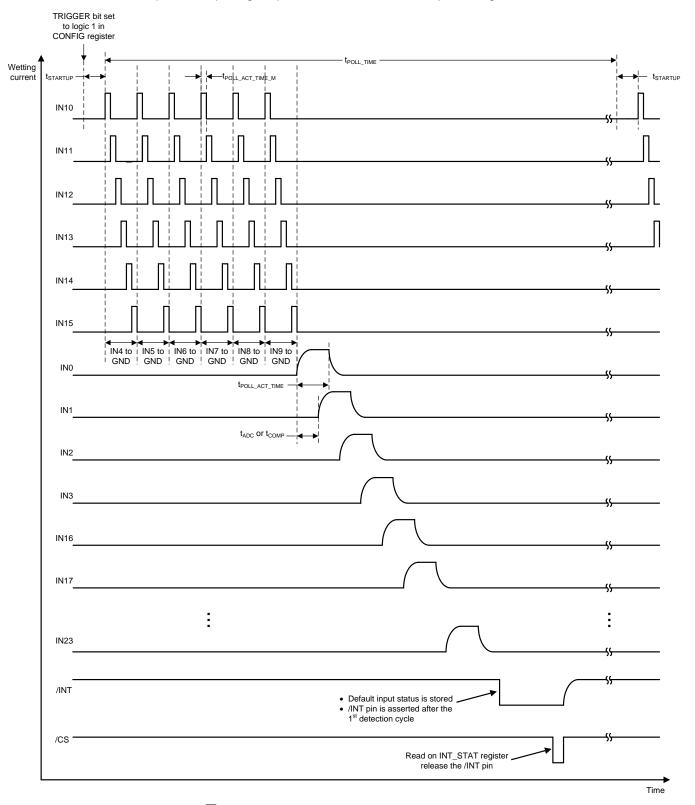


图 29. Polling Scheme for 6x6 Matrix Inputs



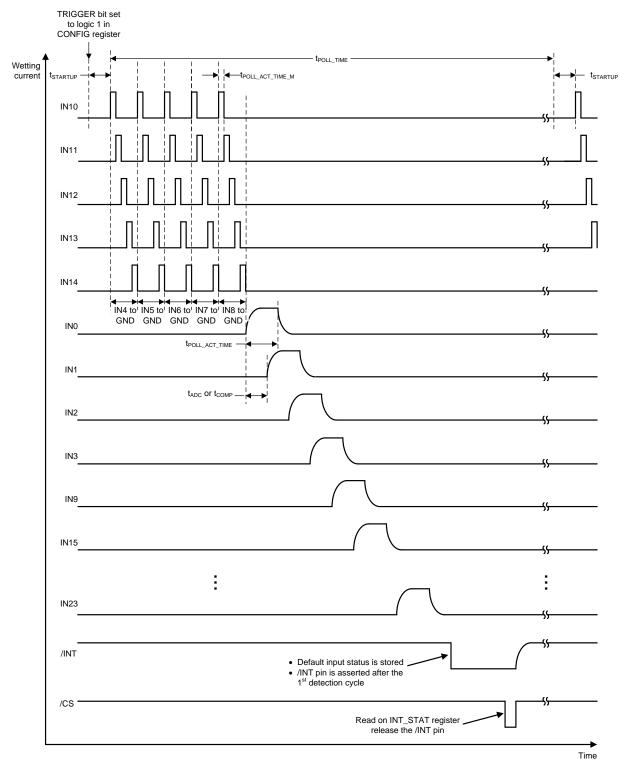


图 30. Polling Scheme For 5x5 Matrix Inputs



₹ 31 illustrates an example of the polling sequence for the 4x4 matrix input configuration. Note inputs IN8, IN9, IN14, and IN15 are included in the standard polling sequence.

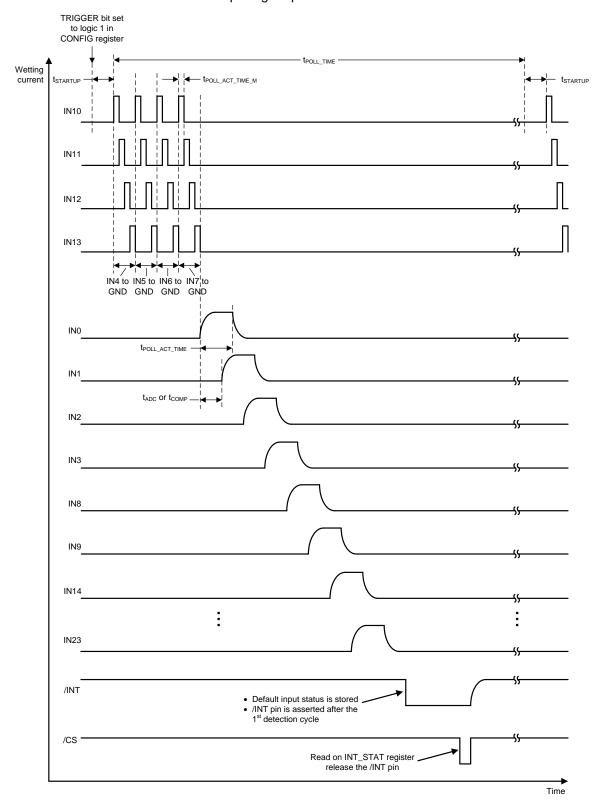


图 31. Polling Scheme For 4x4 Matrix Inputs



#### 8.4.3 Additional Features

There are additional features that can be enabled during continuous and polling mode to increase robustness of device operation or provide more system information. These features are described in detail in the following sections.

#### 8.4.3.1 Clean Current Polling (CCP)

To detect resistor coded switches or reduce overall power consumption of the chip, a lower wetting current setting is recommended. However, certain system design requires 10 mA or higher cleaning current to clear oxide build-up on the mechanical switch contact surface when the current is applied to closed switches. A special type of polling, called the Clean Current Polling (CCP), can be used for this application.

If CCP is enabled each polling cycle consists of two wetting current activation steps. The first step uses the wetting current setting configured in the  $WC\_CFG0$  and  $WC\_CFG1$  registers as in the continuous mode or polling mode. The second step (cleaning cycle) is activated simultaneously for all CCP enabled inputs at a time  $t_{CCP\_TRAN}$  after the normal polling step of the last enabled input. Interrupt generation and  $\overline{INT}$  pin assertion is not impacted by the clean current pulses.

The wetting current and its active time for the cleaning cycle can be configured in the  $CCP\_CFG0$  register. The cleaning cycle can be disabled, if desired, for each individual input by programming the  $CCP\_CFG1$  register. CCP is available for both continuous mode and polling mode. To use the CCP feature, at least one input (standard or matrix) or the  $V_S$  Measurement has to be enabled.

Note that although CCP can be enabled in Matrix polling mode, it is not an effective way to clean the matrix switch contact, since the current supplied from the TIC12400-Q1 is divided and distributed across multiple matrix channels.



图 32 illustrates the operation of the CCP when the device is configured to the standard polling mode.

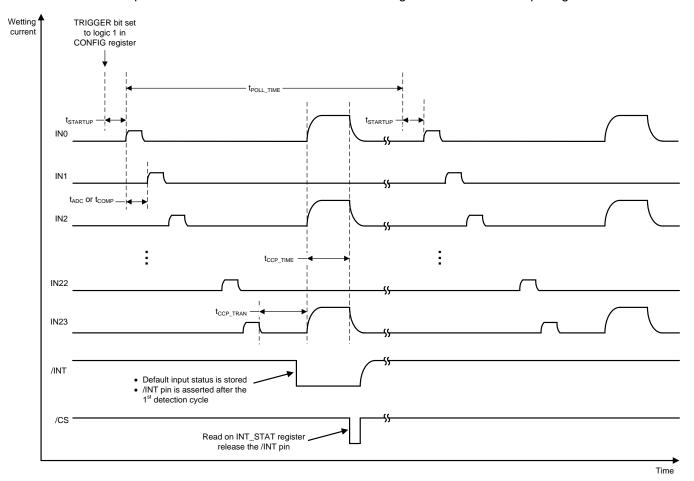


图 32. Standard Polling With CCP Enabled



图 33 illustrates the operation of the CCP when the device is configured to the continuous mode:

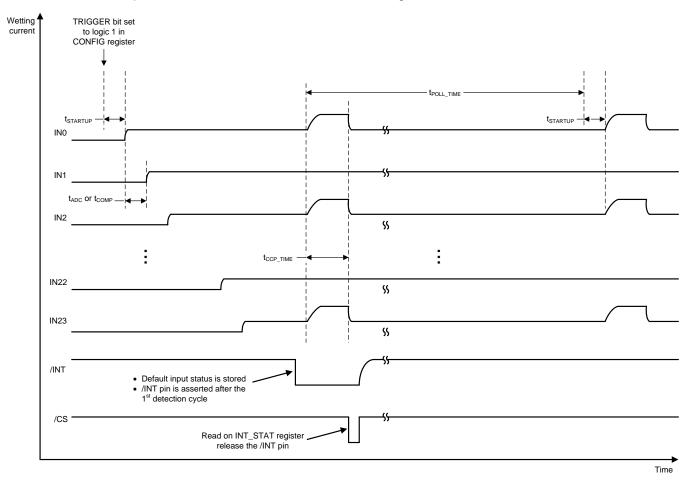


图 33. Continue Mode With CCP Enabled

#### 8.4.3.2 Wetting Current Auto-Scaling

The 10 mA and 15 mA wetting current settings are useful to clean oxide build-up on the mechanical switch contact surface when the switch changes state from open to close. After the switch is closed, it is undesirable to keep the wetting current level at high level if only digital switches are monitored since it results in high current consumption and could potentially heat up the device quickly if multiple inputs are monitored. The wetting current auto-scaling feature helps mitigate this issue.

When enabled (AUTO\_SCALE\_DIS\_CSO or AUTO\_SCALE\_DIS\_CSI bit = logic 0 in the *WC\_CFG1* register), wetting current is reduced to 2 mA from 10 mA or 15 mA setting after switch closure is detected. The threshold used to determine a switch closure is the threshold configured in the *THRES\_COMP* register for inputs configured as comparator input mode. For inputs configured as ADC input mode, the threshold used to determine a switch closure depends on the input number, as described in 表 8 below.

表 8. Threshold Used To Determine A Switch Closure For Wetting Current Auto-scaling For ADC Inputs

INPUT	THRESHOLD USED TO DETERMINE A SWITCH CLOSURE
INO-IN11	Mapped threshold from THRES0 to THRES7
IN12 to IN17	THRES2B
IN18 to IN22	THRES3C
IN23	THRES9



The current reduction takes place N cycles after switch closure is detected on an input, where N depends on the setting of the DET\_FILTER bits in the CONFIG register:

- DET\_FILTER= 00: wetting current is reduced immediately in the next detection cycle after a closed switch is detected.
- DET\_FILTER= 01: wetting current is reduced when a closed switch is detected and the switch status is stable for at least 2 consecutive detection cycles.
- DET\_FILTER= 10: wetting current is reduced when a closed switch is detected and the switch status is stable for at least 3 consecutive detection cycles.
- DET\_FILTER= 11: wetting current is reduced when a closed switch is detected and the switch status is stable for at least 4 consecutive detection cycles.

The wetting current is adjusted back to the original setting of 10 mA or 15 mA at a time of N cycles after an open switch is detected, where N again depends on the DET\_FILTER bit setting in the *CONFIG* register. 图 34 depicts the behavior of the wetting current auto-scaling feature.

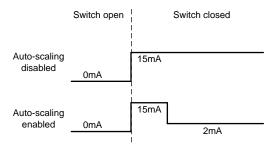


图 34. Wetting Current Auto-scaling Behavior

The wetting current auto-scaling only applies to 10 mA and 15 mA settings and is only available in continuous mode. If AUTO\_SCALE\_DIS\_CSO or AUTO\_SCALE\_DIS\_CSI bit is set to logic 1 in the *WC\_CFG1* registers, the wetting current stays at its original setting when a closed switch is detected. Power dissipation needs to be closely monitored when wetting current auto-scaling is disabled for multiple inputs as the device could heat up quickly when high wetting current settings are used. If the auto-scaling feature is disabled in continuous mode, the total power dissipation can be approximated using 公式 1.

$$P_{TOTAL} = V_S \times \left( I_{S\_CONT} + I_{WETT(TOTAL)} \right) \tag{1}$$

where  $I_{WETT\ (TOTAL)}$  is the sum of all wetting currents from all input channels. Increase in device junction temperature can be calculated based on P ×  $R_{\theta JA}$ . The junction temperature must be below  $T_{TSD}$  for proper device operation. An interrupt will be issued when the junction temperature exceeds  $T_{TW}$  or  $T_{TSD}$ . For detailed description of the temperature monitoring, please refer to sections *Temperature Warning (TW)* and *Temperature Shutdown (TSD)*.

#### 8.4.3.3 V<sub>S</sub> Measurement

When the TIC12400-Q1 is used to monitor resistor-coded switches, the  $V_S$  supply voltage level becomes critical. If  $V_S$  is not sufficiently high, the device might not have enough headroom to produce accurate wetting currents. This could impact the accuracy of the switch status monitoring. It is imperative for the microcontroller to have knowledge of the  $V_S$  voltage on a constant basis in such a case.

Measurement of  $V_S$  voltage is a feature in TIC12400-Q1 that can be enabled by setting the VS\_MEAS\_EN bit in register *CONFIG* to logic 1. If enabled, at the end of every detection/polling cycle, the voltage on the  $V_S$  pin is sampled and converted by the ADC to a digital value. The conversion takes one extra  $t_{ADC}$ , and the converted value is recorded in the *ANA\_STAT12* register.

The  $V_S$  measurement supports two different  $V_S$  voltage ranges that can be configured by the VS\_RATIO bit in the *CONFIG* register. By default (VS\_RATIO= logic 0), the supported  $V_S$  voltage range is from 4.5 V to 9 V, and  $V_S$  voltage in excess of 9 V results in a saturated ADC raw code of 1023. This setting provides better measurement resolution at lower  $V_S$  voltages. When VS\_RATIO bit is set to logic 1, the supported  $V_S$  voltage range is widened to 4.5 V to 30 V, and  $V_S$  voltage in excess of 30 V results in a saturated ADC raw code of 1023. This setting allows wider measurement range but more coarse measurement resolution. It is important to adjust the detection thresholds accordingly depending on the  $V_S$  voltage range configured.



Four different measurement thresholds can be programmed by the TIC12400-Q1: VS0\_THRES2A/B and VS1\_THRES2A/B. The value of these thresholds can be programmed by configuring registers *THRES\_CFG0* to *THRES\_CFG3* and the mapping can be programmed by configuring registers THRESMAP\_VS0\_THRES2A/B and THRESMAP\_VS1\_THRES2A/B bits in the register *THRESMAP\_CFG2*. When setting the thresholds follow the rules in 表 9 below.

#### 表 9. Proper threshold configuration for V<sub>S</sub> measurements

V <sub>S</sub> THRESHOLD	PROPER THRESHOLD CONFIGURATION
VS0	VS0_THRES2B ≥ VS0_THRES2A
VS1	VS1_THRES2B ≥ VS1_THRES2A

After the  $V_S$  measurement is enabled for the first time, the  $V_S$  measurement interrupt is always generated ( $\overline{\text{INT}}$  pin is asserted low, and the VS0 or VS1 bit in the  $INT\_STAT$  register is flagged to logic 1) at the end of the first polling cycle to notify the microcontroller the initial  $V_S$  measurement result is ready to be retrieved. The VS0\_STAT and VS1\_STAT bits from register  $IN\_STAT\_MISC$  indicate the status of the  $V_S$  voltage with respect to the thresholds, and the  $ANA\_STAT12$  register stores the converted digital value of the  $V_S$  voltage. The SPI status flag VS\_TH is also asserted to logic 1 during SPI communications. Note the status detected in the first polling cycle becomes the baseline value of comparison for subsequent  $V_S$  measurements and the interrupt will be generated only if threshold crossing is detected.

Similar to regular inputs, the interrupt generation conditions can be programmed by setting the VS\_TH0\_EN and VS\_TH1\_EN bits in the *INT\_EN\_CFG4* register to the following settings:

- Rising edge: an interrupt is generated if the current V<sub>S</sub> measurement is above the corresponding threshold and the previous measurement was below.
- Falling edge: an interrupt is generated if the current V<sub>S</sub> measurement is below the corresponding threshold and the previous measurement was above.
- 3. Both edges: changes of the V<sub>S</sub> measurement status in either direction results in an interrupt generation.

Interrupt generation can also be disabled by setting VS\_TH0\_EN or VS\_TH1\_EN to logic 0 in register INT\_EN\_CFG4. Once disabled, V<sub>S</sub> voltage crossing does not flag the VS0 or VS1 bit in INT\_STAT register and does not assert INT pin low. To only mask the INT pin from assertion (while keeping INT\_STAT register updated), configure the VS1\_EN and VS0\_EN bits in register INT\_EN\_CFG0 to logic 0.

Note the  $V_S$  measurement is only intended to be used as part of switch detection sequence to determine the validity of the switch detection states that are reported by the TIC12400-Q1. It is not intended to be used for standalone supply monitoring, such as monitoring cranking voltages, due to the potentially delayed response being part of the polling sequence. The  $V_S$  measurement result is accurate for  $V_S$  above 4.5 V.

By default, the V<sub>S</sub> voltage measurement is disabled upon device reset.

#### 8.4.3.4 Wetting Current Diagnostic

When the TIC12400-Q1 is used to monitor safety-critical switches, it might be valuable for the microcontroller to have knowledge of the operating status of the wetting current sources/ sinks. This can be achieved by activating the wetting current diagnostic feature provided for inputs IN0 to IN3. IN0 and IN1 can be diagnosed for defective wetting current sources, while IN2 and IN3 can be diagnosed for defective current sinks.

The wetting current diagnostic feature can be activated by setting the WET\_D\_INx\_EN bits in the CONFIG register to 1 for the desired inputs, where x can be 0, 1, 2, or 3. If activated, the TIC12400-Q1 checks the status of the wetting current sources / sinks for the configured input periodically as part of the polling sequence. If the wetting current is determined to be flawed, the TIC12400-Q1 pulls the INT pin low to notify the host and flag the WET\_DIAG bit in the INT\_STAT register to logic 1. The OI bit in the SPI flag is also asserted during SPI transactions. The microcontroller can then read bits IN0\_D to IN3\_D in register IN\_STAT\_MISC to learn more information on which wetting current source/sink is defective.

The wetting current diagnostic is not performed for inputs that are disabled (IN\_EN\_x bit = 0 in the IN\_EN register) from polling, even if the feature is activated for those inputs. Also, it is critical to configure the current source/sink appropriately (CSO for IN0/IN1 and CSI for IN2/IN3) and program the input to ADC input mode before activating the wetting current diagnostic feature to prevent false interrupts from being generated. The wetting current diagnostic feature can be performed regardless of the states of external switches, and it is available in both continuous mode and polling mode.

₹ 35 shows an example of the feature carried out in a typical polling sequence. In this example, it can be observed that the wetting current is activated for duration of t<sub>POLL\_ACT</sub>+ t<sub>ADC</sub> for each input diagnosed (IN0 or IN2). Normal polling sequence resumes with IN4 and the wetting current is activated for t<sub>POLL\_ACT</sub> for the rest of the inputs. The diagnostic is not executed on inputs IN1 and IN3 in this example since they are disabled.

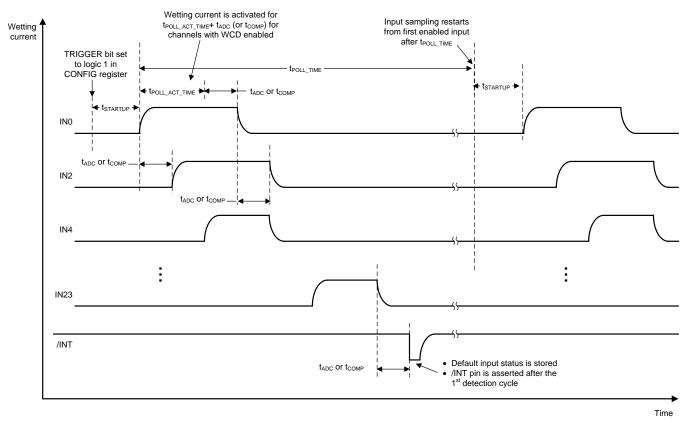


图 35. An Example Of The Polling Sequence In Standard Polling Mode With Wetting Current Diagnostic Enabled

#### 8.4.3.5 ADC Self-Diagnostic

In addition to the wetting current diagnostic, another feature— the ADC self-diagnostic, can be enabled to monitor the integrity of the internal ADC.

The ADC self-diagnostic feature is activated by setting the ADC\_DIAG\_T bit in the *CONFIG* register to logic 1. Once enabled, the TIC12400-Q1 periodically sends a test voltage to the ADC. The conversion result is stored in the ADC\_SELF\_ANA bits in the register *ANA\_STAT12* and is compared with a pre-defined code to determine whether the conversion is performed properly. If an error is detected, the TIC12400-Q1 pulls the INT pin low to notify the host and flag the ADC\_DIAG bit in the *INT\_STAT* to logic 1. The bit ADC\_D in register *IN\_STAT\_MISC* is updated with the result from the self-diagnostic. The ADC self-diagnostic feature is available in both continuous mode and polling mode.



#### 8.5 Programming

The SPI interface communication consists of the 4 pins:  $\overline{CS}$ , SCLK, SI, and SO. The interface can work with SCLK frequency up to 4MHz.

#### 8.5.1 SPI Communication Interface Buses

#### 8.5.1.1 Chip Select (CS)

The system microcontroller selects the TIC12400-Q1 to receive communication using the  $\overline{\text{CS}}$  pin. With the  $\overline{\text{CS}}$  pin in a logic LOW state, command words may be sent to the TIC12400-Q1 via the serial input (SI) pin, and the device information can be retrieved by the microcontroller via the serial output (SO) pin. The falling edge of the  $\overline{\text{CS}}$  enables the SO output and latches the content of the interrupt register INT\_STAT. The microcontroller may issue a READ command to retrieve information stored in the registers. Rising edge on the  $\overline{\text{CS}}$  pin initiates the following operations:

- 1. Disable the output driver and makes SO high-impedance.
- 2.  $\overline{\text{INT}}$  pin is reset to logic HIGH if a READ command to the INT\_STAT register was issued during  $\overline{\text{CS}} = \text{LOW}$ .

To avoid corrupted data, it is essential the HIGH-to-LOW and LOW-to-HIGH transitions of the  $\overline{CS}$  signal occur only when SCLK is in a logic LOW state. A clean  $\overline{CS}$  signal is needed to ensure no incomplete SPI words are sent to the device. The  $\overline{CS}$  pin should be externally pulled up to VDD by a 10 k $\Omega$  resistor.

#### 8.5.1.2 System Clock (SCLK)

The system clock (SCLK) input is used to clock the internal shift register of the TIC12400-Q1. The SI data is latched into the input shift register on the falling edge of the SCLK signal. The SO pin shifts the device stored information out on the rising edge of SCLK. The SO data is available for the microcontroller to read on the falling edge of SCLK.

False clocking of the shift register must be avoided to ensure validity of data and it is essential the SCLK pin be in a logic LOW state whenever  $\overline{CS}$  makes any transition. Therefore, it is recommended that the SCLK pin gets pulled to a logic LOW state as long as the device is not accessed and  $\overline{CS}$  is in a logic HIGH state. When the  $\overline{CS}$  is in a logic HIGH state, any signal on the SCLK and SI pins will be ignored and the SO pin remains as a high impedance output. Refer to  $\overline{S}$  36 and  $\overline{S}$  37 for examples of typical SPI read and write sequence.

### 8.5.1.3 Slave In (SI)

The SI pin is used for serial instruction data input. SI information is latched into the input register on the falling edge of the SCLK. To program a complete word, 32 bits of information must be entered into the device. The SPI logic counts the number of bits clocked into the IC and enables data latching only if exactly 32 bits have been clocked in. In case the word length exceeds or does not meet the required length, the SPI\_FAIL bit of the INT\_STAT register is asserted to logic 1 and the INT pin will be asserted low. The data received is considered invalid. Note the SPI\_FAIL bit is not flagged if SCLK is not present.

#### 8.5.1.4 Slave Out (SO)

The SO pin is the output from the internal shift register. The SO pin remains high-impedance until the  $\overline{\text{CS}}$  pin transitions to a logic LOW state. The negative transition of  $\overline{\text{CS}}$  enables the SO output driver and drives the SO output to the HIGH state (by default). The first positive transition of SCLK makes the status data bit 31 available on the SO pin. Each successive positive clock makes the next status data bit available for the microcontroller to read on the falling edge of SCLK. The SI/SO shifting of the data follows a first-in, first-out scheme, with both input and output words transferring the most significant bit (MSB) first.



## Programming (接下页)

#### 8.5.2 SPI Sequence

图 36 and 图 37 depict the SPI communication sequence during read and write operations for the TIC12400-Q1.

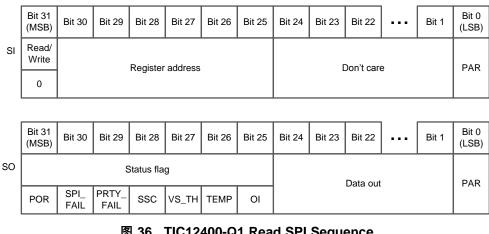
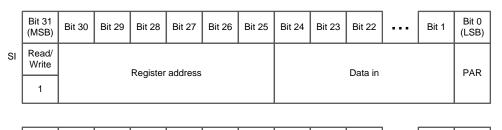


图 36. TIC12400-Q1 Read SPI Sequence



	Bit 31 (MSB)	Bit 30	Bit 29	Bit 28	Bit 27	Bit 26	Bit 25	Bit 24	Bit 23	Bit 22	•••	Bit 1	Bit 0 (LSB)	
so			S	Status fla	g			PAR						
	POR	SPI_ FAIL	PRTY_ FAIL	SSC	VS_TH	TEMP	OI		regis	ter addre	ssed			

图 37. TIC12400-Q1 Write SPI Sequence

#### 8.5.2.1 Read Operation

The Read/Write bit (bit 31) of the SI bus needs to be set to logic 0 for a READ operation. The 6-bits address of the register to be accessed follows next on the SI bus. The content from bit 24 to bit 1 does not represent a valid command for a read operation and will be ignored. The LSB (bit 0) is the parity bit used to detect communication errors.

On the SO bus, the status flags will be outputted from the TIC12400-Q1, followed by the data content in the register that was requested. The LSB is the parity bit used to detect communication errors.

Note there are several test mode registers used in the TIC12400-Q1 in addition to the normal functional registers, and a READ command to these test registers returns the register content. If a READ command is issued to an invalid register address, the TIC12400-Q1 returns all 0's.

#### 8.5.2.2 Write Operation

The Read/Write bit (bit 31) on the SI bus needs to be set to 1 for a write operation. The 6-bits address of the register to be accessed follows next on the SI bus. Note the register needs to be a writable configuration register, or otherwise the command will be ignored. The content from bit 24 to bit 1 represents the data to be written to the register. The LSB (bit 0) is the parity bit used to detect communication errors.



## Programming (接下页)

On the SO bus, the status flags will be output from the TIC12400-Q1, followed by the previous data content of the written register. The previous content of the register is latched after the full register address is decoded in the SI command (after bit 25 is transmitted). The new data will replace the previous data content at the end of the SPI transaction if the SI write is a valid command (valid register address and no SPI/parity error). If the write command is invalid, the new data will be ignored and the register content will remain unchanged. The LSB is the parity bit used to detect communication errors.

Note there are several test mode registers used in the TIC12400-Q1 in addition to the normal functional registers. A WRITE command to these test registers has no effect on the register content, even though the register content is returned on the SO output. If a WRITE command is issued to an invalid register address, the SO output returns all 0's.

## 8.5.2.3 Status Flag

The status flags are output from SO during every READ or WRITE SPI transaction to indicate system conditions. These bits do not belong to an actual register, but their content is mirrored from the interrupt register INT\_STAT. A READ command executed on the INT\_STAT would clear both the bits inside the register and the status flag. The following table describes the information that can be obtained from each SPI status flag:

### 表 10. TIC12400-Q1 SPI Status Flag Description

SYMBOL	NAME	DESCRIPTION
POR	Power-on Reset	This flag mirrors the POR bit in the interrupt register INT_STAT, and it indicates, if set to 1, that a reset event has occurred. This bit is asserted after a successful power-on-reset, hardware reset, or software reset. Refer to section <i>Device Reset</i> for more details.
SPI_FAIL	SPI Error	This flag mirrors the SPI_FAIL bit in the interrupt register INT_STAT and it indicates, if set to 1, that the last SPI Slave In (SI) transaction is invalid. To program a complete word, 32 bits of information must be entered into the device. The SPI logic counts the number of bits clocked into the IC and enables data latching only if exactly 32 bits have been clocked in. In case the word length exceeds or does not meet the required size, the SPI_FAIL bit, which mirrors its value to this SPI_FAIL status flag, of the interrupt register INT_STAT will be set to 1 and the INT in will be asserted low. The data received will be considered invalid. Once the INT_STAT register is read, its content will be cleared on the rising edge of CS. The SPI_FAIL status flag, which mirrors the SPI_FAIL bit in the INT_STAT register, will also be de-asserted. Note the SPI_FAIL bit is not flagged if SCLK is not present.
PRTY_FAIL	Parity Fail	This flag mirrors the PRTY_FAIL bit in the interrupt register INT_STAT and it indicates, if set to 1, that the last SPI Slave In (SI) transaction has a parity error. The device uses odd parity. If the total number of ones in the received data (including the parity bit) is an even number, the received data is discarded. The INT will be asserted low and the PRTY_FAIL bit in the interrupt register (INT_STAT) is flagged to logic 1, and the PRTY_FAIL status flag, which mirrors the PRTY_FAIL bit in the INT_STAT register, is also set to 1. Once the INT_STAT register is read, its content will be cleared on the rising edge of CS. The PRTY_FAIL status flag, which mirrors the PRTY_FAIL bit in the INT_STAT register, will also be de-asserted.
SSC	Switch State Change	This flag mirrors the SSC bit in the interrupt register INT_STAT and it indicates, if set to 1, that one or more switch inputs crossed a threshold. To determine the origin of the state change, the microcontroller can read the content of registers IN_STAT_COMP (if input is set to comparator input mode), IN_STAT_ADC0 to IN_STAT_ADC1 (if input is set to ADC input mode), or IN_STAT_MATRIX1 (if input is set to matrix input). Once the interrupt register (INT_STAT) is read, its content will be cleared on the rising edge of \$\overline{CS}\$. The SSC status flag, which mirrors the SSC bit in the INT_STAT register, will also be de-asserted.
VS_TH	V <sub>S</sub> Threshold Crossing	This flag is set to 1 if either VS0 or VS1 bit in the interrupt register INT_STAT is flagged to 1. It indicates the $V_S$ voltage crosses one or more thresholds defined by VS0_THRES2A, VS0_THRES2B, VS1_THRES2A, or VS1_THRES2B. To determine the origin of the threshold crossing, the microcontroller can read register bits VS0_STAT and VS1_STAT in the register IN_STAT_MISC. Once the interrupt register (INT_STAT) is read, its content will be cleared on the rising edge of $\overline{CS}$ , and the VS_TH status flag will also be de-asserted.
TEMP	Temperature Event	This flag is set to 1 if either Temperature Warning (TW) or Temperature Shutdown (TSD) bit in the interrupt register INT_STAT is flagged to 1. It indicates a TW event or a TSD event has occurred. It is also flagged to 1 if a TW event or a TSD event is cleared. The interrupt register INT_STAT should be read to determine which event occurred. The SPI master can also read the IN_STAT_MISC register to get information on the temperature status of the device. Once the interrupt register (INT_STAT) is read, its content will be cleared on the rising edge of $\overline{\text{CS}}$ , and the TEMP status flag will also be de-asserted.
OI	Other Interrupt	Other interrupt include interrupts such as OV, UV, CRC_CALC. WET_DIAG, ADC_DIAG and CHK_FAIL. This flag will be asserted 1 when any of the abovementioned bits is flagged in the interrupt register INT_STAT. The interrupt register INT_STAT should be read to determine which event(s) occurred. The SPI master can also read the IN_STAT_MISC register to get information on the latest status of the device. Once the INT_STAT register is read, its content will be cleared on the rising edge of $\overline{\text{CS}}$ , and the OI status flag will also be de-asserted.



## 8.6 REGISTER\_MAPS

 $\frac{11}{8}$  lists the memory-mapped registers for the TIC12400-Q1. All register offset addresses not listed in  $\frac{11}{8}$  should be considered as reserved locations and the register contents should not be modified.

表 11. TIC12400-Q1 Registers

OFFSET	TYPE	RESET	ACRONYM	REGISTER NAME	SECTION
1h	R	20h	DEVICE_ID	Device ID Register	Go
2h	RC	1h	INT_STAT	Interrupt Status Register	Go
3h	R	FFFFh	CRC	CRC Result Register	Go
4h	R	0h	IN_STAT_MISC	Miscellaneous Status Register	Go
5h	R	0h	IN_STAT_COMP	Comparator Status Register	Go
6h-7h	R	0h	IN_STAT_ADC0, IN_STAT_ADC1	ADC Status Register	Go
8h-9h	R	0h	IN_STAT_MATRIX0, IN_STAT_MATRIX1	Matrix Status Register	Go
Ah-16h	R	0h	ANA_STAT0- ANA_STAT12	ADC Raw Code Register	Go
17h-19h	_	_	RESERVED	RESERVED	_
1Ah	R/W	0h	CONFIG	Device Global Configuration Register	Go
1Bh	R/W	0h	IN_EN	Input Enable Register	Go
1Ch	R/W	0h	CS_SELECT	Current Source/Sink Selection Register	Go
1Dh-1Eh	R/W	0h	WC_CFG0, WC_CFG1	Wetting Current Configuration Register	Go
1Fh-20h	R/W	0h	CCP_CFG0, CCP_CFG1	Clean Current Polling Register	Go
21h	R/W	0h	THRES_COMP	Comparator Threshold Control Register	Go
22h-23h	R/W	0h	INT_EN_COMP1, INT_EN_COMP2	Comparator Input Interrupt Generation Control Register	Go
24h	R/W	0h	INT_EN_CFG0	Global Interrupt Generation Control Register	Go
25h-28h	R/W	0h	INT_EN_CFG1- INT_EN_CFG4	ADC Input Interrupt Generation Control Register	Go
29h-2Dh	R/W	0h	THRES_CFG0- THRES_CFG4	ADC Threshold Control Register	Go
2Eh- 30h	R/W	0h	THRESMAP_CFG0- THRESMAP_CFG2	ADC Threshold Mapping Register	Go
31h	R/W	0h	Matrix	Matrix Setting Register	Go
32h	R/W	0h	Mode	Mode Setting Register	Go



## 8.6.1 DEVICE\_ID register (Offset = 1h) [reset = 20h]

DEVICE\_ID is shown in 图 38 and described in 表 12.

Return to Summary Table.

This register represents the device ID of the TIC12400-Q1.

## 图 38. DEVICE\_ID Register

23	22	21	20	19	18	17	16	15	14	13	12		
	RESERVED												
	R-0h												
11	10	10 9 8 7 6 5 4 3 2 1 0											
RESERV ED				MAJOR			MIN	NOR					
R-0h				R-2h			R-	-0h					

LEGEND: R = Read only

### 表 12. DEVICE\_ID Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-11	RESERVED	R	0h	RESERVED
10-4	MAJOR	R	2h	These 7 bits represents major revision ID. For TIC12400-Q1 the major revision ID is 2h.
3-0	MINOR	R	0h	These 4 bits represents minor revision ID. For TIC12400-Q1 the minor revision ID is 0h.



## 8.6.2 INT\_STAT Register (Offset = 2h) [reset = 1h]

INT\_STAT is shown in 图 39 and described in 表 13.

Return to Summary Table.

This register records the information of the event as it occurs in the device. A READ command executed on this register clears its content and resets the register to its default value. The  $\overline{\text{INT}}$  pin is released at the rising edge of the  $\overline{\text{CS}}$  pin from the READ command.

图 39. INT\_STAT Register

23	22	21	20	19	18	17	16							
	RESERVED													
	R-0h													
15	14	13	12	11	10	9	8							
RESE	RVED	CHK_FAIL	ADC_DIAG	WET_DIAG	VS1	VS0	CRC_CALC							
R	-0h	RC-0h	RC-0h	RC-0h	RC-0h	RC-0h	RC-0h							
7	6	5	4	3	2	1	0							
UV	OV	TW	TSD	SSC	PRTY_FAIL	SPI_FAIL	POR							
RC-0h	RC-0h	RC-0h	RC-0h	RC-0h	RC-0h	RC-0h	RC-1h							

LEGEND: R = Read only; RC = Read to clear

### 表 13. INT\_STAT Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-14	RESERVED	R	0h	RESERVED
13	CHK_FAIL	RC	Oh	Oh = Default factory setting is successfully loaded upon device initialization or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = An error is detected when loading factory settings into the device upon device initialization.
				During device initialization, factory settings are programmed into the device to allow proper device operation. The device performs a self-check after the device is programmed to diagnose whether correct settings are loaded. If the self-check returns an error, the CHK_FAIL bit is flagged to logic 1 along with the POR bit. The host controller is then recommended to initiate a software reset (see section Software Reset) to re-initialize the device and allow correct settings to be reprogrammed.
12	ADC_DIAG	RC	Oh	Oh = No ADC self-diagnostic error is detected or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = ADC self-diagnostic error is detected.
				The ADC Self-Diagnostic feature (see section ADC Self-Diagnostic) can be activated to monitor the integrity of the internal ADC. The ADC_DIAG bit is flagged to logic 1 if an ADC error is diagnosed.
11	WET_DIAG	RC	Oh	Oh = No wetting current error is detected, or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = Wetting current error is detected.
				The Wetting Current Diagnostic feature (see section Wetting Current Diagnostic) can be activated to monitor the integrity of the internal current sources or sinks. The WET_DIAG bit is flagged to logic 1 if a wetting current error is diagnosed.



# 表 13. INT\_STAT Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
10	VS1	RC	Oh	0h = No $V_S$ voltage state change occurred with respect to VS1_THRES2A or VS1_THRES2B or the status got cleared after a READ command was executed on the INT_STAT register.
				1h = $V_S$ voltage state change occurred with respect to VS1_THRES2A or VS1_THRES2B.
				The VS1 interrupt bit indicates whether $V_S$ voltage state change occurred with respect to thresholds VS1_THRES2A and VS1_THRES2B if the $V_S$ Measurement feature (see section VS Measurement) is activated.
9	VS0	RC	Oh	0h = No $V_S$ voltage state change occurred with respect to VS0_THRES2A or VS0_THRES2B or the status got cleared after a READ command was executed on the INT_STAT register.
				1h = $V_S$ voltage state change occurred with respect to VS0_THRES2A or VS0_THRES2B.
				The VS0 interrupt bit indicates whether $V_S$ voltage state change occurred with respect to thresholds VS0_THRES2A and VS0_THRES2B if the $V_S$ Measurement feature (see section VS Measurement) is activated.
8	CRC_CALC	RC	Oh	Oh = CRC calculation is running, not started, or was acknowledged after a READ command was executed on the INT_STAT register.  1h = CRC calculation is finished.
				CRC calculation (see section Cyclic Redundancy Check (CRC)) can be triggered to make sure correct register values are programmed into the device. Once the calculation is completed, the CRC_CALC bit is flagged to logic 1 to indicate completion of the calculation, and the result can then be accessed from the CRC (offset = 3h) register.
7	UV	RC	Oh	0h = No under-voltage condition occurred or cleared on the $V_S$ pin, or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = Under-voltage condition occurred or cleared on the V <sub>S</sub> pin.
				When the UV bit is flagged to logic 1, it indicates the Under-Voltage (UV) event has occurred. The bit is also flagged to logic 1 when the event clears. For more details about the UV operation, please refer to section VS under-voltage (UV) condition.
6	OV	RC	Oh	0h = No over-voltage condition occurred or cleared on the $V_S$ pin, or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = Over-voltage condition occurred or cleared on the VS pin.
				When the OV bit is flagged to logic 1, it indicates the Over-Voltage (OV) event has occurred. The bit is also flagged to logic 1 when the event clears. For more details about the OV operation, please refer to section VS over-voltage (OV) condition.
5	TW	RC	Oh	Oh = No temperature warning event occurred or the event status got cleared after a READ command was executed on the INT_STAT register.
				1h = Temperature warning event occurred or cleared.
				When the TW bit is flagged to logic 1, it indicates the temperature warning event has occurred. The bit is also flagged to logic 1 when the event clears. For more details about the temperature warning operation, please refer to section Temperature Warning (TW)



# 表 13. INT\_STAT Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
4	TSD	RC	0h	Oh = No temperature Shutdown event occurred or the event status got cleared after a READ command was executed on the INT_STAT register.  1h = Temperature Shutdown event occurred or cleared.
				When the TSD bit is flagged to logic 1, it indicates the temperature shutdown event has occurred. The bit is also flagged to logic 1 when the event clears. For more details about the temperature shutdown operation, please refer to section Temperature shutdown (TSD)
3	SSC	RC	Oh	0h = No switch state change occurred or the status got cleared after a READ command was executed on the INT_STAT register.
				1h = Switch state change occurred.
				The Switch State Change (SSC) bit indicates whether input threshold crossing has occurred from switch inputs IN0 to IN23. This bit is also flagged to logic 1 after the first polling cycle is completed after device polling is triggered.
2	PRTY_FAIL	RC	Oh	Oh = No parity error occurred in the last received SI stream or the error status got cleared after a READ command was executed on the INT_STAT register.
				1h = Parity error occurred.
				When the PRTY_FAIL bit is flagged to logic 1, it indicates the last SPI Slave In (SI) transaction has a parity error. The device uses odd parity. If the total number of ones in the received data (including the parity bit) is an even number, the received data is discarded. The value of this register bit is mirrored to the PRTY_FLAG SPI status flag.
1	SPI_FAIL	RC	0h	Oh = 32 clock pulse during a $\overline{\text{CS}}$ = low sequence was detected or the error status got cleared after a READ command was executed on the INT_STAT register.  1h = SPI error occurred
				When the SPI_FAIL bit is flagged to logic 1, it indicates the last SPI Slave In (SI) transaction is invalid. To program a complete word, 32 bits of information must be entered into the device. The SPI logic counts the number of bits clocked into the IC and enables data latching only if exactly 32 bits have been clocked in. In case the word length exceeds or does not meet the required length, the SPI_FAIL bit is flagged to logic 1, and the data received is considered invalid. The value of this register bit is mirrored to the SPI_FLAG SPI status flag. Note the SPI_FAIL bit is not flagged if SCLK is not present.
0	POR	RC	1h	Oh = no Power-On-Reset (POR) event occurred or the status got cleared after a READ command was executed on the INT_STAT register.  1h = Power-On-Reset (POR) event occurred.
				The Power-On-Reset (POR) event occurred.  The Power-On-Reset (POR) interrupt bit indicates whether a reset event has occurred. A reset event sets the registers to their default values and re-initializes the device state machine. This bit is asserted after a successful power-on-reset, hardware reset, or software reset. The value of this register bit is mirrored to the POR SPI status flag.



## 8.6.3 CRC Register (Offset = 3h) [reset = FFFFh]

CRC is shown in 图 40 and described in 表 14.

Return to Summary Table.

This register returns the CRC-16-CCCIT calculation result. The microcontroller can compare this value with its own calculated value to ensure correct register settings are programmed to the device.

## 图 40. CRC Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
			RESE	RVED	)			CRC															
			R-	0h				R-FFFFh															

LEGEND: R = Read only

### 表 14. CRC Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-16	RESERVED	R	0h	Reserved
15-0	CRC	R	FFFFh	CRC-16-CCITT calculation result: Bit1: LSB of CRC Bit16: MSB or CRC



## 8.6.4 IN\_STAT\_MISC Register (Offset = 4h) [reset = 0h]

IN\_STAT\_MISC is shown in 图 41 and described in 表 15.

Return to Summary Table.

This register indicates current device status unrelated to switch input monitoring.

## 图 41. IN\_STAT\_MISC Register

23	22	21	20	19	18	17	16		
			RESE	RVED					
	R-0h								
15	14	13	12	11	10	9	8		
	RESERVED		ADC_D	IN3_D	IN2_D	IN1_D	IN0_D		
	R-0h		R-0h	R-0h	R-0h	R-0h	R-0h		
7	6	5	4	3	2	1	0		
VS1	VS1_STAT VS0_STAT			UV_STAT	OV_STAT	TW_STAT	TSD_STAT		
R	R-0h	R	-0h	R-0h	R-0h	R-0h	R-0h		

### 表 15. IN\_STAT\_MISC Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-13	RESERVED	R	0h	Reserved
12	ADC_D	R	0h	0h = No error is identified from ADC self-diagnostic. 1h = An error is identified from ADC self-diagnostic.
11	IN3_D	R	Oh	0h = Current sink on IN3 is operational. 1h = Current sink on IN3 is abnormal.
10	IN2_D	R	Oh	0h = Current sink on IN2 is operational. 1h = Current sink on IN2 is abnormal.
9	IN1_D	R	0h	0h = Current source on IN1 is operational. 1h = Current source on IN1 is abnormal.
8	INO_D	R	0h	0h = Current source on IN0 is operational. 1h = Current source on IN0 is abnormal.
7-6	VS1_STAT	R	Oh	$0h = V_S \text{ voltage is below threshold VS1\_THRES2A.} \\ 1h = V_S \text{ voltage is below threshold VS1\_THRES2B and equal to or above threshold VS1\_THRES2A.} \\ 2h = V_S \text{ voltage is equal to or above threshold VS1\_THRES2B.} \\ 3h = N/A.$
5-4	VS0_STAT	R	Oh	$0h = V_S \text{ voltage is below threshold VS0\_THRES2A.} \\ 1h = V_S \text{ voltage is below threshold VS0\_THRES2B and equal to or above threshold VS0\_THRES2A.} \\ 2h = V_S \text{ voltage is equal to or above threshold VS0\_THRES2B.} \\ 3h = N/A$
3	UV_STAT	R	0h	0h = V <sub>S</sub> voltage is above the under-voltage condition threshold. 1h = V <sub>S</sub> voltage is below the under-voltage condition threshold.
2	OV_STAT	R	0h	0h = V <sub>S</sub> voltage is below the over-voltage condition threshold. 1h = V <sub>S</sub> voltage is above the over-voltage condition threshold.
1	TW_STAT	R	Oh	$\begin{array}{l} \mbox{Oh = Device junction temperature is below the temperature warning threshold $T_{TW}$.} \\ \mbox{1h = Device junction temperature is above the temperature warning threshold $T_{TW}$.} \end{array}$



# 表 15. IN\_STAT\_MISC Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
0	TSD_STAT	R	Oh	$\begin{array}{ll} \mbox{Oh = Device junction temperature is below the temperature shutdown threshold $T_{TSD}$.} \\ \mbox{1h = Device junction temperature is above the temperature shutdown threshold $T_{TSD}$.} \end{array}$



## 8.6.5 IN\_STAT\_COMP Register (Offset = 5h) [reset = 0h]

IN\_STAT\_COMP is shown in 图 42 and described in 表 16.

Return to Summary Table.

This register indicates whether an input is below or above the comparator threshold when it is configured as comparator input mode.

图 42. IN\_STAT\_COMP Register

23	22	21	20	19	18	17	16
INC_23	INC_22	INC_21	INC_20	INC_19	INC_18	INC_17	INC_16
R-0h							
15	14	13	12	11	10	9	8
INC_15	INC_14	INC_13	INC_12	INC_11	INC_10	INC_9	INC_8
R-0h							
7	6	5	4	3	2	1	0
INC_7	INC_6	INC_5	INC_4	INC_3	INC_2	INC_1	INC_0
R-0h							

LEGEND: R = Read only

## 表 16. IN\_STAT\_COMP Register Field Descriptions

Bit	Field	Туре	Reset	Description
23	INC_23	R	0h	0h = Input IN23 is below the comparator threshold. 1h = Input IN23 is above the comparator threshold.
22	INC_22	R	0h	0h = Input IN22 is below the comparator threshold. 1h = Input IN22 is above the comparator threshold.
21	INC_21	R	0h	Oh = Input IN21 is below the comparator threshold.  1h = Input IN21 is above the comparator threshold.
20	INC_20	R	0h	0h = Input IN20 is below the comparator threshold. 1h = Input IN20 is above the comparator threshold.
19	INC_19	R	0h	Oh = Input IN19 is below the comparator threshold.  1h = Input IN19 is above the comparator threshold.
18	INC_18	R	0h	Oh = Input IN18 is below the comparator threshold.  1h = Input IN18 is above the comparator threshold.
17	INC_17	R	0h	0h = Input IN17 is below the comparator threshold. 1h = Input IN17 is above the comparator threshold.
16	INC_16	R	0h	0h = Input IN16 is below the comparator threshold. 1h = Input IN16 is above the comparator threshold.
15	INC_15	R	0h	0h = Input IN15 is below the comparator threshold. 1h = Input IN15 is above the comparator threshold.
14	INC_14	R	0h	Oh = Input IN14 is below the comparator threshold.  1h = Input IN14 is above the comparator threshold.
13	INC_13	R	0h	0h = Input IN13 is below the comparator threshold. 1h = Input IN13 is above the comparator threshold.
12	INC_12	R	0h	0h = Input IN12 is below the comparator threshold. 1h = Input IN12 is above the comparator threshold.
11	INC_11	R	0h	Oh = Input IN11 is below the comparator threshold.  1h = Input IN11 is above the comparator threshold.
10	INC_10	R	0h	0h = Input IN10 is below the comparator threshold. 1h = Input IN10 is above the comparator threshold.



# 表 16. IN\_STAT\_COMP Register Field Descriptions (接下页)

Field	Туре	Reset	Description
INC_9	R	0h	0h = Input IN9 is below the comparator threshold.
			1h = Input IN9 is above the comparator threshold.
INC_8	R	0h	0h = Input IN8 is below the comparator threshold.
			1h = Input IN8 is above the comparator threshold.
INC_7	R	0h	0h = Input IN7 is below the comparator threshold.
			1h = Input IN7 is above the comparator threshold.
INC_6	R	0h	0h = Input IN6 is below the comparator threshold.
			1h = Input IN6 is above the comparator threshold.
INC_5	R	0h	0h = Input IN5 is below the comparator threshold.
			1h = Input IN5 is above the comparator threshold.
INC_4	R	0h	0h = Input IN4 is below the comparator threshold.
			1h = Input IN4 is above the comparator threshold.
INC_3	R	0h	0h = Input IN3 is below the comparator threshold.
			1h = Input IN3 is above the comparator threshold.
INC_2	R	0h	0h = Input IN2 is below the comparator threshold.
			1h = Input IN2 is above the comparator threshold.
INC_1	R	0h	0h = Input IN1 is below the comparator threshold.
			1h = Input IN1 is above the comparator threshold.
INC_0	R	0h	0h = Input IN0 is below the comparator threshold.
			1h = Input IN0 is above the comparator threshold.
	INC_9 INC_8 INC_7 INC_6 INC_5 INC_4 INC_3 INC_2 INC_1	INC_9 R INC_8 R INC_7 R INC_6 R INC_5 R INC_4 R INC_3 R INC_2 R INC_1 R	INC_9 R 0h INC_8 R 0h INC_7 R 0h INC_6 R 0h INC_5 R 0h INC_4 R 0h INC_3 R 0h INC_3 R 0h INC_2 R 0h INC_2 R 0h



## 8.6.6 IN\_STAT\_ADC0 Register (Offset = 6h) [reset = 0h]

IN\_STAT\_ADC0 is shown in 图 43 and described in 表 17.

Return to Summary Table.

This register indicates whether an input is below or above the programmed threshold (for IN0-IN11) when it is configured as ADC input mode. For IN12-IN17, there are 2 thresholds and the register bits indicate whether the input is below, above or in-between the 2 thresholds.

图 43. IN\_STAT\_ADC0 Register

23	22	21	20	19	18	17	16	
INA	_17	INA	_16	INA	_15	INA_14		
R-	-0h	R-	0h	R-	0h	R-0h		
15	14	13	12	11	10	9	8	
INA	_13	INA	_12	INA_11	INA_10	INA_9	INA_8	
R-	-0h	R-	0h	R-0h	R-0h	R-0h	R-0h	
7	6	5	4	3	2	1	0	
INA_7	INA_6	INA_5	INA_4	INA_3	INA_2	INA_1	INA_0	
R-0h	R-0h	R-0h R-0h		R-0h	R-0h	R-0h	R-0h	

LEGEND: R = Read only

### 表 17. IN\_STAT\_ADC0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-22	INA_17	R	Oh	0h = Input IN17 is below threshold 2A.  1h = Input IN17 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN17 is equal to or above threshold 2B.  3h = N/A
21-20	INA_16	R	Oh	0h = Input IN16 is below threshold 2A.  1h = Input IN16 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN16 is equal to or above threshold 2B.  3h = N/A
19-18	INA_15	R	Oh	0h = Input IN15 is below threshold 2A.  1h = Input IN15 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN15 is equal to or above threshold 2B.  3h = N/A
17-16	INA_14	R	Oh	0h = Input IN14 is below threshold 2A.  1h = Input IN14 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN14 is equal to or above threshold 2B.  3h = N/A
15-14	INA_13	R	Oh	Oh = Input IN13 is below threshold 2A.  1h = Input IN13 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN13 is equal to or above threshold 2B.  3h = N/A
13-12	INA_12	R	Oh	Oh = Input IN12 is below threshold 2A.  1h = Input IN12 is below threshold 2B and equal to or above threshold 2A.  2h = Input IN12 is equal to or above threshold 2B.  3h = N/A



# 表 17. IN\_STAT\_ADC0 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
11	INA_11	R	0h	0h = Input IN11 is below configured threshold.
				1h = Input IN11 is above configured threshold.
10	INA_10	R	0h	0h = Input IN10 is below configured threshold.
				1h = Input IN10 is above configured threshold.
9	INA_9	R	0h	0h = Input IN9 is below configured threshold.
				1h = Input IN9 is above configured threshold.
8	INA_8	R	0h	-
			0.11	0h = Input IN8 is below configured threshold.
				1h = Input IN8 is above configured threshold.
7	INA_7	R	0h	0h = Input IN7 is below configured threshold.
				1h = Input IN7 is above configured threshold.
6	INA_6	R	0h	0h = Input IN6 is below configured threshold.
				1h = Input IN6 is above configured threshold.
5	INA_5	R	0h	· · · · · · · · · · · · · · · · · · ·
3	11V/_0		OII	0h = Input IN5 is below configured threshold.
				1h = Input IN5 is above configured threshold.
4	INA_4	R	0h	0h = Input IN4 is below configured threshold.
				1h = Input IN4 is above configured threshold.
3	INA_3	R	0h	0h = Input IN3 is below configured threshold.
				1h = Input IN3 is above configured threshold.
2	INA_2	R	0h	·
	11472		OII	0h = Input IN2 is below configured threshold.
				1h = Input IN2 is above configured threshold.
1	INA_1	R	0h	0h = Input IN1 is below configured threshold.
				1h = Input IN1 is above configured threshold.
0	INA_0	R	0h	0h = Input IN0 is below configured threshold.
				1h = Input INO is above configured threshold.



## 8.6.7 IN\_STAT\_ADC1 Register (Offset = 7h) [reset = 0h]

IN\_STAT\_ADC1 is shown in 图 44 and described in 表 18.

Return to Summary Table.

This register indicates whether an input is above or below the programmed thresholds 3A, 3B, and 3C when it is configured as ADC input mode. For IN23, there are 5 thresholds that can be programmed.

## 图 44. IN\_STAT\_ADC1 Register

23	22	21	20	19	18	17	16	15	14	13	12
					RESERVED	)					INA_23
					R-0h						R-0h
11	10	9	8	7	6	5	4	3	2	1	0
INA	_23	INA	_22	INA	INA_21						_18
R-	0h	R-	0h	R	-0h	R-	0h	R-	0h	R-	0h

LEGEND: R = Read only

### 表 18. IN\_STAT\_ADC1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-13	RESERVED	R	0h	Reserved
12-10	INA_23	R	0h	0h = Input IN23 is below threshold 3A.
				1h = Input IN23 is below threshold 3B and equal to or above threshold 3A.
				2h = Input IN23 is below threshold 3C and equal to or above threshold 3B.
				3h = Input IN23 is below threshold THRES8 and equal to or above threshold 3C.
				4h = Input IN23 is below threshold THRES9 and equal to or above threshold THRES8.
				5h = Input IN23 is equal to or above threshold THRES9.
9-8	INA_22	R	0h	0h = Input IN22 is below threshold 3A.
				1h = Input IN22 is below threshold 3B and equal to or above threshold 3A.
				2h = Input IN22 is below threshold 3C and equal to or above threshold 3B.
				3h = Input IN22 is equal to or above threshold 3C.
7-6	INA_21	R	0h	0h = Input IN21 is below threshold 3A.
				1h = Input IN21 is below threshold 3B and equal to or above threshold 3A.
				2h = Input IN21 is below threshold 3C and equal to or above threshold 3B.
				3h = Input IN21 is equal to or above threshold 3C.
5-4	INA_20	R	0h	0h = Input IN20 is below threshold 3A.
				1h = Input IN20 is below threshold 3B and equal to or above threshold 3A.
				2h = Input IN20 is below threshold 3C and equal to or above threshold 3B.
				3h = Input IN20 is equal to or above threshold 3C.
3-2	INA_19	R	0h	0h = Input IN19 is below threshold 3A.
				1h = Input IN19 is below threshold 3B and equal to or above threshold 3A.
				2h = Input IN19 is below threshold 3C and equal to or above threshold 3B.
				3h = Input IN19 is equal to or above threshold 3C.



# 表 18. IN\_STAT\_ADC1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
1-0	INA_18	R	0h	0h = Input is IN18 is below threshold 3A.
				1h = Input is IN18 is below threshold 3B and equal to or above threshold 3A.
				2h = Input is IN18 is below threshold 3C and equal to or above threshold 3B.
				3h = Input is IN18 is equal to or above threshold 3C.



# 8.6.8 IN\_STAT\_MATRIX0 Register (Offset = 8h) [reset = 0h]

IN\_STAT\_MATRIX0 is shown in 图 45 and described in 表 19.

Return to Summary Table.

This register indicates whether an input is below or above the programmed threshold in the matrix polling mode for switches connected to IN10-IN13.

## 图 45. IN\_STAT\_MATRIX0 Register

23	22	21	20	19	18	17	16
INMAT_13_IN9	INMAT_13_IN8	INMAT_13_IN7	INMAT_13_IN6	INMAT_13_IN5	INMAT_13_IN4	INMAT_12_IN9	INMAT_12_IN8
R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h
15	14	13	12	11	10	9	8
INMAT_12_IN7	INMAT_12_IN6	INMAT_12_IN5	INMAT_12_IN4	INMAT_11_IN9	INMAT_11_IN8	INMAT_11_IN7	INMAT_11_IN6
R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h
7	6	5	4	3	2	1	0
INMAT_11_IN5	INMAT_11_IN4	INMAT_10_IN9	INMAT_10_IN8	INMAT_10_IN7	INMAT_10_IN6	INMAT_10_IN5	INMAT_10_IN4
R-0h	-0h R-0h R-0h		R-0h	R-0h	R-0h	R-0h	R-0h

LEGEND: R = Read only

### 表 19. IN\_STAT\_MATRIX0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23	INMAT_13_IN9	R	Oh	0h = Input IN13 is below threshold while IN9 pulled to GND. 1h = Input IN13 is above threshold while IN9 pulled to GND.
22	INMAT_13_IN8	R	Oh	0h = Input IN13 is below threshold while IN8 pulled to GND. 1h = Input IN13 is above threshold while IN8 pulled to GND.
21	INMAT_13_IN7	R	Oh	0h = Input IN13 is below threshold while IN7 pulled to GND. 1h = Input IN13 is above threshold while IN7 pulled to GND.
20	INMAT_13_IN6	R	Oh	0h = Input IN13 is below threshold while IN6 pulled to GND. 1h = Input IN13 is above threshold while IN6 pulled to GND.
19	INMAT_13_IN5	R	0h	0h = Input IN13 is below threshold while IN5 pulled to GND. 1h = Input IN13 is above threshold while IN5 pulled to GND.
18	INMAT_13_IN4	R	Oh	0h = Input IN13 is below threshold while IN4 pulled to GND. 1h = Input IN13 is above threshold while IN4 pulled to GND.
17	INMAT_12_IN9	R	0h	0h = Input IN12 is below threshold while IN9 pulled to GND. 1h = Input IN12 is above threshold while IN9 pulled to GND.
16	INMAT_12_IN8	R	0h	0h = Input IN12 is below threshold while IN8 pulled to GND. 1h = Input IN12 is above threshold while IN8 pulled to GND.
15	INMAT_12_IN7	R	0h	0h = Input IN12 is below threshold while IN7 pulled to GND. 1h = Input IN12 is above threshold while IN7 pulled to GND.
14	INMAT_12_IN6	R	0h	0h = Input IN12 is below threshold while IN6 pulled to GND. 1h = Input IN12 is above threshold while IN6 pulled to GND.
13	INMAT_12_IN5	R	0h	Oh = Input IN12 is below threshold while IN5 pulled to GND.  1h = Input IN12 is above threshold while IN5 pulled to GND.
12	INMAT_12_IN4	R	0h	Oh = Input IN12 is below threshold while IN4 pulled to GND.  1h = Input IN12 is above threshold while IN4 pulled to GND.
11	INMAT_11_IN9	R	0h	Oh = Input IN11 is below threshold while IN9 pulled to GND.  1h = Input IN11 is above threshold while IN9 pulled to GND.
10	INMAT_11_IN8	R	Oh	0h = Input IN11 is below threshold while IN8 pulled to GND. 1h = Input IN11 is above threshold while IN8 pulled to GND.



# 表 19. IN\_STAT\_MATRIXO Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
9	INMAT_11_IN7	R	0h	0h = Input IN11 is below threshold while IN7 pulled to GND. 1h = Input IN11 is above threshold while IN7 pulled to GND.
8	INMAT_11_IN6	R	0h	0h = Input IN11 is below threshold while IN6 pulled to GND. 1h = Input IN11 is above threshold while IN6 pulled to GND.
7	INMAT_11_IN5	R	0h	0h = Input IN11 is below threshold while IN5 pulled to GND. 1h = Input IN11 is above threshold while IN5 pulled to GND.
6	INMAT_11_IN4	R	0h	0h = Input IN11 is below threshold while IN4 pulled to GND. 1h = Input IN11 is above threshold while IN4 pulled to GND.
5	INMAT_10_IN9	R	0h	0h = Input IN10 is below threshold while IN9 pulled to GND. 1h = Input IN10 is above threshold while IN9 pulled to GND.
4	INMAT_10_IN8	R	0h	0h = Input IN10 is below threshold while IN8 pulled to GND. 1h = Input IN10 is above threshold while IN8 pulled to GND.
3	INMAT_10_IN7	R	0h	0h = Input IN10 is below threshold while IN7 pulled to GND. 1h = Input IN10 is above threshold while IN7 pulled to GND.
2	INMAT_10_IN6	R	0h	0h = Input IN10 is below threshold while IN6 pulled to GND. 1h = Input IN10 is above threshold while IN6 pulled to GND.
1	INMAT_10_IN5	R	Oh	0h = Input IN10 is below threshold while IN5 pulled to GND. 1h = Input IN10 is above threshold while IN5 pulled to GND.
0	INMAT_10_IN4	R	Oh	0h = Input IN10 is below threshold while IN4 pulled to GND. 1h = Input IN10 is above threshold while IN4 pulled to GND.



### 8.6.9 IN\_STAT\_MATRIX1 Register (Offset = 9h) [reset = 0h]

IN\_STAT\_MATRIX1 is shown in 图 46 and described in 表 20.

Return to Summary Table.

This register indicates whether an input is below or above the programmed threshold in the matrix polling mode for switches connected to IN14-IN15. This register also indicates the status of IN0-IN11 with respect to. the common threshold THRES\_COM.

图 46. IN\_STAT\_MATRIX1 Register

23	22	21	20	19	18	17	16
IN11_COM	IN10_COM	IN9_COM	IN8_COM	IN7_COM	IN6_COM	IN5_COM	IN4_COM
R-0h							
15	14	13	12	11	10	9	8
IN3_COM	IN2_COM	IN1_COM	IN0_COM	INMAT_15_IN9	INMAT_15_IN8	INMAT_15_IN7	INMAT_15_IN6
R-0h							
7	6	5	4	3	2	1	0
INMAT_15_IN5	INMAT_15_IN4	INMAT_14_IN9	INMAT_14_IN8	INMAT_14_IN7	INMAT_14_IN6	INMAT_14_IN5	INMAT_14_IN4
R-0h							

LEGEND: R = Read only

## 表 20. IN\_STAT\_MATRIX1 Register Field Descriptions

Bit	Field	Туре	Reset	Description							
23	IN11_COM	R	0h	0h = Input IN11 below threshold THRES_COM							
				1h = Input IN11 equal to or above threshold THRES_COM							
22	IN10_COM	R	0h	0h = Input IN10 below threshold THRES_COM							
				1h = Input IN10 equal to or above threshold THRES_COM							
21	IN9_COM	R	0h	0h = Input IN9 below threshold THRES COM							
				1h = Input IN9 equal to or above threshold THRES_COM							
20	IN8_COM	R	0h	0h = Input IN8 below threshold THRES_COM							
				1h = Input IN8 equal to or above threshold THRES_COM							
19	IN7 COM	R	0h								
10	III _COM		011	0h = Input IN7 below threshold THRES_COM							
				1h = Input IN7 equal to or above threshold THRES_COM							
18	IN6_COM	R	0h	0h = Input IN6 below threshold THRES_COM							
				1h = Input IN6 equal to or above threshold THRES_COM							
17	IN5_COM	R	0h	0h = Input IN5 below threshold THRES_COM							
				1h = Input IN5 equal to or above threshold THRES_COM							
16	IN4_COM	R	0h	0h = Input IN4 below threshold THRES_COM							
				1h = Input IN4 equal to or above threshold THRES_COM							
15	IN3 COM	R	0h	0h = Input IN3 below threshold THRES_COM							
	_			1h = Input IN3 equal to or above threshold THRES_COM							
14	IN2_COM	R	0h								
14	IIVZ_COW	IX.	OII	0h = Input IN2 below threshold THRES_COM							
		_		1h = Input IN2 equal to or above threshold THRES_COM							
13	IN1_COM	R	0h	0h = Input IN1 below threshold THRES_COM							
				1h = Input IN1 equal to or above threshold THRES_COM							
12	IN0_COM	R	0h	0h = Input IN0 below threshold THRES_COM							
				1h = Input IN0 equal to or above threshold THRES_COM							
11	INMAT_15_IN9	R	0h	0h = Input IN15 below threshold while IN9 pulled to GND							
				·							
				1h = Input IN15 above threshold while IN9 pulled to GND							



# 表 20. IN\_STAT\_MATRIX1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
10	INMAT_15_IN8	R	0h	0h = Input IN15 below threshold while IN8 pulled to GND 1h = Input IN15 above threshold while IN8 pulled to GND
9	INMAT_15_IN7	R	0h	0h = Input IN15 below threshold while IN7 pulled to GND 1h = Input IN15 above threshold while IN7 pulled to GND
8	INMAT_15_IN6	R	0h	0h = Input IN15 below threshold while IN6 pulled to GND 1h = Input IN15 above threshold while IN6 pulled to GND
7	INMAT_15_IN5	R	0h	0h = Input IN15 below threshold while IN5 pulled to GND 1h = Input IN15 above threshold while IN5 pulled to GND
6	INMAT_15_IN4	R	0h	0h = Input IN15 below threshold while IN4 pulled to GND 1h = Input IN15 above threshold while IN4 pulled to GND
5	INMAT_14_IN9	R	0h	0h = Input IN14 below threshold while IN9 pulled to GND 1h = Input IN14 above threshold while IN9 pulled to GND
4	INMAT_14_IN8	R	0h	0h = Input IN14 below threshold while IN8 pulled to GND 1h = Input IN14 above threshold while IN8 pulled to GND
3	INMAT_14_IN7	R	Oh	0h = Input IN14 below threshold while IN7 pulled to GND 1h = Input IN14 above threshold while IN7 pulled to GND
2	INMAT_14_IN6	R	Oh	0h = Input IN14 below threshold while IN6 pulled to GND 1h = Input IN14 above threshold while IN6 pulled to GND
1	INMAT_14_IN5	R	0h	0h = Input IN14 below threshold while IN5 pulled to GND 1h = Input IN14 above threshold while IN5 pulled to GND
0	INMAT_14_IN4	R	Oh	0h = Input IN14 below threshold while IN4 pulled to GND 1h = Input IN14 above threshold while IN4 pulled to GND



### 8.6.10 ANA\_STAT0 Register (Offset = Ah) [reset = 0h]

ANA\_STAT0 is shown in 图 47 and described in 表 21.

Return to Summary Table.

### 图 47. ANA\_STAT0 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)		IN1_ANA													IN0_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 21. ANA\_STATO Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN1_ANA	R	0h	10-bits value of IN1 Bit 10: LSB
				Bit 19: MSB
9-0	INO_ANA	R	0h	10-bits value of IN0
				Bit 0: LSB
				Bit 9: MSB

### 8.6.11 ANA\_STAT1 Register (Offset = Bh) [reset = 0h]

ANA\_STAT1 is shown in 图 48 and described in 表 22.

Return to Summary Table.

### 图 48. ANA\_STAT1 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)		IN5_ANA													IN4_	ANA				
	R-	0h					R-	0h								R-	0h						

LEGEND: R = Read only

### 表 22. ANA\_STAT1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN3_ANA	R	0h	10-bits value of IN3
				Bit 10: LSB
				Bit 19: MSB
9-0	IN2_ANA	R	0h	10-bits value of IN2
				Bit 0: LSB
				Bit 9: MSB



## 8.6.12 ANA\_STAT2 Register (Offset = Ch) [reset = 0h]

ANA\_STAT2 is shown in 图 49 and described in 表 23.

Return to Summary Table.

### 图 49. ANA\_STAT2 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
	RESE	RVED			IN5_ANA											IN4_ANA								
	R-	0h						R-	0h									R-	0h					

LEGEND: R = Read only

## 表 23. ANA\_STAT2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN5_ANA	R	0h	10-bits value of IN5 Bit 10: LSB Bit 19: MSB
9-0	IN4_ANA	R	Oh	10-bits value of IN4 Bit 0: LSB Bit 9: MSB

### 8.6.13 ANA\_STAT3 Register (Offset = Dh) [reset = 0h]

ANA\_STAT3 is shown in 图 50 and described in 表 24.

Return to Summary Table.

### 图 50. ANA\_STAT3 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)					IN7_	ANA									IN6_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

#### 表 24. ANA\_STAT3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN7_ANA	R	0h	10-bits value of IN7
				Bit 10: LSB
				Bit 19: MSB
9-0	IN6_ANA	R	0h	10-bits value of IN6
				Bit 0: LSB
				Bit 9: MSB



### 8.6.14 ANA\_STAT4 Register (Offset = Eh) [reset = 0h]

ANA\_STAT4 is shown in 图 51 and described in 表 25.

Return to Summary Table.

### 图 51. ANA\_STAT4 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						IN9_	ANA									IN8_	ANA				
	R-	-0h						R-	0h									R-	0h				

LEGEND: R = Read only

#### 表 25. ANA\_STAT4 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN9_ANA	R	Oh	10-bits value of IN9 Bit 10: LSB Bit 19: MSB
9-0	IN8_ANA	R	Oh	10-bits value of IN8 Bit 0: LSB Bit 9: MSB

### 8.6.15 ANA\_STAT5 Register (Offset = Fh) [reset = 0h]

ANA\_STAT5 is shown in 图 52 and described in 表 26.

Return to Summary Table.

### 图 52. ANA\_STAT5 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						IN11	_ANA									IN10_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 26. ANA\_STAT5 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN11_ANA	R	0h	10-bits value of IN11 Bit 10: LSB
				Bit 19: MSB
9-0	IN10_ANA	R	0h	10-bits value of IN10
				Bit 0: LSB Bit 9: MSB



# 8.6.16 ANA\_STAT6 Register (Offset = 10h) [reset = 0h]

ANA\_STAT6 is shown in 图 53 and described in 表 27.

Return to Summary Table.

### 图 53. ANA\_STAT6 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						IN13	_ANA									IN12_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

## 表 27. ANA\_STAT6 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN13_ANA	R	Oh	10-bits value of IN13 Bit 10: LSB Bit 19: MSB
9-0	IN12_ANA	R	Oh	10-bits value of IN12 Bit 0: LSB Bit 9: MSB

### 8.6.17 ANA\_STAT7 Register (Offset = 11h) [reset = 0h]

ANA\_STAT7 is shown in 图 54 and described in 表 28.

Return to Summary Table.

### 图 54. ANA\_STAT7 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)					IN15_	_ANA									IN14	_ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 28. ANA\_STAT7 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN15_ANA	R	0h	10-bits value of IN15
				Bit 10: LSB
				Bit 19: MSB
9-0	IN14_ANA	R	0h	10-bits value of IN14
				Bit 0: LSB
				Bit 9: MSB



### 8.6.18 ANA\_STAT8 Register (Offset = 12h) [reset = 0h]

ANA\_STAT8 is shown in 图 55 and described in 表 29.

Return to Summary Table.

### 图 55. ANA\_STAT8 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						IN17	_ANA									IN16_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 29. ANA\_STAT8 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN17_ANA	R	0h	10-bits value of IN17 Bit 10: LSB
				Bit 19: MSB
9-0	IN16_ANA	R	0h	10-bits value of IN16
				Bit 0: LSB
				Bit 9: MSB

### 8.6.19 ANA\_STAT9 Register (Offset = 13h) [reset = 0h]

ANA\_STAT9 is shown in 图 56 and described in 表 30.

Return to Summary Table.

### 图 56. ANA\_STAT9 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						IN19_	_ANA									IN18_	ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 30. ANA\_STAT9 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN19_ANA	R	0h	10-bits value of IN19
				Bit 10: LSB
				Bit 19: MSB
9-0	IN18_ANA	R	0h	10-bits value of IN18
				Bit 0: LSB
				Bit 9: MSB



# 8.6.20 ANA\_STAT10 Register (Offset = 14h) [reset = 0h]

ANA\_STAT10 is shown in 图 57 and described in 表 31.

Return to Summary Table.

## 图 57. ANA\_STAT10 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
F	RESE	RVED						IN21	ANA									IN20_	ANA				
	R-	0h			R-0h													R-	0h				

LEGEND: R = Read only

### 表 31. ANA\_STAT10 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN21_ANA	R	Oh	10-bits value of IN21 Bit 10: LSB Bit 19: MSB
9-0	IN20_ANA	R	Oh	10-bits value of IN20 Bit 0: LSB Bit 9: MSB

### 8.6.21 ANA\_STAT11 Register (Offset = 15h) [reset = 0h]

ANA\_STAT11 is shown in 图 58 and described in 表 32.

Return to Summary Table.

### 图 58. ANA\_STAT11 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)					IN23	_ANA									IN22_	_ANA				
	R-	0h						R-	0h									R-	0h				

LEGEND: R = Read only

### 表 32. ANA\_STAT11 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	IN23_ANA	R	0h	10-bits value of IN23
				Bit 10: LSB
				Bit 19: MSB
9-0	IN22_ANA	R	0h	10-bits value of IN22
				Bit 0: LSB
				Bit 9: MSB



# 8.6.22 ANA\_STAT12 Register (Offset = 16h) [reset = 0h]

ANA\_STAT12 is shown in 图 59 and described in 表 33.

Return to Summary Table.

### 图 59. ANA\_STAT12 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED			ADC_SELF_ANA V <sub>S</sub> _ANA																		
	R-	0h			R-0h													R-	0h				

LEGEND: R = Read only

## 表 33. ANA\_STAT12 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	ADC_SELF_ANA	R	Oh	10-bits value of the ADC self-diagnosis Bit 10: LSB Bit 19: MSB
9-0	V <sub>S</sub> _ANA	R	Oh	10-bits value of V <sub>S</sub> measurement Bit 0: LSB Bit 9: MSB



# 8.6.23 CONFIG Register (Offset = 1Ah) [reset = 0h]

CONFIG is shown in 图 60 and described in 表 34.

Return to Summary Table.

# 图 60. CONFIG Register

23	22	21	20	19	18	17	16	
VS_RATIO	ADC_DIAG_T	WET_D_IN3_E N	WET_D_IN2_E N	WET_D_IN1_E N	WET_D_IN0_E N	VS_MEAS_EN	TW_CUR_DIS_ CSI	
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	
15	14	13	12 11		10	9	8	
DET_F	FILTER	TW_CUR_DIS_ CSO	INT_CONFIG	TRIGGER	POLL_EN	CRC_T	POLL_ACT_TI ME	
R/W	V-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	
7	6	5	4	3	2	1	0	
	POLL_ACT_TIME			POLL_TIME				
	R/W-0h			R/W-0h				

LEGEND: R/W = Read/Write

### 表 34. CONFIG Register Field Descriptions

Bit	Field	Туре	Reset	Description
23	VS_RATIO	R/W	0h	0h = Use voltage divider factor of 3 for the $V_S$ measurement 1h = Use voltage divider factor of 10 for the $V_S$ measurement
22	ADC_DIAG_T	R/W	Oh	For detailed descriptions for the ADC self-diagnostic feature, refer to section ADC Self-Diagnostic  Oh = Disable ADC self-diagnostic feature  1h = Enable ADC self-diagnostic feature
21	WET_D_IN3_EN	R/W	0h	0h = Disable wetting current diagnostic for input IN3 1h = Enable wetting current diagnostic for input IN3
20	WET_D_IN2_EN	R/W	0h	0h = Disable wetting current diagnostic for input IN2 1h = Enable wetting current diagnostic for input IN2
19	WET_D_IN1_EN	R/W	Oh	Oh = Disable wetting current diagnostic for input IN1 1h = Enable wetting current diagnostic for input IN1
18	WET_D_IN0_EN	R/W	0h	0h = Disable wetting current diagnostic for input IN0 1h = Enable wetting current diagnostic for input IN0
17	VS_MEAS_EN	R/W	0h	For detailed descriptions for the $\rm V_{\rm S}$ measurement, refer to section VS Measurement.
				0h = Disable V <sub>S</sub> measurement at the end of every polling cycle 1h = Enable V <sub>S</sub> measurement at the end of every polling cycle
16	TW_CUR_DIS_CSI	R/W	0h	0h = Enable wetting current reduction (to 2 mA) for 10mA and 15mA settings upon TW event for all inputs enabled with CSI.
				1h = Disable wetting current reduction (to 2 mA) for 10mA and 15mA settings upon TW event for all inputs enabled with CSI.
15-14	DET_FILTER	R/W	0h	For detailed descriptions for the detection filter, refer to section Detection Filter.
				0h = every sample is valid and taken for threshold evaluation
				1h = 2 consecutive and equal samples required to be valid data
				2h = 3 consecutive and equal samples required to be valid data
				3h = 4 consecutive and equal samples required to be valid data
13	TW_CUR_DIS_CSO	R/W	0h	0h = Enable wetting current reduction (to 2mA) for 10mA and 15mA settings upon TW event for all inputs enabled with CSO.
				1h = Disable wetting current reduction (to 2mA) for 10mA and 15mA settings upon TW event for all inputs enabled with CSO.



# 表 34. CONFIG Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
12	INT_CONFIG	R/W	Oh	For detailed descriptions for the $\overline{\text{INT}}$ pin assertion scheme, refer to section Interrupt Generation and /INT Assertion. $0h = \overline{\text{INT}} \text{ pin assertion scheme set to static}$ $1h = \overline{\text{INT}} \text{ pin assertion scheme set to dynamic}$
11	TRIGGER	R/W	Oh	When the TRIGGER bit is set to logic 1, normal device operation (wetting current activation and polling) starts. To stop device operation and keep the device in an idle state, de-assert this bit to 0. After device normal operation is triggered, if at any time the device setting needs to be re-configured, the microcontroller is required to first set the bit TRIGGER to logic 0 to stop device operation. Once the re-configuration is completed, the microcontroller can set the TRIGGER bit back to logic 1 to re-start device operation. If re-configuration is done on the fly without first stopping the device operation, false switch status could be reported and accidental interrupt might be issued. The following register bits are the exception and can be configured when TRIGGER bit is set to logic 1:  TRIGGER (bit 11 of the CONFIG register)  CRC_T (bit 9 of the CONFIG register)  RESET (bit 0 of the CONFIG register)  The CCP_CFG1 register  Oh = Stop TIC12400-Q1 from normal operation.  1h = Trigger TIC12400-Q1 normal operation
10	POLL_EN	R/W	Oh	Oh = Polling disabled. Device operates in continuous mode.  1h = Polling enabled and the device operates in one of the polling modes.
9	CRC_T	R/W	Oh	Set this bit to 1 to trigger a CRC calculation on all the configuration register bits. Once triggered, it is strongly recommended the SPI master does not change the content of the configuration registers until the CRC calculation is completed to avoid erroneous CRC calculation result. The TIC12400-Q1 sets the CRC_CALC interrupt bit and asserts the INT pin low when the CRC calculation is completed. The calculated result will be available in the CRC register. This bit self-clears back to 0 after CRC calculation is executed.  Oh = no CRC calculation triggered  1h = trigger CRC calculation
8-5	POLL_ACT_TIME	R/W	Oh	0h = 64μs 1h = 128μs 2h = 192μs 3h = 256μs 4h = 320μs 5h = 384μs 6h = 448μs 7h = 512μs 8h = 640μs 9h = 768μs Ah = 896μs Bh = 1024μs Ch = 2048μs Dh-15h = 512μs (most frequently-used setting)



# 表 34. CONFIG Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
4-1	POLL_TIME	R/W	0h	0h = 2ms
				1h = 4ms
				2h = 8ms
				3h = 16ms
				4h = 32ms
				5h = 48ms
				6h = 64ms
				7h = 128ms
				8h = 256ms
				9h = 512ms
				Ah = 1024ms
				Bh = 2048ms
				Ch = 4096ms
				Dh-15h = 8ms (most frequently-used setting)
0	RESET	R/W	0h	0h = No reset
				1h = Trigger software reset of the device.



# 8.6.24 IN\_EN Register (Offset = 1Bh) [reset = 0h]

IN\_EN is shown in 图 61 and described in 表 35.

Return to Summary Table.

# 图 61. IN\_EN Register

23	22	21	20	19	18	17	16
IN_EN_23	IN_EN_22	IN_EN_21	IN_EN_20	IN_EN_19	IN_EN_18	IN_EN_17	IN_EN_16
R/W-0h							
15	14	13	12	11	10	9	8
IN_EN_15	IN_EN_14	IN_EN_13	IN_EN_12	IN_EN_11	IN_EN_10	IN_EN_9	IN_EN_8
R/W-0h							
7	6	5	4	3	2	1	0
IN_EN_7	IN_EN_6	IN_EN_5	IN_EN_4	IN_EN_3	IN_EN_2	IN_EN_1	IN_EN_0
R/W-0h							

LEGEND: R/W = Read/Write

### 表 35. IN\_EN Register Field Descriptions

Bit	Field	Туре	Reset	Description
23	IN_EN_23	R/W	Oh	Oh = Input channel IN23 disabled. Polling sequence skips this channel  1h = Input channel IN23 enabled.
22	IN_EN_22	R/W	0h	Oh = Input channel IN22 disabled. Polling sequence skips this channel  1h = Input channel IN22 enabled.
21	IN_EN_21	R/W	0h	Oh = Input channel IN21 disabled. Polling sequence skips this channel  1h = Input channel IN21 enabled.
20	IN_EN_20	R/W	Oh	Oh = Input channel IN20 disabled. Polling sequence skips this channel  1h = Input channel IN20 enabled.
19	IN_EN_19	R/W	0h	Oh = Input channel IN19 disabled. Polling sequence skips this channel  1h = Input channel IN19 enabled.
18	IN_EN_18	R/W	0h	Oh = Input channel IN18 disabled. Polling sequence skips this channel  1h = Input channel IN18 enabled.
17	IN_EN_17	R/W	Oh	Oh = Input channel IN17 disabled. Polling sequence skips this channel  1h = Input channel IN17 enabled.
16	IN_EN_16	R/W	Oh	Oh = Input channel IN16 disabled. Polling sequence skips this channel  1h = Input channel IN16 enabled.
15	IN_EN_15	R/W	0h	Oh = Input channel IN15 disabled. Polling sequence skips this channel  1h = Input channel IN15 enabled.
14	IN_EN_14	R/W	0h	Oh = Input channel IN14 disabled. Polling sequence skips this channel  1h = Input channel IN14 enabled.
13	IN_EN_13	R/W	0h	Oh = Input channel IN13 disabled. Polling sequence skips this channel  1h = Input channel IN13 enabled.



# 表 35. IN\_EN Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
12	IN_EN_12	R/W	Oh	Oh = Input channel IN12 disabled. Polling sequence skips this channel  1h = Input channel IN12 enabled.
11	IN_EN_11	R/W	Oh	Oh = Input channel IN11 disabled. Polling sequence skips this channel  1h = Input channel IN11 enabled.
10	IN_EN_10	R/W	Oh	Oh = Input channel IN10 disabled. Polling sequence skips this channel  1h = Input channel IN10 enabled.
9	IN_EN_9	R/W	0h	0h = Input channel IN9 disabled. Polling sequence skips this channel 1h = Input channel IN9 enabled.
8	IN_EN_8	R/W	0h	0h = Input channel IN8 disabled. Polling sequence skips this channel 1h = Input channel IN8 enabled.
7	IN_EN_7	R/W	0h	0h = Input channel IN7 disabled. Polling sequence skips this channel 1h = Input channel IN7 enabled.
6	IN_EN_6	R/W	0h	0h = Input channel IN6 disabled. Polling sequence skips this channel 1h = Input channel IN6 enabled.
5	IN_EN_5	R/W	0h	0h = Input channel IN5 disabled. Polling sequence skips this channel 1h = Input channel IN5 enabled.
4	IN_EN_4	R/W	0h	0h = Input channel IN4 disabled. Polling sequence skips this channel 1h = Input channel IN4 enabled.
3	IN_EN_3	R/W	0h	0h = Input channel IN3 disabled. Polling sequence skips this channel 1h = Input channel IN3 enabled.
2	IN_EN_2	R/W	0h	0h = Input channel IN2 disabled. Polling sequence skips this channel 1h = Input channel IN2 enabled.
1	IN_EN_1	R/W	0h	0h = Input channel IN1 disabled. Polling sequence skips this channel 1h = Input channel IN1 enabled.
0	IN_EN_0	R/W	0h	0h = Input channel IN0 disabled. Polling sequence skips this channel 1h = Input channel IN0 enabled.

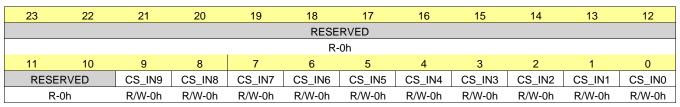


### 8.6.25 CS\_SELECT Register (Offset = 1Ch) [reset = 0h]

CS\_SELECT is shown in 图 62 and described in 表 36.

Return to Summary Table.

## 图 62. CS\_SELECT Register



LEGEND: R/W = Read/Write; R = Read only

#### 表 36. CS\_SELECT Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-10	RESERVED	R	0h	Reserved
9	CS_IN9	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
8	CS_IN8	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
7	CS_IN7	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
6	CS_IN6	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
5	CS_IN5	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
4	CS_IN4	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
3	CS_IN3	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
2	CS_IN2	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
1	CS_IN1	R/W	0h	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected
0	CS_IN0	R/W	Oh	0h = Current Source (CSO) selected 1h = Current Sink (CSI) selected



### 8.6.26 WC\_CFG0 Register (Offset = 1Dh) [reset = 0h]

WC\_CFG0 is shown in 图 63 and described in 表 37.

Return to Summary Table.

# 图 63. WC\_CFG0 Register

23	22	21	20	19	18	17	16	15	14	13	12	
	WC_IN11			WC_IN10			WC_IN8_IN9			WC_IN6_IN7		
	R/W-0h			R/W-0h		R/W-0h		R/W-0h				
11	10	9	8	7	6	5	4	3	2	1	0	
	WC_IN5			WC_IN4			WC_IN2_IN3	3	WC_IN0_IN1			
	R/W-0h			R/W-0h			R/W-0h		R/W-0h			

LEGEND: R/W = Read/Write

# 表 37. WC\_CFG0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-21	WC_IN11	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
20-18	WC_IN10	R/W	0h	Oh = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
17-15	WC_IN8_IN9	R/W	0h	Oh = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
14-12	WC_IN6_IN7	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
11-9	WC_IN5	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
8-6	WC_IN4	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current



# 表 37. WC\_CFG0 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
5-3	WC_IN2_IN3	R/W	0h	Oh = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
2-0	WC_IN0_IN1	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current



### 8.6.27 WC\_CFG1 Register (Offset = 1Eh) [reset = 0h]

WC\_CFG1 is shown in 图 64 and described in 表 38.

Return to Summary Table.

### 图 64. WC\_CFG1 Register

23	22	21	20	19	18	17	16	15	14	13	12	
RESERV ED	AUTO_S CALE_DI S_CSI	AUTO_S CALE_DI S_CSO		WC_IN23			WC_IN22		W	C_IN20_IN2	21	
R-0h	R/W-0h	R/W-0h		R/W-0h		R/W-0h			R/W-0h			
11	10	9	8	7	6	5	4	3	2	1	0	
W	C_IN18_IN	19	٧	VC_IN16_IN17	7	WC_IN14_IN15		WC_IN12_IN13		WC_IN12_IN13		3
	R/W-0h			R/W-0h			R/W-0h		 R/W-0h			

LEGEND: R/W = Read/Write; R = Read only

#### 表 38. WC\_CFG1 Register Field Descriptions

		_		ister Field Descriptions
Bit	Field	Туре	Reset	Description
24-23	RESERVED	R	0h	Reserved
22	AUTO_SCALE_DIS_CSI	R/W	0h	0h = Enable wetting current auto-scaling (to 2mA) in continuous mode for 10mA and 15mA settings upon switch closure for all inputs enabled with CSI
				1h = Disable wetting current auto-scaling (to 2mA) in continuous mode for 10mA and 15mA settings upon switch closure for all inputs enabled with CS
				For detailed descriptions for the wetting current auto-scaling, refer to section Wetting Current Auto-Scaling.
21	AUTO_SCALE_DIS_CSO	R/W	Oh	0h = Enable wetting current auto-scaling (to 2mA) in continuous mode for 10mA and 15mA settings upon switch closure for all inputs enabled with CSO
				1h = Disable wetting current auto-scaling (to 2mA) in continuous mode for 10mA and 15mA settings upon switch closure for all inputs enabled with CSO
				For detailed descriptions for the wetting current auto-scaling, refer to section Wetting Current Auto-Scaling.
20-18	WC_IN23	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
17-15	WC_IN22	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
14-12	WC_IN20_IN21	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current



# 表 38. WC\_CFG1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
11-9	WC_IN18_IN19	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
8-6	WC_IN16_IN17	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
5-3	WC_IN14_IN15	R/W	0h	0h = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current
2-0	WC IN12 IN13	R/W	0h	Oh = no wetting current
				1h = 1mA (typ.) wetting current
				2h = 2mA (typ.) wetting current
				3h = 5mA (typ.) wetting current
				4h = 10mA (typ.) wetting current
				5h-7h = 15mA (typ.) wetting current



### 8.6.28 CCP\_CFG0 Register (Offset = 1Fh) [reset = 0h]

CCP\_CFG0 is shown in 图 65 and described in 表 39.

Return to Summary Table.

# 图 65. CCP\_CFG0 Register

23	22	21	20	19	18	17	16	15	14	13	12
					RESE	RVED					
	R-0h										
11	10	9	8	7	6	5	4	3	2	1	0
	ı	RESERVED			CCP_TIME			WC_CCP	WC_CCP	WC_CCP	WC_CCP
					3	2	1	0			
R-0h						R-0h F			R-0h	R-0h	R-0h

LEGEND: R/W = Read/Write; R = Read only

## 表 39. CCP\_CFG0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-7	RESERVED	R	0h	Reserved
6-4	CCP_TIME	R/W	Oh	Wetting current activation time in CCP mode $0h = 64\mu s$ $1h = 128\mu s$ $2h = 192\mu s$ $3h = 256\mu s$ $4h = 320\mu s$ $5h = 384\mu s$ $6h = 448\mu s$
3	WC_CCP3	R/W	Oh	7h = 512µs  Wetting current setting for IN18 to IN23 in CCP mode 0h = 10mA (typ.) wetting current 1h = 15mA (typ.) wetting current
2	WC_CCP2	R/W	Oh	Wetting current setting for IN12 to IN17 in CCP mode  0h = 10mA (typ.) wetting current  1h = 15mA (typ.) wetting current
1	WC_CCP1	R/W	Oh	Wetting current setting for IN6 to IN11 in CCP mode  0h = 10mA (typ.) wetting current  1h = 15mA (typ.) wetting current
0	WC_CCP0	R/W	0h	Wetting current setting for IN0 to IN5 in CCP mode  0h = 10mA (typ.) wetting current  1h = 15mA (typ.) wetting current



# 8.6.29 CCP\_CFG1 Register (Offset = 20h) [reset = 0h]

CCP\_CFG1 is shown in 图 66 and described in 表 40.

Return to Summary Table.

### 图 66. CCP\_CFG1 Register

23	22	21	20	19	18	17	16
CCP_IN23	CCP_IN22	CCP_IN21	CCP_IN20	CCP_IN19	CCP_IN18	CCP_IN17	CCP_IN16
R/W-0h							
15	14	13	12	11	10	9	8
CCP_IN15	CCP_IN14	CCP_IN13	CCP_IN12	CCP_IN11	CCP_IN10	CCP_IN9	CCP_IN8
R/W-0h							
7	6	5	4	3	2	1	0
CCP_IN7	CCP_IN6	CCP_IN5	CCP_IN4	CCP_IN3	CCP_IN2	CCP_IN1	CCP_IN0
R/W-0h							

LEGEND: R/W = Read/Write

### 表 40. CCP\_CFG1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23	CCP_IN23	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated
22	CCP_IN22	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
21	CCP_IN21	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
20	CCP_IN20	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated
19	CCP_IN19	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
18	CCP_IN18	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
17	CCP_IN17	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
16	CCP_IN16	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated
15	CCP_IN15	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
14	CCP_IN14	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
13	CCP_IN13	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated
12	CCP_IN12	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
11	CCP_IN11	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated
10	CCP_IN10	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated



# 表 40. CCP\_CFG1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
9	CCP_IN9	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
8	CCP_IN8	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
7	CCP_IN7	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
6	CCP_IN6	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
5	CCP_IN5	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
4	CCP_IN4	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
3	CCP_IN3	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
2	CCP_IN2	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
1	CCP_IN1	R/W	0h	0h = no CCP wetting current 1h = CCP wetting current activated
0	CCP_IN0	R/W	Oh	0h = no CCP wetting current 1h = CCP wetting current activated



# 8.6.30 THRES\_COMP Register (Offset = 21h) [reset = 0h]

THRES\_COMP is shown in 图 67 and described in 表 41.

Return to Summary Table.

## 图 67. THRES\_COMP Register

23	22	21	20	19	18	17	16	
			RESE	RVED				
			R-	0h				
15	14	13	12	11	10	9	8	
	RESE	RVED		THRES_COM	1P_IN20_IN23	THRES_COMP_IN16_IN19		
	R-0	Dh		R/V	V-0h	R/W-0h		
7	6	5	4	3	2	1	0	
THRES_COM	THRES_COMP_IN12_IN15 THRES_COMP_IN8_IN11			THRES_COMP_IN4_IN7		THRES_COMP_IN0_IN3		
R/W	R/W-0h R/W-0h			R/V	V-0h	R/V	V-0h	

LEGEND: R/W = Read/Write; R = Read only

### 表 41. THRES\_COMP Register Field Descriptions

Bit	Field	Туре	Reset	Description
31-12	RESERVED	R	0h	Reserved
11-10	THRES_COMP_IN20_IN2	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN20 to IN23
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V
9-8	THRES_COMP_IN16_IN1	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN16 to IN19
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V
7-6	THRES_COMP_IN12_IN1 5	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN12 to IN15
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V
5-4	THRES_COMP_IN8_IN11	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN8 to IN11
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V
3-2	THRES_COMP_IN4_IN7	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN4 to IN7
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V



# 表 41. THRES\_COMP Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
1-0	THRES_COMP_IN0_IN3	R/W	0h	These 2 bits configures the comparator thresholds for input channels IN0 to IN3
				0h = comparator threshold set to 2V
				1h = comparator threshold set to 2.7V
				2h = comparator threshold set to 3V
				3h = comparator threshold set to 4V



# 8.6.31 INT\_EN\_COMP1 Register (Offset = 22h) [reset = 0h]

INT\_EN\_COMP1 is shown in 图 68 and described in 表 42.

Return to Summary Table.

#### 图 68. INT\_EN\_COMP1 Register

23	22	21	20	19	18	17	16	15	14	13	12	
INC_E	N_11	INC_EN_10		INC_EN_9		INC_EN_8		INC_EN_7		INC_EN_6		
R/W	'-0h	R/W	R/W-0h		R/W-0h		R/W-0h		R/W-0h		R/W-0h	
11	10	9	8	7	6	5	4	3	2	1	0	
INC_E	EN_5	INC_E	INC_EN_4		INC_EN_3		INC_EN_2		EN_1	INC_EN_0		
R/W	'-0h	R/W	-0h	R/W-0h		R/W-0h		R/W-0h		R/W-0h		

LEGEND: R/W = Read/Write

### 表 42. INT\_EN\_COMP1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-22	INC_EN_11	R/W	0h	0h = no interrupt generation for IN11
				1h = interrupt generation on rising edge above THRES_COMP_IN8_IN11 for IN11
				2h = interrupt generation on falling edge below THRES_COMP_IN8_IN11 for IN11
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN8_IN11 for IN11
21-20	INC_EN_10	R/W	0h	0h = no interrupt generation for IN10
				1h = interrupt generation on rising edge above THRES_COMP_IN8_IN11 for IN10
				2h = interrupt generation on falling edge below THRES_COMP_IN8_IN11 for IN10
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN8_IN11 for IN10
19-18	INC_EN_9	R/W	0h	0h = no interrupt generation for IN9
				1h = interrupt generation on rising edge above THRES_COMP_IN8_IN11 for IN9
				2h = interrupt generation on falling edge below THRES_COMP_IN8_IN11 for IN9
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN8_IN11 for IN9
17-16	INC_EN_8	R/W	0h	0h = no interrupt generation for IN8
				1h = interrupt generation on rising edge above THRES_COMP_IN8_IN11 for IN8
				2h = interrupt generation on falling edge below THRES_COMP_IN8_IN11 for IN8
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN8_IN11 for IN8
15-14	INC_EN_7	R/W	0h	0h = no interrupt generation for IN7
				1h = interrupt generation on rising edge above THRES_COMP_IN4_IN7 for IN7
				2h = interrupt generation on falling edge below THRES_COMP_IN4_IN7 for IN7
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN4_IN7 for IN7



# 表 42. INT\_EN\_COMP1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description				
13-12	INC_EN_6	R/W	0h	0h = no interrupt generation for IN6				
				1h = interrupt generation THRES_COMP_IN4_IN7 for IN6	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN4_IN7 for IN6	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN4_IN7 for IN6	falling	and	rising	edge of
11-10	INC_EN_5	R/W	0h	0h = no interrupt generation for IN5				
				1h = interrupt generation THRES_COMP_IN4_IN7 for IN5	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN4_IN7 for IN5	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN4_IN7 for IN5	falling	and	rising	edge of
9-8	INC_EN_4	R/W	0h	0h = no interrupt generation for IN4				
				1h = interrupt generation THRES_COMP_IN4_IN7 for IN4	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN4_IN7 for IN4	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN4_IN7 for IN4	falling	and	rising	edge of
7-6	INC_EN_3	R/W	0h	0h = no interrupt generation for IN3				
				1h = interrupt generation THRES_COMP_IN0_IN3 for IN3	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN0_IN3 for IN3	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN0_IN3 for IN3	falling	and	rising	edge of
5-4	INC_EN_2	R/W	0h	0h = no interrupt generation for IN2				
				1h = interrupt generation THRES_COMP_IN0_IN3 for IN2	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN0_IN3 for IN2	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN0_IN3 for IN2	falling	and	rising	edge of
3-2	INC_EN_1	R/W	0h	0h = no interrupt generation for IN1				
				1h = interrupt generation THRES_COMP_IN0_IN3 for IN1	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN0_IN3 for IN1	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN0_IN3 for IN1	falling	and	rising	edge of
1-0	INC_EN_0	R/W	0h	0h = no interrupt generation for IN0				
				1h = interrupt generation THRES_COMP_IN0_IN3 for IN0	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN0_IN3 for IN0	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN0_IN3 for IN0	falling	and	rising	edge of



# 8.6.32 INT\_EN\_COMP2 Register (Offset = 23h) [reset = 0h]

INT\_EN\_COMP2 is shown in 图 69 and described in 表 43.

Return to Summary Table.

#### 图 69. INT\_EN\_COMP2 Register

23	22	21	20	19	18	17	16	15	14	13	12
INC_E	INC_EN_23 INC_EN_22		INC_EN_21		INC_EN_20		INC_EN_19		INC_EN_18		
R/W	'-0h	R/W	-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h
11	10	9	8	7	6	5	4	3	2	1	0
INC_E	N_17	INC_E	N_16	INC_E	N_15	INC_E	N_14	INC_E	N_13	INC_E	N_12
R/W	'-0h	R/W	-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h

LEGEND: R/W = Read/Write

### 表 43. INT\_EN\_COMP2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-22	INC_EN_23	R/W	Oh	0h = no interrupt generation for IN23 1h = interrupt generation on rising edge above THRES_COMP_IN20_IN23 for IN23
				2h = interrupt generation on falling edge below THRES_COMP_IN20_IN23 for IN23
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN20_IN23 for IN23
21-20	INC_EN_22	R/W	0h	0h = no interrupt generation for IN22
				1h = interrupt generation on rising edge above THRES_COMP_IN20_IN23 for IN22
				2h = interrupt generation on falling edge below THRES_COMP_IN20_IN23 for IN22
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN20_IN23 for IN22
19-18	INC_EN_21	R/W	0h	0h = no interrupt generation for IN21
				1h = interrupt generation on rising edge above THRES_COMP_IN20_IN23 for IN21
				2h = interrupt generation on falling edge below THRES_COMP_IN20_IN23 for IN21
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN20_IN23 for IN21
17-16	INC_EN_20	R/W	0h	0h = no interrupt generation for IN20
				1h = interrupt generation on rising edge above THRES_COMP_IN20_IN23 for IN20
				2h = interrupt generation on falling edge below THRES_COMP_IN20_IN23 for IN20
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN20_IN23 for IN20
15-14	INC_EN_19	R/W	0h	0h = no interrupt generation for IN19
				1h = interrupt generation on rising edge above THRES_COMP_IN16_IN19 for IN19
				2h = interrupt generation on falling edge below THRES_COMP_IN16_IN19 for IN19
				3h = interrupt generation on falling and rising edge of THRES_COMP_IN16_IN19 for IN19



# 表 43. INT\_EN\_COMP2 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description				
13-12	INC_EN_18	R/W	0h	0h = no interrupt generation for IN18				
				1h = interrupt generation THRES_COMP_IN16_IN19 for IN18	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN16_IN19 for IN18	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN16_IN19 for IN18	falling	and	rising	edge of
11-10	INC_EN_17	R/W	0h	0h = no interrupt generation for IN17				
				1h = interrupt generation THRES_COMP_IN16_IN19 for IN17	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN16_IN19 for IN17	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN16_IN19 for IN17	falling	and	rising	edge of
9-8	INC_EN_16	R/W	0h	0h = no interrupt generation for IN16				
				1h = interrupt generation THRES_COMP_IN16_IN19 for IN16	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN16_IN19 for IN16	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN16_IN19 for IN16	falling	and	rising	edge of
7-6	INC_EN_15	R/W	0h	0h = no interrupt generation for IN15				
				1h = interrupt generation THRES_COMP_IN12_IN15 for IN15	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN12_IN15 for IN15	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN12_IN15 for IN15	falling	and	rising	edge of
5-4	INC_EN_14	R/W	0h	0h = no interrupt generation for IN14				
				1h = interrupt generation THRES_COMP_IN12_IN15 for IN14	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN12_IN15 for IN14	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN12_IN15 for IN14	falling	and	rising	edge of
3-2	INC_EN_13	R/W	0h	0h = no interrupt generation for IN13				
				1h = interrupt generation THRES_COMP_IN12_IN15 for IN13	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN12_IN15 for IN13	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN12_IN15 for IN13	falling	and	rising	edge of
1-0	INC_EN_12	R/W	0h	0h = no interrupt generation for IN12				
				1h = interrupt generation THRES_COMP_IN12_IN15 for IN12	on	rising	edge	above
				2h = interrupt generation THRES_COMP_IN12_IN15 for IN12	on	falling	edge	below
				3h = interrupt generation on THRES_COMP_IN12_IN15 for IN12	falling	and	rising	edge of



# 8.6.33 INT\_EN\_CFG0 Register (Offset = 24h) [reset = 0h]

INT\_EN\_CFG0 is shown in 图 70 and described in 表 44.

Return to Summary Table.

#### 图 70. INT\_EN\_CFG0 Register

23	22	21	20	19	18	17	16			
	RESERVED									
	R-0h									
15	14	13	12	11	10	9	8			
	RESE	RVED		ADC_DIAG_EN	WET_DIAG_E N	VS1_EN	VS0_EN			
	R-	0h		R/W-0h	R/W-0h	R/W-0h	R/W-0h			
7	6	5	4	3	2	1	0			
CRC_CALC_E N	UV_EN	OV_EN	TW_EN	TSD_EN	SSC_EN	PRTY_FAIL_E N	SPI_FAIL_EN			
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h			

LEGEND: R/W = Read/Write; R = Read only

#### 表 44. INT\_EN\_CFG0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-12	RESERVED	R	0h	Reserved
11	ADC_DIAG_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to ADC error disabled. 1h = $\overline{\text{INT}}$ pin assertion due to ADC error enabled.
10	WET_DIAG_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to wetting current error disabled.  1h = $\overline{\text{INT}}$ pin assertion due to wetting current error enabled.
9	VS1_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to VS1 threshold crossing disabled.  1h = $\overline{\text{INT}}$ pin assertion due to VS1 threshold crossing enabled.
8	VS0_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to VS0 threshold crossing disabled.  1h = $\overline{\text{INT}}$ pin assertion due to VS0 threshold crossing enabled.
7	CRC_CALC_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to CRC calculation completion disabled. 1h = $\overline{\text{INT}}$ pin assertion due to CRC calculation completion enabled.
6	UV_EN	R/W	0h	0h = INT pin assertion due to UV event disabled.  1h = INT pin assertion due to UV event enabled.
5	OV_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to OV event disabled.  1h = $\overline{\text{INT}}$ pin assertion due to OV event enabled.
4	TW_EN	R/W	0h	0h = INT pin assertion due to TW event disabled. 1h = INT pin assertion due to TW event enabled.
3	TSD_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to TSD event disabled.  1h = $\overline{\text{INT}}$ pin assertion due to TSD event enabled.
2	SSC_EN	R/W	0h	0h = $\overline{\text{INT}}$ pin assertion due to SSC event disabled.  1h = $\overline{\text{INT}}$ pin assertion due to SSC event enabled.
1	PRTY_FAIL_EN	R/W	0h	0h = INT pin assertion due to parity fail event disabled.  1h = INT pin assertion due to parity fail event enabled.
0	SPI_FAIL_EN	R/W	0h	0h = INT pin assertion due to SPI fail event disabled.  1h = INT pin assertion due to SPI fail event enabled.



### 8.6.34 INT\_EN\_CFG1 Register (Offset = 25h) [reset = 0h]

INT\_EN\_CFG1 is shown in 图 71 and described in 表 45.

Return to Summary Table.

#### 图 71. INT\_EN\_CFG1 Register

23	22	21	20	19	18	17	16	15	14	13	12
IN11	_EN	IN10	_EN	IN9_	_EN	IN8_	_EN	IN7_	_EN	IN6_	_EN
R/W	/-0h	R/W	'-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h
11	10	9	8	7	6	5	4	3	2	1	0
IN5_	_EN	IN4_	EN	IN3_	_EN	IN2_	_EN	IN1_	_EN	INO_	_EN
R/W	/-0h	R/W	'-0h	R/W	′-0h	R/W	/-0h	R/W	/-0h	R/W	/-0h

LEGEND: R/W = Read/Write

### 表 45. INT\_EN\_CFG1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-22	IN11_EN	R/W	Oh	0h = no interrupt generation for IN11 1h = interrupt generation on rising edge above THRESx for IN11 2h = interrupt generation on falling edge below THRESx for IN11 3h = interrupt generation on falling and rising edge of THRESx for IN11
21-20	IN10_EN	R/W	Oh	0h = no interrupt generation for IN10 1h = interrupt generation on rising edge above THRESx for IN10 2h = interrupt generation on falling edge below THRESx for IN10 3h = interrupt generation on falling and rising edge of THRESx for IN10
19-18	IN9_EN	R/W	Oh	Oh = no interrupt generation for IN9  1h = interrupt generation on rising edge above THRESx for IN9  2h = interrupt generation on falling edge below THRESx for IN9  3h = interrupt generation on falling and rising edge of THRESx for IN9
17-16	IN8_EN	R/W	Oh	Oh = no interrupt generation for IN8  1h = interrupt generation on rising edge above THRESx for IN8  2h = interrupt generation on falling edge below THRESx for IN8  3h = interrupt generation on falling and rising edge of THRESx for IN8
15-14	IN7_EN	R/W	Oh	0h = no interrupt generation for IN7 1h = interrupt generation on rising edge above THRESx for IN7 2h = interrupt generation on falling edge below THRESx for IN7 3h = interrupt generation on falling and rising edge of THRESx for IN7
13-12	IN6_EN	R/W	Oh	0h = no interrupt generation for IN6 1h = interrupt generation on rising edge above THRESx for IN6 2h = interrupt generation on falling edge below THRESx for IN6 3h = interrupt generation on falling and rising edge of THRESx for IN6
11-10	IN5_EN	R/W	Oh	Oh = no interrupt generation for IN5  1h = interrupt generation on rising edge above THRESx for IN5  2h = interrupt generation on falling edge below THRESx for IN5  3h = interrupt generation on falling and rising edge of THRESx for IN5



# 表 45. INT\_EN\_CFG1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
9-8	IN4_EN	R/W	0h	0h = no interrupt generation for IN4
				1h = interrupt generation on rising edge above THRESx for IN4
				2h = interrupt generation on falling edge below THRESx for IN4
				3h = interrupt generation on falling and rising edge of THRESx for IN4
7-6	IN3_EN	R/W	0h	0h = no interrupt generation for IN3
				1h = interrupt generation on rising edge above THRESx for IN3
				2h = interrupt generation on falling edge below THRESx for IN3
				3h = interrupt generation on falling and rising edge of THRESx for IN3
5-4	IN2_EN	R/W	0h	0h = no interrupt generation for IN2
				1h = interrupt generation on rising edge above THRESx for IN2
				2h = interrupt generation on falling edge below THRESx for IN2
				3h = interrupt generation on falling and rising edge of THRESx for IN2
3-2	IN1_EN	R/W	0h	0h = no interrupt generation for IN1
				1h = interrupt generation on rising edge above THRESx for IN1
				2h = interrupt generation on falling edge below THRESx for IN1
				3h = interrupt generation on falling and rising edge of THRESx for IN1
1-0	IN0_EN	R/W	0h	0h = no interrupt generation for IN0
				1h = interrupt generation on rising edge above THRESx for IN0
				2h = interrupt generation on falling edge below THRESx for IN0
				3h = interrupt generation on falling and rising edge of THRESx for IN0



### 8.6.35 INT\_EN\_CFG2 Register (Offset = 26h) [reset = 0h]

INT\_EN\_CFG2 is shown in 图 72 and described in 表 46.

Return to Summary Table.

#### 图 72. INT\_EN\_CFG2 Register

23	22	21	20	19	18	17	16	15	14	13	12	
	IN17_EN				IN16_EN				IN15_EN			
	R/W	'-0h			R/V	V-0h			R/V	V-0h		
11	10	9	8	7	6	5	4	3	2	1	0	
	IN14	_EN		IN13_EN				IN12_EN				
	R/W	'-0h			R/V	V-0h		R/W-0h				

LEGEND: R/W = Read/Write

### 表 46. INT\_EN\_CFG2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	IN17_EN	R/W	0h	xx00: no interrupt generation for IN17 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN17
				xx10: interrupt generation on falling edge below THRES2A for IN17
				xx11: interrupt generation on falling and rising edge of THRES2A for IN17
				00xx: no interrupt generation for IN17 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN17
				10xx: interrupt generation on falling edge below THRES2B for IN17
				11xx: interrupt generation on falling and rising edge of THRES2B for IN17
19-16	IN16_EN	R/W	0h	xx00: no interrupt generation for IN16 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN16
				xx10: interrupt generation on falling edge below THRES2A for IN16
				xx11: interrupt generation on falling and rising edge of THRES2A for IN16
				00xx: no interrupt generation for IN16 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN16
				10xx: interrupt generation on falling edge below THRES2B for IN16
				11xx: interrupt generation on falling and rising edge of THRES2B for IN16
15-12	IN15_EN	R/W	0h	xx00: no interrupt generation for IN15 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN15
				xx10: interrupt generation on falling edge below THRES2A for IN15
				xx11: interrupt generation on falling and rising edge of THRES2A for IN15
				00xx: no interrupt generation for IN15 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN15
				10xx: interrupt generation on falling edge below THRES2B for IN15
				11xx: interrupt generation on falling and rising edge of THRES2B for IN15



# 表 46. INT\_EN\_CFG2 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
11-8	IN14_EN	R/W	0h	xx00: no interrupt generation for IN14 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN14
				xx10: interrupt generation on falling edge below THRES2A for IN14
				xx11: interrupt generation on falling and rising edge of THRES2A for IN14
				00xx: no interrupt generation for IN14 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN14
				10xx: interrupt generation on falling edge below THRES2B for IN14
				11xx: interrupt generation on falling and rising edge of THRES2B for IN14
7-4	IN13_EN	R/W	0h	xx00: no interrupt generation for IN13 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN13
				xx10: interrupt generation on falling edge below THRES2A for IN13
				xx11: interrupt generation on falling and rising edge of THRES2A for IN13
				00xx: no interrupt generation for IN13 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN13
				10xx: interrupt generation on falling edge below THRES2B for IN13
				11xx: interrupt generation on falling and rising edge of THRES2B for IN13
3-0	IN12_EN	R/W	0h	xx00: no interrupt generation for IN12 w.r.t. THRES2A
				xx01: interrupt generation on rising edge above THRES2A for IN12
				xx10: interrupt generation on falling edge below THRES2A for IN12
				xx11: interrupt generation on falling and rising edge of THRES2A for IN12
				00xx: no interrupt generation for IN12 w.r.t. THRES2B
				01xx: interrupt generation on rising edge above THRES2B for IN12
				10xx: interrupt generation on falling edge below THRES2B for IN12
				11xx: interrupt generation on falling and rising edge of THRES2B for IN12



## 8.6.36 INT\_EN\_CFG3 Register (Offset = 27h) [reset = 0h]

INT\_EN\_CFG3 is shown in 图 73 and described in 表 47.

Return to Summary Table.

#### 图 73. INT\_EN\_CFG3 Register

23	22	21	20	19	18	17	16	15	14	13	12
		IN21	_EN					IN20	_EN		
		R/W	/-0h					R/W	/-0h		
11	10	9	8	7	6	5	4	3	2	1	0
		IN19	_EN					IN18	_EN		
		R/W	/-0h					R/W	/-0h		

LEGEND: R/W = Read/Write

### 表 47. INT\_EN\_CFG3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-18	IN21_EN	R/W	0h	xxxx00: no interrupt generation for IN21 w.r.t. THRES3A
				xxxx01: interrupt generation on rising edge above THRES3A for IN21
				xxxx10: interrupt generation on falling edge below THRES3A for IN21
				xxxx11: interrupt generation on falling and rising edge of THRES3A for IN21
				xx00xx: no interrupt generation for IN21 w.r.t. THRES3B
				xx01xx: interrupt generation on rising edge above THRES3B for IN21
				xx10xx: interrupt generation on falling edge below THRES3B for IN21
				xx11xx: interrupt generation on falling and rising edge of THRES3B for IN21
				00xxxx: no interrupt generation for IN21 w.r.t. THRES3C
				01xxxx: interrupt generation on rising edge above THRES3C for IN21
				10xxxx: interrupt generation on falling edge below THRES3C for IN21
				11xxxx: interrupt generation on falling and rising edge of THRES3C for IN21
17-12	IN20_EN	R/W	0h	xxxx00: no interrupt generation for IN20 w.r.t. THRES3A
				xxxx01: interrupt generation on rising edge above THRES3A for IN20
				xxxx10: interrupt generation on falling edge below THRES3A for IN20
				xxxx11: interrupt generation on falling and rising edge of THRES3A for IN20
				xx00xx: no interrupt generation for IN20 w.r.t. THRES3B
				xx01xx: interrupt generation on rising edge above THRES3B for IN20
				xx10xx: interrupt generation on falling edge below THRES3B for IN20
				xx11xx: interrupt generation on falling and rising edge of THRES3B for IN20
				00xxxx: no interrupt generation for IN20 w.r.t. THRES3C
				01xxxx: interrupt generation on rising edge above THRES3C for IN20
				10xxxx: interrupt generation on falling edge below THRES3C for IN20
				11xxxx: interrupt generation on falling and rising edge of THRES3C for IN20



# 表 47. INT\_EN\_CFG3 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
11-6	IN19_EN	R/W	0h	xxxx00: no interrupt generation for IN19 w.r.t. THRES3A
				xxxx01: interrupt generation on rising edge above THRES3A for IN19
				xxxx10: interrupt generation on falling edge below THRES3A for IN19
				xxxx11: interrupt generation on falling and rising edge of THRES3A for IN19
				xx00xx: no interrupt generation for IN19 w.r.t. THRES3B
				xx01xx: interrupt generation on rising edge above THRES3B for IN19
				xx10xx: interrupt generation on falling edge below THRES3B for IN19
				xx11xx: interrupt generation on falling and rising edge of THRES3B for IN19
				00xxxx: no interrupt generation for IN19 w.r.t. THRES3C
				01xxxx: interrupt generation on rising edge above THRES3C for IN19
				10xxxx: interrupt generation on falling edge below THRES3C for IN19
				11xxxx: interrupt generation on falling and rising edge of THRES3C for IN19
5-0	IN18_EN	R/W	0h	xxxx00: no interrupt generation for IN18 w.r.t. THRES3A
				xxxx01: interrupt generation on rising edge above THRES3A for IN18
				xxxx10: interrupt generation on falling edge below THRES3A for IN18
				xxxx11: interrupt generation on falling and rising edge of THRES3A for IN18
				xx00xx: no interrupt generation for IN18 w.r.t. THRES3B
				xx01xx: interrupt generation on rising edge above THRES3B for IN18
				xx10xx: interrupt generation on falling edge below THRES3B for IN18
				xx11xx: interrupt generation on falling and rising edge of THRES3B for IN18
				00xxxx: no interrupt generation for IN18 w.r.t. THRES3C
				01xxxx: interrupt generation on rising edge above THRES3C for IN18
				10xxxx: interrupt generation on falling edge below THRES3C for IN18
				11xxxx: interrupt generation on falling and rising edge of THRES3C for IN18



### 8.6.37 INT\_EN\_CFG4 Register (Offset = 28h) [reset = 0h]

INT\_EN\_CFG4 is shown in 图 74 and described in 表 48.

Return to Summary Table.

#### 图 74. INT\_EN\_CFG4 Register

23	22	21	20	19	18	17	16	15	14	13	12
	VS_TH	l1_EN			VS_TH	HO_EN			IN23	B_EN	
	R/W	/-0h			R/W	/-0h			R/V	V-0h	
11	10	9	8	7	6	5	4	3	2	1	0
		IN23	_EN					IN22	2_EN		
		R/W	/-0h					R/W	V-0h		

LEGEND: R/W = Read/Write

### 表 48. INT\_EN\_CFG4 Register Field Descriptions

			0.0	
Bit	Field	Туре	Reset	Description
23-20	VS_TH1_EN	R/W	0h	xx00: no interrupt generation for V <sub>S</sub> w.r.t. VS1_THRES2A
				xx01: interrupt generation on rising edge above VS1_THRES2A for $\ensuremath{\text{V}_{\text{S}}}$
				xx10: interrupt generation on falling edge below VS1_THRES2A for $\ensuremath{\text{V}_{\text{S}}}$
				xx11: interrupt generation on falling and rising edge of VS1_THRES2A for $\rm V_{S}$
				00xx: no interrupt generation for V <sub>S</sub> w.r.t. VS1_THRES2B
				01xx: interrupt generation on rising edge above VS1_THRES2B for $\ensuremath{V_S}$
				10xx: interrupt generation on falling edge below VS1_THRES2B for $\rm V_{\rm S}$
				11xx: interrupt generation on falling and rising edge of VS1_THRES2B for $\rm V_{S}$
19-16	VS_TH0_EN	R/W	0h	xx00: no interrupt generation for V <sub>S</sub> w.r.t. VS0_THRES2A
				xx01: interrupt generation on rising edge above VS0_THRES2A for $\rm V_{\rm S}$
				xx10: interrupt generation on falling edge below VS0_THRES2A for $\rm V_{\rm S}$
				xx11: interrupt generation on falling and rising edge of VS0_THRES2A for VS
				00xx: no interrupt generation for V <sub>S</sub> w.r.t. VS0_THRES2B
				01xx: interrupt generation on rising edge above VS0_THRES2B for $\rm V_{S}$
				10xx: interrupt generation on falling edge below VS0_THRES2B for $V_{\rm S}$
				11xx: interrupt generation on falling and rising edge of VS0_THRES2B for $\mbox{V}_{\mbox{\scriptsize S}}$



# 表 48. INT\_EN\_CFG4 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
15-6	IN23_EN	R/W	0h	xxxxxxxx00: no interrupt generation for IN23 w.r.t. THRES3A
				xxxxxxxxx01: interrupt generation on rising edge above THRES3A for IN23
				xxxxxxxx10: interrupt generation on falling edge below THRES3A for IN23
				xxxxxxxxx11: interrupt generation on falling and rising edge of THRES3A for IN23
				xxxxxx00xx: no interrupt generation for IN23 w.r.t. THRES3B
				xxxxxx01xx: interrupt generation on rising edge above THRES3B for IN23
				xxxxxx10xx: interrupt generation on falling edge below THRES3B for IN23
				xxxxxx11xx: interrupt generation on falling and rising edge of THRES3B for IN23
				xxxx00xxxx: no interrupt generation for IN23 w.r.t. THRES3C
				xxxx01xxxx: interrupt generation on rising edge above THRES3C for IN23
				xxxx10xxxx: interrupt generation on falling edge below THRES3C for IN23
				xxxx11xxxx: interrupt generation on falling and rising edge of THRES3C for IN23
				xx00xxxxxx: no interrupt generation for IN23 w.r.t. THRES8
				xx01xxxxxx: interrupt generation on rising edge above THRES8 for IN23
				xx10xxxxxx: interrupt generation on falling edge below THRES8 for IN23
				xx11xxxxxx: interrupt generation on falling and rising edge of THRES8 for IN23
				00xxxxxxxx: no interrupt generation for IN23 w.r.t. THRES9
				01xxxxxxxx: interrupt generation on rising edge above THRES9 for IN23
				10xxxxxxxx: interrupt generation on falling edge below THRES9 for IN23
				11xxxxxxxx: interrupt generation on falling and rising edge of THRES9 for IN23
5-0	IN22_EN	R/W	0h	xxxx00: no interrupt generation for IN22 w.r.t. THRES3A
				xxxx01: interrupt generation on rising edge above THRES3A for IN22
				xxxx10: interrupt generation on falling edge below THRES3A for IN22
				xxxx11: interrupt generation on falling and rising edge of THRES3A for IN22
				xx00xx: no interrupt generation for IN22 w.r.t. THRES3B
				xx01xx: interrupt generation on rising edge above THRES3B for IN22
				xx10xx: interrupt generation on falling edge below THRES3B for IN22
				xx11xx: interrupt generation on falling and rising edge of THRES3B for IN22
				00xxxx: no interrupt generation for IN22 w.r.t. THRES3C
				01xxxx: interrupt generation on rising edge above THRES3C for IN22
				10xxxx: interrupt generation on falling edge below THRES3C for IN22
				11xxxx: interrupt generation on falling and rising edge of THRES3C for IN22



### 8.6.38 THRES\_CFG0 Register (Offset = 29h) [reset = 0h]

THRES\_CFG0 is shown in 图 75 and described in 表 49.

Return to Summary Table.

#### 图 75. THRES\_CFG0 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED	)					THR	ES1									THR	ES0				
	R-	0h			R-0h										R-	0h							

LEGEND: R/W = Read/Write; R = Read only

#### 表 49. THRES\_CFG0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
31-20	RESERVED	R	0h	Reserved
19-10	THRES1	R/W	Oh	10-bits value of threshold 1: Bit10: LSB Bit19: MSB
9-0	THRES0	R/W	Oh	10-bits value of threshold 0 Bit0: LSB Bit9: MSB

### 8.6.39 THRES\_CFG1 Register (Offset = 2Ah) [reset = 0h]

THRES\_CFG1 is shown in 图 76 and described in 表 50.

Return to Summary Table.

#### 图 76. THRES\_CFG1 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	RESE	RVED						THR	ES3									THR	ES2				
	R-	0h			R-0h													R-	0h				

LEGEND: R/W = Read/Write; R = Read only

#### 表 50. THRES\_CFG1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	THRES3	R/W	0h	10-bits value of threshold 3:
				Bit10: LSB
				Bit19: MSB
9-0	THRES2	R/W	0h	10-bits value of threshold 2
				Bit0: LSB
				Bit9: MSB



#### 8.6.40 THRES\_CFG2 Register (Offset = 2Bh) [reset = 0h]

THRES\_CFG2 is shown in 图 77 and described in 表 51.

Return to Summary Table.

#### 图 77. THRES\_CFG2 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ı	RESE	RVED						THR	ES5									THR	ES4				
	R-	0h			R-0h													R-	0h				

LEGEND: R/W = Read/Write; R = Read only

#### 表 51. THRES\_CFG2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-20	RESERVED	R	0h	Reserved
19-10	THRES5	R/W	Oh	10-bits value of threshold 5: Bit10: LSB Bit19: MSB
10-1	THRES4	R/W	Oh	10-bits value of threshold 4: Bit0: LSB Bit9: MSB

### 8.6.41 THRES\_CFG3 Register (Offset = 2Ch) [reset = X]

THRES\_CFG3 is shown in 图 78 and described in 表 52.

Return to Summary Table.

#### 图 78. THRES\_CFG3 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0				
	RESE	RVED	)	THRES6								THRES7															
	R-	0h			R-0h													R-	0h	R-0h							

LEGEND: R/W = Read/Write; R = Read only

#### 表 52. THRES\_CFG3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
31-20	RESERVED	R	0h	Reserved
19-10	THRES7	R/W	0h	10-bits value of threshold 7: Bit10: LSB
				Bit19: MSB
9-0	THRES6	R/W	Oh	10-bits value of threshold 6: Bit0: LSB Bit9: MSB



### 8.6.42 THRES\_CFG4 Register (Offset = 2Dh) [reset = X]

THRES\_CFG4 is shown in 图 79 and described in 表 53.

Return to Summary Table.

## 图 79. THRES\_CFG4 Register

23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
RESERVED THRES9										THRES8													
	R-	0h		R-0h												R-	0h						

LEGEND: R/W = Read/Write; R = Read only

### 表 53. THRES\_CFG4 Register Field Descriptions

Bit	Field	Туре	Reset	Description
31-20	RESERVED	R	0h	Reserved
19-10	THRES9	R/W	Oh	10-bits value of threshold 9: Bit10: LSB Bit19: MSB
9-0	THRES8	R/W	Oh	10-bits value of threshold 8: Bit0: LSB Bit9: MSB



# 8.6.43 THRESMAP\_CFG0 Register (Offset = 2Eh) [reset = 0h]

THRESMAP\_CFG0 is shown in 图 80 and described in 表 54.

Return to Summary Table.

### 图 80. THRESMAP\_CFG0 Register

23	22	21	20	19	18	17	16	15	14	13	12	
TI	HRESMAP_IN	17	TH	RESMAP_II	N6	TH	HRESMAP_II	N5	THRESMAP_IN4			
	R/W-0h			R/W-0h			R/W-0h			R/W-0h		
11	10	9	8	7	6	5	4	3	2	1	0	
TI	HRESMAP_IN	13	TH	RESMAP_II	N2	TH	HRESMAP_II	N1	THRESMAP_IN0			
R/W-0h R/W-0h							R/W-0h		R/W-0h			

LEGEND: R/W = Read/Write

### 表 54. THRESMAP\_CFG0 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-21	THRESMAP_IN7	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6
20-18	THRESMAP_IN6	R/W	Oh	7h = THRES7  0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
17-15	THRESMAP_IN5	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
14-12	THRESMAP_IN4	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7



# 表 54. THRESMAP\_CFG0 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
11-9	THRESMAP_IN3	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
8-6	THRESMAP_IN2	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
5-3	THRESMAP_IN1	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
2-0	THRESMAP_IN0	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7

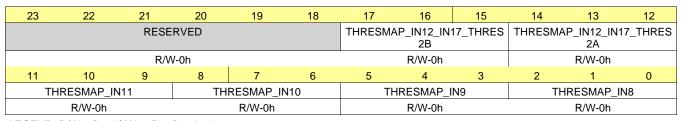


### 8.6.44 THRESMAP\_CFG1 Register (Offset = 2Fh) [reset = 0h]

THRESMAP\_CFG1 is shown in 图 81 and described in 表 55.

Return to Summary Table.

## 图 81. THRESMAP\_CFG1 Register



LEGEND: R/W = Read/Write; R = Read only

## 表 55. THRESMAP\_CFG1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-18	RESERVED	R	0h	Reserved
17-15	THRESMAP_IN12_IN17_ THRES2B	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
14-12	THRESMAP_IN12_IN17_ THRES2A	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
11-9	THRESMAP_IN11	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
8-6	THRESMAP_IN10	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7



# 表 55. THRESMAP\_CFG1 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
5-3	THRESMAP_IN9	R/W	0h	0h = THRES0
				1h = THRES1
				2h = THRES2
				3h = THRES3
				4h = THRES4
				5h = THRES5
				6h = THRES6
				7h = THRES7
2-0	THRESMAP_IN8	R/W	0h	0h = THRES0
				1h = THRES1
				2h = THRES2
				3h = THRES3
				4h = THRES4
				5h = THRES5
				6h = THRES6
				7h = THRES7



# 8.6.45 THRESMAP\_CFG2 Register (Offset = 30h) [reset = 0h]

THRESMAP\_CFG2 is shown in 图 82 and described in 表 56.

Return to Summary Table.

### 图 82. THRESMAP\_CFG2 Register

23	22	21	20	19	18	17	16	15	14	13	12
	RESERVED		THRESM	AP_VS1_T	THRES2B	THRESN	MAP_VS1_T	HRES2A	THRESM	IAP_VS0_TI	HRES2B
	R-0h			R/W-0h			R/W-0h			R/W-0h	
11	10	9	8	7	6	5	4	3	2	1	0
THRES	SMAP_VS0_TH	RES2A	THRESMA	P_IN18_IN 3C	23_THRES	THRESMA	P_IN18_IN 3B	23_THRES	THRESMA	P_IN18_IN2 3A	3_THRES
	R/W-0h			R/W-0h			R/W-0h			R/W-0h	

LEGEND: R/W = Read/Write; R = Read only

## 表 56. THRESMAP\_CFG2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-21	RESERVED	R	0h	Reserved
20-18	THRESMAP_VS1_THRE S2B	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
17-15	THRESMAP_VS1_THRE S2A	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
14-12	THRESMAP_VS0_THRE S2B	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7
11-9	THRESMAP_VS0_THRE S2A	R/W	Oh	0h = THRES0 1h = THRES1 2h = THRES2 3h = THRES3 4h = THRES4 5h = THRES5 6h = THRES6 7h = THRES7



# 表 56. THRESMAP\_CFG2 Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
8-6	THRESMAP_IN18_IN23_	R/W	0h	0h = THRES0
	THRES3C			1h = THRES1
				2h = THRES2
				3h = THRES3
				4h = THRES4
				5h = THRES5
				6h = THRES6
				7h = THRES7
5-3	THRESMAP_IN18_IN23_	R/W	0h	0h = THRES0
	THRES3B			
				1h = THRES1
				2h = THRES2
				3h = THRES3
				4h = THRES4
				5h = THRES5
				6h = THRES6
				7h = THRES7
2-0	THRESMAP_IN18_IN23_	R/W	0h	0h = THRES0
	THRES3A			1h = THRES1
				2h = THRES2
				3h = THRES3
				4h = THRES4
				5h = THRES5
				6h = THRES6
				7h = THRES7



# 8.6.46 Matrix Register (Offset = 31h) [reset = 0h]

Matrix is shown in 图 83 and described in 表 57.

Return to Summary Table.

## 图 83. Matrix Register

23	22	21	20	19	18	17	16	15	14	13	12
RESERVED						IN_CO	M_EN	Т	HRES_COM	Л	
R-0h					R/W	/-0h		R/W-0h			
11	11 10 9 8 7 6 5				5	4	3	2	1	0	
THRES_COM						MAT	RIX	POL	L_ACT_TIM	E_M	
R/W-0h						R/W	/-0h		R/W-0h		

LEGEND: R/W = Read/Write; R = Read only

## 表 57. Matrix Register Field Descriptions

Bit	Field	Туре	Reset	Description
23-17	RESERVED	R	0h	Reserved
16-15	IN_COM_EN	R/W	0h	0h = no interrupt generation for w.r.t. threshold THRES_COM
				1h = interrupt generation on rising edge above threshold THRES_COM
				2h = interrupt generation on falling edge below threshold THRES_COM
				3h = interrupt generation on falling and rising edge of threshold THRES_COM
14-5	THRES_COM	R/W	0h	10-bits value of threshold THRES_COM:
				Bit5: LSB
				Bit14: MSB
4-3	MATRIX	R/W	0h	0h = no matrix, regular inputs only
				1h = 4x4 matrix
				2h = 5x5 matrix
				3h = 6x6 matrix
2-0	POLL_ACT_TIME_M	R/W	0h	Polling active time setting for the matrix inputs:
				$0h = 64\mu s$
				1h = 128μs
				$2h = 256\mu s$
				$3h = 384\mu s$
				$4h = 512\mu s$
				5h = 768μs
				6h = 1024μs
				7h = 1360μs



## 8.6.47 Mode Register (Offset = 32h) [reset = 0h]

Mode is shown in 图 84 and described in 表 58.

Return to Summary Table.

# 图 84. Mode Register

23	22	21	20	19	18	17	16	15	14	13	12
M_IN23	M_IN22	M_IN21	M_IN20	M_IN19	M_IN18	M_IN17	M_IN16	M_IN15	M_IN14	M_IN13	M_IN12
R/W-0h											
11	10	9	8	7	6	5	4	3	2	1	0
M_IN11	M_IN10	M_IN9	M_IN8	M_IN7	M_IN6	M_IN5	M_IN4	M_IN3	M_IN2	M_IN1	M_IN0
R/W-0h											

LEGEND: R/W = Read/Write

### 表 58. Mode Register Field Descriptions

	表 56. Widde Register Field Descriptions							
Bit	Field	Туре	Reset	Description				
23	M_IN23	R/W	0h	0h = comparator mode for IN23 1h = ADC mode for IN23				
22	M_IN22	R/W	0h	0h = comparator mode for IN22 1h = ADC mode for IN22				
21	M_IN21	R/W	0h	0h = comparator mode for IN21 1h = ADC mode for IN21				
20	M_IN20	R/W	0h	0h = comparator mode for IN20 1h = ADC mode for IN20				
19	M_IN19	R/W	0h	0h = comparator mode for IN19 1h = ADC mode for IN19				
18	M_IN18	R/W	Oh	0h = comparator mode for IN18 1h = ADC mode for IN18				
17	M_IN17	R/W	Oh	0h = comparator mode for IN17 1h = ADC mode for IN17				
16	M_IN16	R/W	0h	0h = comparator mode for IN16 1h = ADC mode for IN16				
15	M_IN15	R/W	0h	0h = comparator mode for IN15 1h = ADC mode for IN15				
14	M_IN14	R/W	0h	0h = comparator mode for IN14 1h = ADC mode for IN14				
13	M_IN13	R/W	0h	0h = comparator mode for IN13 1h = ADC mode for IN13				
12	M_IN12	R/W	0h	0h = comparator mode for IN12 1h = ADC mode for IN12				
11	M_IN11	R/W	0h	0h = comparator mode for IN11 1h = ADC mode for IN11				
10	M_IN10	R/W	Oh	0h = comparator mode for IN10 1h = ADC mode for IN10				
9	M_IN9	R/W	0h	0h = comparator mode for IN9 1h = ADC mode for IN9				
8	M_IN8	R/W	Oh	0h = comparator mode for IN8 1h = ADC mode for IN8				



## 表 58. Mode Register Field Descriptions (接下页)

Bit	Field	Туре	Reset	Description
7	M_IN7	R/W	0h	0h = comparator mode for IN7 1h = ADC mode for IN7
6	M_IN6	R/W	0h	0h = comparator mode for IN6 1h = ADC mode for IN6
5	M_IN5	R/W	0h	0h = comparator mode for IN5 1h = ADC mode for IN5
4	M_IN4	R/W	0h	0h = comparator mode for IN4 1h = ADC mode for IN4
3	M_IN3	R/W	0h	0h = comparator mode for IN3 1h = ADC mode for IN1
2	M_IN2	R/W	0h	0h = comparator mode for IN2 1h = ADC mode for IN0
1	M_IN1	R/W	0h	0h = comparator mode for IN1 1h = ADC mode for IN1
0	M_INO	R/W	0h	0h = comparator mode for IN0 1h = ADC mode for IN0

# 8.7 Programming Guidelines

When configuring the TIC12400-Q1, it is critical to follow the programming guideline summarized below (see 表 59) to ensure proper behavior of the device:

## 表 59. TIC12400-Q1 Programming Guidelines

Category	Programming requirement
Threshold setup:	<ul> <li>THRES2B ≥ THRES2A (for IN12 to IN17)</li> <li>THRES3C ≥ THRES3B ≥ THRES3A (for IN18 to IN22)</li> <li>THRES9 ≥ THRES8 ≥ THRES3C ≥ THRES3B ≥ THRES3A (for IN23)</li> </ul>
Threshold setup:  • V <sub>S</sub> measurement	<ul><li>VS0_THRES2B ≥ VS0_THRES2A</li><li>VS1_THRES2B ≥ VS1_THRES2A</li></ul>
4x4 matrix mode (MATRIX [4:3] = 2'b01)	<ul> <li>POLL_EN=1</li> <li>IN_EN[7:4]=4'b1111; IN_EN[13:10]= 4'b1111</li> <li>MODE[7:4] = 4'b0000; MODE[13:10] = 4'b0000</li> <li>CS_SELECT[7:4]= 4'b1111; CS_SELECT[13:10]= 4'b0000</li> <li>IWETT(CSI) &gt; IWETT (CSO): <ol> <li>WC_CFG0[20:18] &gt; WC_CFG0[8:6]</li> <li>WC_CFG0[23:21] &gt; WC_CFG0[11:9]</li> <li>WC_CFG1[2:0] &gt; WC_CFG0[14:12]</li> </ol> </li> <li>If TW event is expected, CSO can only be set to 1mA or 2mA: <ol> <li>If WC_CFG0[8:6]= 3'b001: WC_CFG0[20:18]= 3'b010, 3'b011, 3'b100, 3'b111, 3'b110, or 3'b111; If WC_CFG0[8:6]= 3'b010: WC_CFG0[20:18]= 3'b011</li> <li>If WC_CFG0[11:9]= 3'b001: WC_CFG0[23:21]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG0[11:9]= 3'b010: WC_CFG0[23:21]= 3'b011</li> <li>If WC_CFG1[2:0]= 3'b001: WC_CFG0[14:12]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[2:0]= 3'b010: WC_CFG0[14:12]= 3'b011</li> </ol></li></ul>



# Programming Guidelines (接下页)

#### 表 59. TIC12400-Q1 Programming Guidelines (接下页)

表 59. HC12400-Q1 Programming Guidelines (接下贝)					
Category	Programming requirement				
5x5 matrix mode (MATRIX [4:3] = 2'b10)	<ul> <li>POLL_EN=1</li> <li>IN_EN[8:4]= 5'b11111; IN_EN[14:10]= 5'b11111</li> <li>MODE[8:4] = 5'b00000; MODE[14:10] = 5'b00000</li> <li>CS_SELECT[8:4]= 5'b11111; CS_SELECT[14:10]= 5'b00000</li> <li>IWETT(CSI) &gt; IWETT (CSO):  1. WC_CFG0[20:18] &gt; WC_CFG0[8:6]  2. WC_CFG0[23:21] &gt; WC_CFG0[11:9]  3. WC_CFG1[2:0] &gt; WC_CFG0[14:12]  4. WC_CFG1[5:3] &gt; WC_CFG0[17:15]</li> <li>If TW event is expected, CSO can only be set to 1mA or 2mA:  1. If WC_CFG0[8:6]= 3'b001: WC_CFG0[20:18]= 3'b010, 3'b011, 3'b100, 3'b111, 3'b110, or 3'b111; If WC_CFG0[8:6]= 3'b010: WC_CFG0[20:18] = 3'b011</li> <li>2. If WC_CFG0[11:9]= 3'b001: WC_CFG0[23:21]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG0[11:9]= 3'b010: WC_CFG0[23:21] = 3'b011</li> <li>3. If WC_CFG1[2:0]= 3'b001: WC_CFG0[14:12]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[2:0]= 3'b010: WC_CFG0[14:12]= 3'b011</li> <li>4. If WC_CFG1[5:3]= 3'b001: WC_CFG0[17:15]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[5:3]= 3'b010: WC_CFG0[17:15]= 3'b011</li> </ul>				
6x6 Matrix Mode (MATRIX [4:3]= 2'b11)	<ul> <li>POLL_EN=1</li> <li>IN_EN[9:4]= 6'b111111; IN_EN[15:10]= 6'b111111</li> <li>MODE[9:4] = 6'b000000; MODE[15:10] = 6'b000000</li> <li>CS_SELECT[9:4]= 6'b111111; CS_SELECT[15:10]= 6'b000000</li> <li>IWETT(CSI) &gt; IWETT (CSO):  1. WC_CFG0[20:18] &gt; WC_CFG0[8:6]  2. WC_CFG0[23:21] &gt; WC_CFG0[11:9]  3. WC_CFG1[2:0] &gt; WC_CFG0[14:12]  4. WC_CFG1[5:3] &gt; WC_CFG0[17:15]</li> <li>If TW event is expected, CSO can only be set to 1mA or 2mA:  1. If WC_CFG0[8:6]= 3'b001: WC_CFG0[20:18]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG0[8:6]= 3'b010: WC_CFG0[20:18] = 3'b011</li> <li>2. If WC_CFG0[11:9]= 3'b001: WC_CFG0[23:21]= 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG0[11:9]= 3'b010: WC_CFG0[23:21] = 3'b011</li> <li>3. If WC_CFG1[2:0]= 3'b001: WC_CFG0[14:12]= 3'b010, 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[2:0]= 3'b010: WC_CFG0[14:12]= 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[5:3]= 3'b010: WC_CFG0[17:15]= 3'b011, 3'b100, 3'b101, 3'b110, or 3'b111; If WC_CFG1[5:3]= 3'b010: WC_CFG0[17:15]= 3'b011</li> </ul>				
Clean Current Polling (if CCP_INx= 1 in the CCP_CFG1 register)	At least one input (standard or matrix) or the VS measurement has to be enabled: IN_EN_x= 1 in the IN_EN register or CONFIG [16]= 1'b1 <sup>(1)</sup>				
Wetting current auto-scaling (if WC_CFG1 [22:21] != 2b'11)	<ul> <li>The wetting current auto-scaling feature is only activated in the continuous mode: POLL_EN= 0 (2)</li> <li>The wetting current auto-scaling only applies to 10mA or 15mA wetting currents: WC_INx bits = 3'b100, 3'b101, 3'b110, or 3'b111 in the WC_CFG0 and WC_CFG1 registers. (2)</li> </ul>				
Wetting current diagnostic (If CONFIG [21:18] != 4b'0000)	<ul> <li>At least one channel has to be enabled from IN0 to IN3 (IN_EN[3:0] != 4b'0000)</li> <li>Inputs IN0 to IN3 need to be configured to ADC input mode: MODE[3:0] = 4'b1111</li> <li>Inputs IN0 and IN1 need to be configured to CSO: CS SELECT [1:0]= 2b'00</li> <li>Inputs IN2 and IN3 need to be configured to CSI: CS SELECT [3:2]= 2b'11</li> </ul>				
<ul><li>Continuous mode</li><li>Standard polling mode</li></ul>	t <sub>POLL_TIME</sub> and t <sub>POLL_ACT_TIME</sub> settings have to meet the below requirement: t <sub>POLL_TIME</sub> ≥ 1.3 ×[ t <sub>POLL_ACT_TIME</sub> + n × 24μs + 10 μs] <sup>(3)(4)</sup> • n: the number of enabled channels configured in register IN_EN • t <sub>POLL_TIME</sub> : timing setting configured in CONFIG[4:1] • t <sub>POLL_ACT_TIME</sub> : timing setting configured in CONFIG[8:5]				

<sup>(1)</sup> This is a soft requirement to take advantage of the clean current polling feature. The feature takes no effect otherwise.

<sup>(2)</sup> These are soft requirements to take advantage of the wetting current auto-scaling feature. The feature takes no effect otherwise.

<sup>(3)</sup> If WCD is enabled, add additional 96μs

<sup>(4)</sup> If CCP is enabled, add tCCP\_TRAN +tCCP\_TIME, where tCCP\_TIME is the timing setting configured in CCP\_CFG0[6:4]



# Programming Guidelines (接下页)

# 表 59. TIC12400-Q1 Programming Guidelines (接下页)

Category	Programming requirement
	tpoll_time ,tpoll_act_time, and tpoll_act_time_m settings have to meet the below requirement:
Matrix polling mode	t <sub>POLL_TIME</sub> > 1.3 × [ m × t <sub>POLL_ACT_TIME_M</sub> + t <sub>POLL_ACT_TIME</sub> + n × 24μs + 10 μs] (3)(4)  • n: the number of enabled channels configured in register IN_EN  • m: 16 for 4x4 matrix; 25 for 5x5 matrix; 36 for 6x6 matrix
	<ul> <li>t<sub>POLL_TIME</sub>: timing setting configured in CONFIG[4:1]</li> <li>t<sub>POLL_ACT_TIME_M</sub>: timing setting configured in MATRIX[2:0]</li> <li>t<sub>POLL_ACT_TIME</sub>: timing setting configured in CONFIG[8:5]</li> </ul>



# 9 Application and Implementation

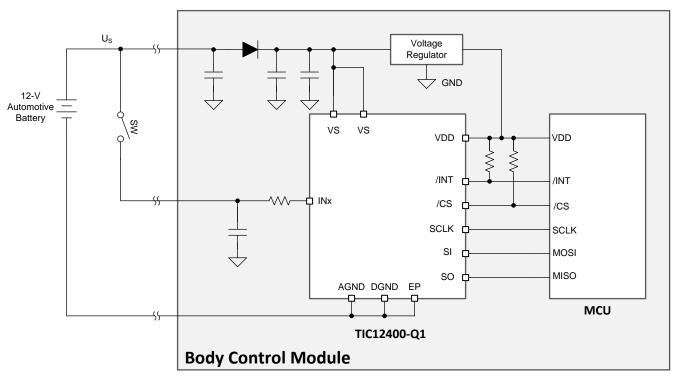
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The TIC12400-Q1 is an advanced 24-input Multiple Switch Detection Interface (MSDI) device designed to detect external mechanical switch status in a 12-V automotive system by acting as an interface between the switches and the low- voltage microcontroller. The device offers a number of unique features to replace systems implemented with discrete components, saving board space and reducing the bill of materials (BOM). The device can also be configured into low-power polling mode, which provides significant savings on system power consumption.

## 9.2 Using TIC12400-Q1 in a 12 V Automotive System



Copyright © 2016, Texas Instruments Incorporated

图 85. Typical system diagram of battery connections for TIC12400-Q1

The TIC12400-Q1 is designed to operate with a 12 V automotive system.  $\boxtimes$  85 depicts a typical system diagram to show how the device is connected to the battery. Care must be taken when connecting the battery directly to the device on the V<sub>S</sub> supply pin (through a reverse-blocking diode) or the input (IN<sub>X</sub>) pins since an automotive battery can be subjected to various transient and over-voltage events. Manufacturers have independently created standards and test procedures in an effort to prevent sensitive electronics from failing due to these events. Recently, combined efforts are made with ISO to develop the ISO 16750-2 standard (Road vehicles -- Environmental conditions and testing for electrical and electronic equipment -- Part 2: Electrical loads), which describe the possible transients that could occur to an automotive battery and specify test methods to simulate them.



# Using TIC12400-Q1 in a 12 V Automotive System (接下页)

It shall be noted that the TIC12400-Q1 is designed and tested according to the ISO 16750-2 standard. A few voltage stress tests and their test conditions are listed below. Exposing the device to more severe transient events than described by the standard could potentially causes performance degradation and long-term damage to the device.

- Direct current supply voltage: V<sub>BAT, min</sub>= 6 V; V<sub>BAT, max</sub>= 16 V

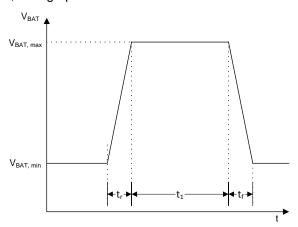


图 86. Voltage profile to test a jump start event

表 60. Voltage profile parameters to test a jump start event

Parameter	Value
$V_{BAT,\;min}$	10.8 V
V <sub>BAT, max</sub>	24 V
t <sub>r</sub>	< 10 ms
t <sub>1</sub>	60 s ± 6 s
t <sub>f</sub>	< 10 ms
Number of cycles	1

To emulate a load dump event for an alternator with centralized load dump suppression, voltage profile
described below is used. U<sub>A</sub> and U<sub>S</sub>\* are applied directly to V<sub>BAT</sub>.

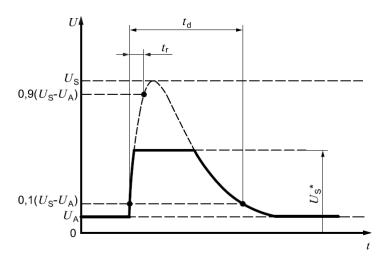


图 87. Voltage profile to test a load dump event with centralized load dump suppression



表 61. Voltage profile used to test a load dump event with centralized load dump suppression	表 61.	Voltage profile	used to test a lo	ad dump event with	centralized load dump	suppression
---	-------	-----------------	-------------------	--------------------	-----------------------	-------------

Parameter	Value
$U_A$	13.5 V
U <sub>S</sub>	79 V ≤ US ≤ 101
U <sub>S</sub> *	35 V
t <sub>d</sub>	40 ms ≤ t <sub>d</sub> ≤ 400 ms
t <sub>r</sub>	< 10 ms
Number of cycles	5 pulses at intervals of 1 min

To emulate a cranking event, voltage profile describe below is used. U<sub>S</sub>, U<sub>S6</sub>, and U<sub>A</sub> are applied directly to V<sub>BAT</sub>.

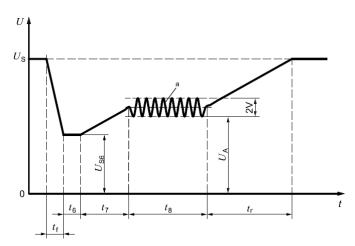


图 88. Voltage profile to test a cranking event

表 62. Voltage profile used to test a cranking event

	- · · · · · · · · · · · · · · · · · · ·	•			
Parameter	Value - Level I	Value - Level II	Value - Level IV		
U <sub>S6</sub>	8 V	4.5 V	6 V		
U <sub>S</sub>	9.5 V	6.5 V	6.5 V		
U <sub>A</sub>	14 V ± 0.2 V	$14 \text{ V} \pm 0.2 \text{ V}$	14 V ± 0.2 V		
t <sub>f</sub>	5 ms ± 0.5 ms	5 ms ± 0.5 ms	5 ms ± 0.5 ms		
t <sub>6</sub>	15 ms ± 1.5 ms	15 ms ± 1.5 ms	15 ms ± 1.5 ms		
t <sub>7</sub>	50 ms ± 5 ms	50 ms ± 5 ms	50 ms ± 5 ms		
t <sub>8</sub>	1000 ms ± 100 ms	10000 ms ± 1000 ms	10000 ms ± 1000 ms		
t <sub>r</sub>	40 ms ± 4 ms	100 ms ± 10 ms	100 ms ± 10 ms		

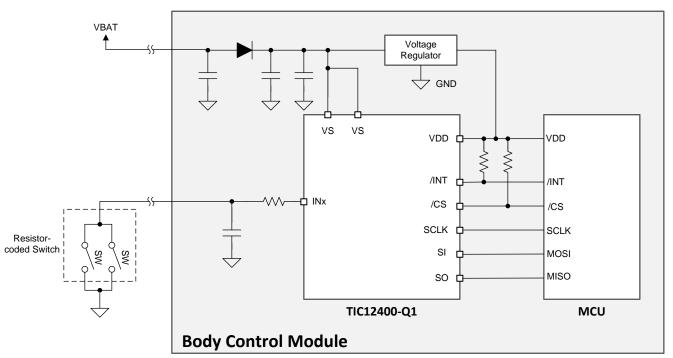
## 9.3 Resistor-coded Switches Detection in Automotive Body Control Module

The body control module (BCM) is an electronic control unit responsible for monitoring and controlling various electronic accessories in a vehicle's body. Detection of various mechanical switches status in a vehicle is one important task handled by the BCM. Besides the typical on-and-off (or digital) type of switch, more sophisticated type of switches, called resistor-coded switches, can also be present in an automotive body control system.

Resistor-coded switches have more than 2 unique switch states, and are often used for implementation of wiper, illumination, and signal control arms in a vehicle. Due to various voltage potentials generated by different positions of a resistor-coded switch, an ADC, typically inside the microcontroller, is used to detect the different states of the switch. The TIC12400-Q1 can natively support monitoring of an resistor-coded switch with its integrated 10-bit ADC and configurable thresholds. The following application diagram depicts how the TIC12400-Q1 is used in a BCM to detect external mechanical resistor-coded switches and a detailed design example is shown in the following sections.

# TEXAS INSTRUMENTS

# Resistor-coded Switches Detection in Automotive Body Control Module (接下页)



Copyright © 2016, Texas Instruments Incorporated

#### 图 89. Using TIC12400-Q1 to Monitor a Resistor-Coded Switch in Body Control Module Application

#### 9.3.1 Design Requirements

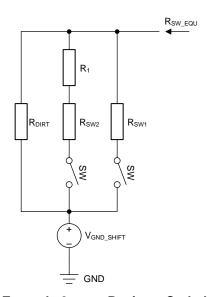


图 90. Example 3-state Resistor-Coded Switch

表 63. Example Resistor-Coded Switch Specification

	SPECIFICATION	MIN	MAX
$V_{BAT}$	9 V ≤ V <sub>BAT</sub> ≤ 16 V	9 V	16 V
R <sub>1</sub>	680 Ω ± 8%	625.6 Ω	734.4 Ω
R <sub>SW1</sub>	50 $\Omega$ Max when closed	0 Ω	50 Ω



## Resistor-coded Switches Detection in Automotive Body Control Module (接下页)

表 63. Example Resistor-Coded Switch Specification (接下页)

	SPECIFICATION	MIN	MAX
R <sub>SW2</sub>	50 $\Omega$ Max when closed	0 Ω	50 Ω
R <sub>DIRT</sub>	5000 Ω Min	5000 Ω	∞
V <sub>GND_SHIFT</sub>	±1 V	-1 Ω	+1 Ω

An example of a 3-state resistor-coded switch is shown in 图 90, with 表 63 summarizing its detailed specification. The goal of this design is to utilize the TIC12400-Q1's integrated ADC to detect and differentiate the 3 switch states:

- 1. State 1: Both SW1 and SW2 open
- 2. State 2: SW1 open and SW2 closed
- 3. State 3: SW1 closed and SW2 open

To mimic real automotive systems, the battery is assumed to be fluctuating between 9 V and 16 V. R<sub>DIRT</sub> is introduced to model the small leakage flowing across the switch in open state. There is also a ±1 V ground shift present in the system, meaning there could be up to ±1 V of potential difference between the switch reference point and the ground reference of the TIC12400-Q1. When the switch changes position and the switch state changes from one to another, the TIC12400-Q1 is required to correctly detect the state transition and issue an interrupt to alert the microcontroller. The switch information needs to be stored in the status registers for the microcontroller to retrieve.

#### 9.3.2 Detailed Design Procedure

STEP Equivalent R Value

P 1	STE	P 2	STE	P 3	STE	STEP 5		
Resistance (Ω)	V <sub>IN</sub>	, (V)	V <sub>INX</sub> + V <sub>GN</sub>	ND_SHIFT(V)	ADC Cod	e Spread	Threshold	
MAX	MIN	MAX	MIN	MAX	MIN	MAX		
8	> 6 V	-	>6 V	-	1023	-		

表 64. Detailed Design Procedure

	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
State 1: Both SW1 and SW2 open	5000	∞	> 6 V	-	>6 V	-	1023	-	
State 2: SW1 open and SW2 closed	555.95	678.03	2.502	3.729	1.502	4.729	256	806	915
State 3: SW1 closed and SW2 open	0	49.5	0	0.272	0	1.272	0	217	237

use the following procedures to calculate thresholds to program to the TIC12400-Q1 for proper switch detection:

- Calculate the equivalent resistance values at different switch states, taking into account R<sub>DIRT</sub> and the 8% resistance variation.
- 2. Estimate the voltage established when wetting current flows through the switch by utilizing the relationship  $V_{INX} = R_{SW\_EQU} \times I_{WETT\_ACT}$ , where  $R_{SW\_EQU}$  is the equivalent switch resistance value and  $I_{WETT\_ACT}$  is the actual wetting current flowing through the switch. The 5 mA wetting current setting is selected in this design, because it best uses the dynamic range of the ADC (from 0 to 6 V). The wetting current, however, can vary depending on manufacturing process variation and operating temperature, and needs to be taken into account. Referring to the electrical table of the TIC12400-Q1 and assuming enough headroom for the current source (CSO) to operate, the 5mA wetting current setting produces current ranging between 4.5 mA and 5.5 mA (for  $V_S IN_X \ge 3$  V condition). The voltage established on the TIC12400-Q1 input pin ( $V_{INX}$ ) can be calculated accordingly.
- Take the ground shift non-ideality into account. As defined in *Design Requirements*, the ground shift can be varying between ±1 V. Therefore, effectively, the actual voltage seen at the TIC12400-Q1 can also vary up to ±1 V.
- 4. Convert the voltage established on the INx pin into equivalent ADC code. The full-scale range of the 10-bit ADC is from 0 V to 6 V, with 6 V corresponding to the max code of 1023. Therefore, the ADC code spread for each of the 3 different switch states can be calculated accordingly.
- 5. After the ADC code spread for each switch state is calculated, the detection threshold can be chosen to be



the mid-point between the upper and lower codes of two neighboring states to give best margin for detection.

#### 9.3.3 Application Curves

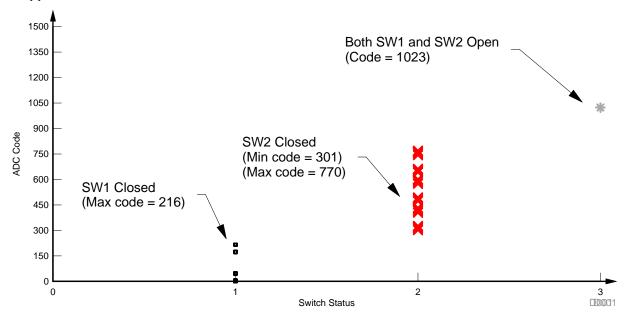


图 91. Measured ADC Code Distribution for the 3 Switch States



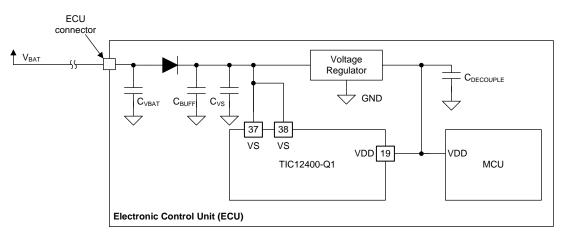
## 10 Power Supply Recommendations

There are two supply input pins for the TIC12400-Q1:  $V_S$  and  $V_{DD}$ .  $V_S$  is the main power supply for the entire chip and is essential for all critical functions of the device. The  $V_S$  supply is designed to be connected to a 12-V automotive battery (through a reverse blocking diode) with nominal operating voltage no greater than 16V. The  $V_{DD}$  supply is used to determine the logic level on the SPI communication interface, source the current for the SO driver, and sets the pull-up voltage for the /CS pin. It can also be used as a possible external pull-up supply for the /INT pin as an alternative to the  $V_S$  supply and it shall be connected to a 3 V to 5.5 V logic supply. Removing  $V_{DD}$  from the device disables SPI communications, but does not impact normal operation of the device.

To improve stability of the supply inputs, some decoupling capacitors are recommended on the PCB. 图 92 shows an example on the on-board power supply decoupling scheme. The battery voltage ( $V_{BAT}$ ) is decoupled on the Electronic Control Unit (ECU) board using a large decoupling capacitor ( $C_{BUFF}$ ). The diode is installed to prevent damage to the internal system under reversed battery condition.  $C_{VS}$  shall be installed close to the TIC12400-Q1 for best decoupling performance. The voltage regulator provides a regulated voltage for the digital portion of the device and for the local microcontroller and its output is decoupled with  $C_{DECOUPLE}$ . 表 65 lists recommended values for each individual decoupling capacitor shown in the system diagram.

24 co. 2 cocup 3 cubu	
CRC RULE	VALUE
C <sub>BUFF</sub>	100 μF, 50 V rated, ±20%
C <sub>VBAT</sub>	100 nF, 50V rated, ±10%; X7R
C <sub>VS</sub>	100 nF, 50 V rated
C <sub>DECOUPLE</sub>	100 nF~1 μF

表 65. Decoupling Capacitor Recommendations



Copyright © 2016, Texas Instruments Incorporated

图 92. Recommended Power Supply Decoupling



## 11 Layout

#### 11.1 Layout Guidelines

- - 1. Decouple the  $V_S$  and  $V_{DD}$  pins with capacitor using recommended values from section *Power Supply Recommendations* and place them as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the  $V_S$  and  $V_{DD}$  supplies.
  - 2. Keep the input lines as short as possible.
  - 3. Use a solid ground plane to help distribute heat and reduce electromagnetic interference (EMI) noise pickup.
  - 4. Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.
  - 5. To achieve good thermal performance, the exposed thermal pad underneath the device must be soldered to the board and flooded with VIAs to ground planes. For simple double-sided PCBs where there are no internal layers, the surface layers can be used to remove heat. For multilayer PCBs, internal ground planes can be used for heat removal.
  - 7. Minimize the inductive parasitic between the INx input capacitors and the thermal pad ground return.



#### 11.2 Layout Example

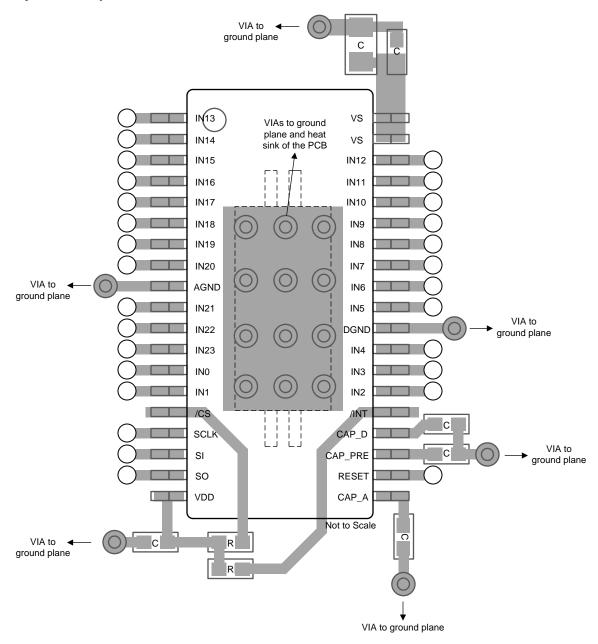


图 93. Example Layout



#### 12 器件和文档支持

#### 12.1 接收文档更新通知

要接收文档更新通知,请导航至 Tl.com 上的器件产品文件夹。单击右上角的*通知我* 进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

#### 12.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 TI 的工程师对工程师 (E2E) 社区。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中,您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

#### 12.3 商标

E2E is a trademark of Texas Instruments.

#### 12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



# 13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据如有变更,恕不另行通知和修订此文档。如欲获取此产品说明书的浏览器版本,请参阅左侧的导航。



## PACKAGE OPTION ADDENDUM

10-Dec-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TIC12400QDCPRQ1	ACTIVE	HTSSOP	DCP	38	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	TIC12400Q	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

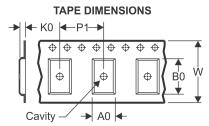
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 26-Feb-2019

## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TIC12400QDCPRQ1	HTSSOP	DCP	38	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

www.ti.com 26-Feb-2019



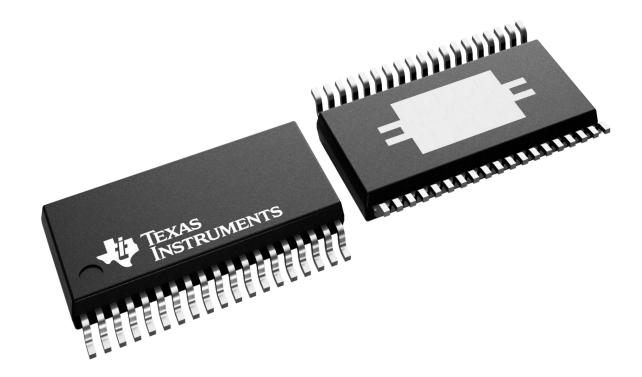
#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TIC12400QDCPRQ1	HTSSOP	DCP	38	2000	350.0	350.0	43.0

4.4 x 9.7, 0.5 mm pitch

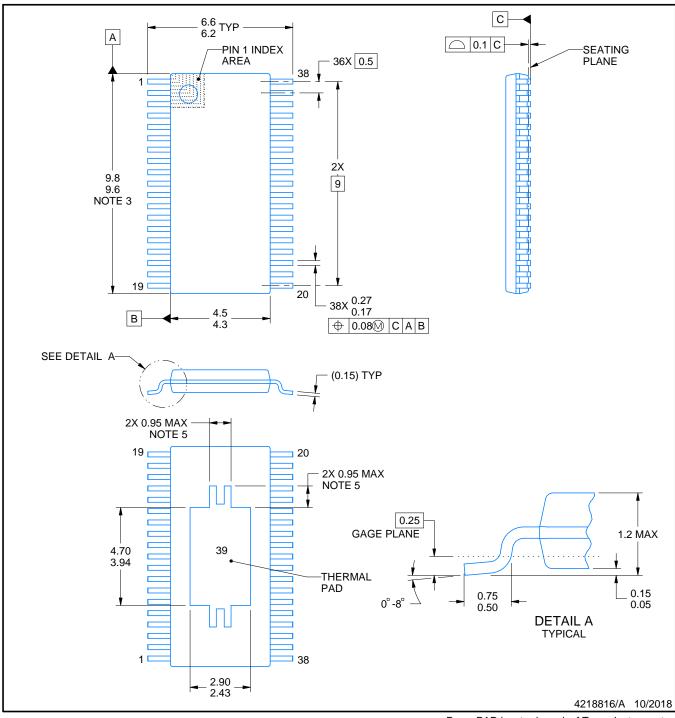
SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



# PowerPAD<sup>™</sup> TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



#### NOTES:

PowerPAD is a trademark of Texas Instruments.

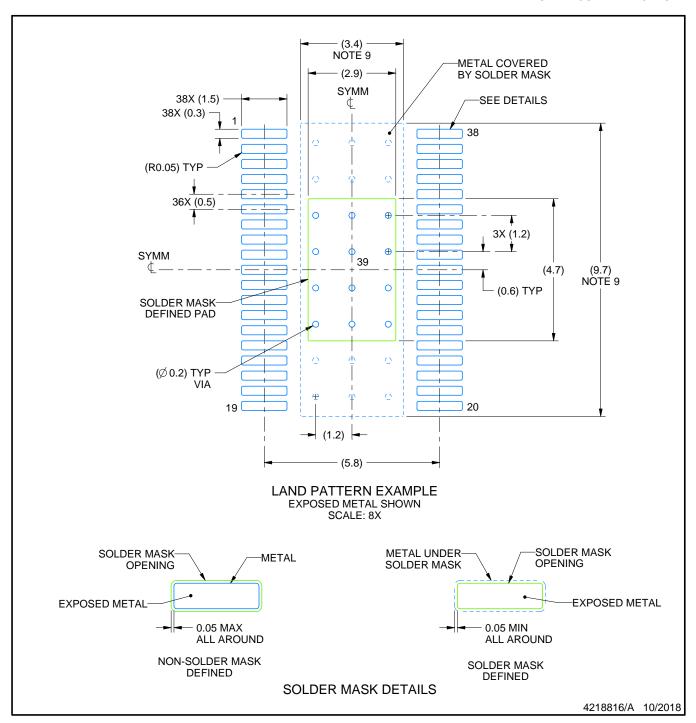
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-153.
- 5. Features may differ or may not be present.



SMALL OUTLINE PACKAGE

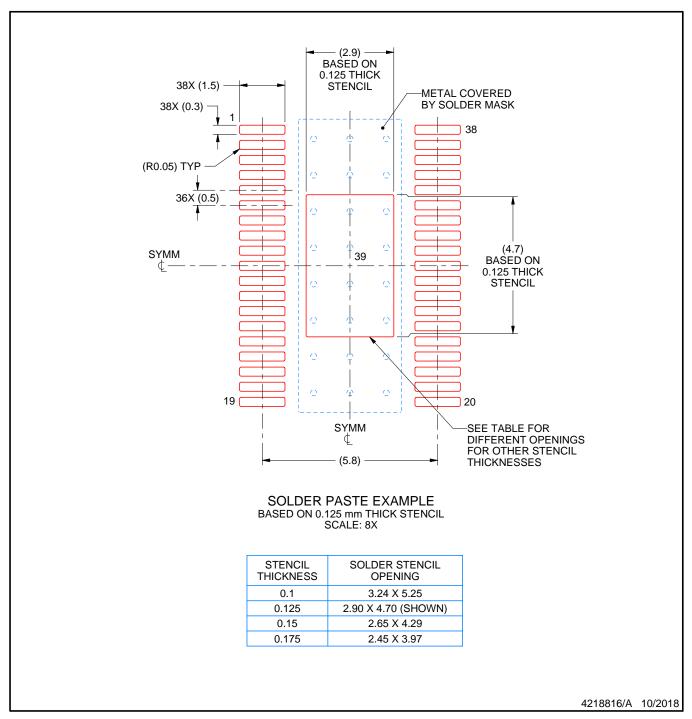


#### NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- 10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



## 重要声明和免责声明

TI 提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源,不保证没有瑕疵且不做出任何明示或暗示的担保,包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任:(1) 针对您的应用选择合适的 TI 产品,(2) 设计、验证并测试您的应用,(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。这些资源如有变更,恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务,TI 对此概不负责。

TI 提供的产品受 TI 的销售条款 (https://www.ti.com.cn/zh-cn/legal/termsofsale.html) 或 ti.com.cn 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

邮寄地址:上海市浦东新区世纪大道 1568 号中建大厦 32 楼,邮政编码:200122 Copyright © 2021 德州仪器半导体技术(上海)有限公司